

Optoelectronic devices

Prof. Dr. H. Hillmer

- 1 very important
- 2 important
- 3 for specialists

Lehrveranstaltungen der „Technischen Elektronik“ --- „Lectures offered by Technological Electronics“

real title / translation

Masterthesis

WS Semiconductor Lasers 3 SWS Halbleiterlaser Nr.5266	WS / SS Praktikum Optoelektronik I (Mikrosystemtechnik, Fabry Pérot arrays, Messung und Simulation) Practical training in Optoelectronics I (Microsystem technology, Fabry Pérot arrays, measurement and simulation) Nr.2281	WS / SS Praktikum Optoelektronik II (Messungen an Halbleiterlasern) Practical training in Optoelectronics II (Measurement of semiconductor Lasers) Nr.2282	SS 2 SWS Microsystem Technology Mikrosystemtechnik in der Optoelektronik Nr.5267	SS 2 SWS Technology of Electronic and Optoelectronic Devices Technologie der elektronischen und optoelektronischen Bauelemente Nr.8500	WS / SS Mikrosystemtechnik Praktikum Microsystem Technology practical training Nr. 2215	WS Semiconductor memories Halbleiter Speicher Nr.2211	WS Nanosensorics Nanosensorik Nr.2285	WS Nanosensorics Lab training Nanosensorik Lab Training Nr.5272	WS / SS Studentenseminar Elektronik und Photonik Seminar in Electronics and Photonics Nr. 5273	SS / WS Seminar Optoelectronics I + II Studentenseminar Optoelektronik Nr .3180	SS 4 SWS Photonische Komponenten und Systeme Photonic components and Systems (Hillmer, Witzigmann, Bangert) Nr.2213
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Bachelorthesis

WS 4 SWS Optoelectronic Devices Komponenten der Optoelektronik Nr. 5265	WS / SS 2 SWS Seminar Elektronik und Optoelektronik Seminar in Electronics and Optoelectronics Nr.5269	WS / SS 2 SWS Studentenseminar Mikrosystemtechnik und Nanotechnologie Seminar Microsystem Technology and Nanotechnology Nr. 2218	
WS 3 SWS Elektronische Bauelemente Electronic components Nr. 2209	WS 2 SWS Werkstoffe der Elektrotechnik Materials of electrical Engineering (ET und Mechatronik) Nr. 5605	SS 2 SWS Grundlagen der technischen Optik Basics of technical Optics Nr. 2272	WS 2 SWS Grundwissen der Elektronik Basic knowledge of Electronics (Informatik und Wilng) Nr.2206

1. Introduction

in the lecture: emphasis on methodology

motivation: frequency multiplexing in optical communication systems,

colours of some exotic butterflies and trogons by photonic crystals:

looking into the successful solutions of nature, a promising approach for an advanced working engineer

2. General requirements on information transmission

3. Fundamental principles in optics

- Differentiation: ray optics \leftrightarrow wave optics \leftrightarrow quantum optics
- refractive optics \leftrightarrow diffractive optics
- Refractive index, polarisation, interference, diffraction, coherence
- material properties of glass; dispersion, absorption

4. Optical waveguiding

- waveguides
- fibres
- special emphasis on
 - intermode dispersion: modal dispersion
 - intramode dispersion: material dispersion and waveguide dispersion

5. Interferometers (Michelson, Fabry-Pérot, Mach-Zehnder)

6. Multilayer mirrors and interference filters

7. Introduction to lasers

- material properties of semiconductors: electrons, holes, band structure
- pn-homojunction, pn-heterojunction
- optical and electrical confinement
- absorption of radiation, emission of light
- different cavity and resonator structures (e.g. edge and surface emitters)
- in-plane FP, in-plane DFB, in-plane DBR, VC arrays

8. Introduction to LEDs

- principles, materials, sensitivity of the human eye, applications

9. Light detecting/absorbing devices:

- photodiodes
- solar cells

10. Microoptics

Recommended literature / Literaturempfehlung

1) Optoelectronic devices + semiconductor lasers / Komponenten der Optoelektronik + Halbleiterlaser

- S. Kasap, H. Ruda and Y. Boucher:
Illustrated Handbook of Optoelectronics and Photonics, Cambridge University Press, 2009
- S. O. Kasap:
Optoelectronics and photonics, Prentice Hall, 2001
- J. Gowar:
Optical Communication Systems, 2nd Ed., Prentice Hall, 1993
- H. Hillmer and S. Hansmann
Semiconductor Lasers, from Handbook of Lasers and Optics Chapter 11.3, 1st Edition, Ed. F. Träger,
Springer, ISBN-10:0-387-95579-8, pages 695-726 ; ISBN-13:978-0-387-95579-7
http://www.springerlink.com/content/v9r801/?sortorder=asc&p_o=0
- H. Hillmer and T. Kusserow
Semiconductor Lasers, from Handbook of Lasers and Optics Chapter 11.3, 2nd Edition, Ed. F. Träger,
Springer, ISBN-978-3-642-19408-5, pages 757-792
- J. Singh:
Semiconductor Devices – an Introduction, McGraw-Hill
- J. Singh:
Semiconductor Devices - Basic Principles, John Wiley & Sons, New York 2001
- J. Jahns, S. Helfert:
Introduction to Micro- and Nano optics, Wiley-VCH, Weinheim, 2012
- K. J. Ebeling:
Integrierte Optoelektronik, 2. Aufl., Springer Verlag, 1992
- H. Fouckhardt:
Photonik, Teubner Verlag, Stuttgart 1994
- H. Fouckhardt:
Halbleiterlaser – unter Verwendung Fourier-optischer Methoden, Vieweg + Teubner Verlag, 2011
- H. Hultsch (Herausgeber):
Optische Telekommunikationssysteme, Damm Verlag, 1996
- W. Bludau:
Halbleiter-Optoelektronik, Hanser Verlag, 1995
- T.E. Sale:
Vertical Cavity Surface Emitting Lasers, RSP, John Wiley & Sons, Chichester, UK, 1995
- C. Breck Hitz:
Understanding Laser Technology, PennWell Books, Tulsa, Oklahoma, 1985
- L. A. Coldren and S. W. Corzine:
Diode Lasers and Photonic Integrated Circuits, John Wiley & Sons, New York 1995
- S. L. Chuang:
Physics of Optoelectronic Devices, John Wiley & Sons, New York 1995
- W. Harth and H. Grothe:
Sende- und Empfangsdioden für die optische Nachrichtentechnik, Teubner Verlag, Stuttgart 1994
- M. Young:
Optik, Laser, Wellenleiter, Springer-Verlag, Heidelberg, 1997
- M. Young:
Optics and lasers, Springer-Verlag, Heidelberg, 1993
- P. Bhattacharya:
Semiconductor Optoelectronic Devices, 2nd edition, Prentice Hall, London 1997
- F. K. Kneubühl und M. W. Sigrist:
Laser, Teubner Verlag, 1995
- O. Svelto and D. C. Hanna:
Principles of Lasers, 4th edition, Plenum Press, New York 1998
- G.P. Agrawal and N.K. Dutta:
Long-Wavelength Semiconductor Lasers, Van Nostrand Reinhold, New York, 1986
- H. Ghafouri-Shiraz und B.S.K. Lo:
Distributed Feedback Laser Diodes: Principles and Physical Modelling, John Wiley & Sons, Chichester, UK, 1996
- S. M. Sze:
Physics of semiconductor devices , John Wiley & Sons, New York
- V. Brückner:
Optische Nachrichtentechnik: Grundlagen und Anwendungen, Teubner Verlag, Stuttgart, 2003

H.Hillmer und J. Salbeck:

Kap. 8, "Materialien der Optoelektronik – Grundlagen und Anwendungen", in Bergmann Schäfer, Band 6, Festkörper, Auflage 2005, Walter de Gruyter Verlag, Berlin, New York.

J.G. Proakis und M. Salehi:

Grundlagen der Kommunikationstechnik, 2. Auflage, Pearson Studium, München, 2004

B.E.A. Saleh and M.C. Teich:

Fundamentals of Photonics, John Wiley & Sons, Inc., 1991

O. Solgaard:

Photonic Microsystems – Micro and Nanotechnology Applied to Optical Devices and Systems, Springer Science+Business Media, 2009

Ulrich Hahn:

Physik für Ingenieure Band 1: Mechanik, Thermodynamik, Schwingungen und Wellen, 2015

Physik für Ingenieure Band 2: Elektrizität und Magnetismus, Optik, Messungen und ihre Auswertung, 2015

2) Optical communications / Optische Nachrichtentechnik

J. H. Franz, V. K. Jain:

Optical Communication, Narosa, New Dehli

J. Gowar:

Optical Communication Systems, 2nd Ed., Prentice Hall, 1993

G. Grau und W. Freude:

Optische Nachrichtentechnik, Springer Verlag, 1991

H. G. Unger:

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H. Hultsch (Herausgeber):

Optische Telekommunikationssysteme, Damm Verlag, 1996

J. M. Senior:

Optical Fiber Communications, 2nd Ed., Prentice Hall, 1993

G. Winstel und C. Weyrich:

Optoelektronik I, Serie Halbleiter-Elektronik, Band 10, Springer Verlag

G. Winstel und C. Weyrich:

Optoelektronik II, Serie Halbleiter-Elektronik, Band 11, Springer Verlag

Y. Suematsu, K. I. Iga:

Introduction to optical fibre communications

V. Brückner:

Optische Nachrichtentechnik: Grundlagen und Anwendungen, Teubner Verlag, Stuttgart, 2003

3) Technology of electronic and optoelectronic devices -

Technologie der elektronischen und optoelektronischen Bauelemente

S. Büttgenbach:

Mikromechanik - Einführung in Technologie und Anwendungen, 2. Auflage, Teubner Verlag, Stuttgart 1994

H. I. Smith:

Submicron- and nanometer-structures technology, 2nd edition, NanoStructures Press, 437 Peakham Road, Sudbury, MA 01776, USA, 1994

H. Hultsch (Herausgeber):

Optische Telekommunikationssysteme, Damm Verlag, 1996

H. Beneking:

Halbleiter-Technologie - Eine Einführung in die Prozeßtechnik von Silizium und III-V-Verbindungen

Teubner Verlag, Stuttgart 1991

I. Ruge und H. Mader:

Halbleitertechnologie, Serie Halbleiter-Elektronik, Band 4, Springer Verlag, 1991

J. Jahns, S. Helfert:

Introduction to Micro- and Nano optics, Wiley-VCH, Weinheim, 2012

L. F. Thompson, C. G. Willson, and M. J. Bowden:

Introduction to Microlithography, 2nd edition, ACS Professional Reference Book, American Chemical Society, 1994

D. V. Morgan and K. Board:

An introduction to semiconductor microtechnology, 2nd edition, John Wiley & Sons, Chichester 1994

S. M. Sze:

Semiconductor devices - Physics and technology, John Wiley & Sons, New York 1985

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Modern Semiconductor Device Physics , John Wiley & Sons, New York 1998

W. M. Moreau

- Semiconductor Lithography - principles, practices and materials, Plenum Press, 1991
 G.P. Agrawal and N.K. Dutta:
 Long-Wavelength Semiconductor Lasers, Van Nostrand Reinhold, New York, 1986
 U. Hartmann:
 Nanostrukturforschung und Nanotechnologie, Band 1: Grundlagen, Oldenbourg Verlag, München, 2012
 U. Hilleringmann
 Silizium-Halbleitertechnologie, 3. Auflage, Teubner Verlag, Stuttgart, 2002
 H.-G. Wagemann, T. Schönauer:
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 Springer, ISBN-978-3-642-19408-5, pages 757-792
 B. Bhushan (Editor):
 Springer Handbook of Nanotechnology, Springer Verlag Berlin Heidelberg, 2004
<http://www.springerlink.com/content/m02080/>
 M. Wautelet et al.:
 Nanotechnologie, Oldenbourg Verlag München, 2008
 N. Schwesinger, Carolin Dehne, Frederic Adler:
 Lehrbuch Mikrosystemtechnik: Anwendungen, Grundlagen, Materialien und Herstellung von Mikrosystemen;
 Oldenbourg Verlag München, 2009
 O. Solgaard:
 Photonic Microsystems – Micro and Nanotechnology Applied to Optical Devices and Systems, Springer
 Science+Business Media, 2009

4) Microsystem technology - *Mikromechanik und Mikrosystemtechnik*

- W. Menz, J. Mohr und O. Paul:
 Microsystem Technology, VCH Verlag, 2001
 W. Menz und J. Mohr:
 Mikrosystemtechnik für Ingenieure, 2. Aufl., VCH Verlag, 1997
 S. Fatikov, U. Remold,
 Microsystem Technology and Microrobotics, Springer 1997
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 Mikrosystemtechnik, Spektrum der Wissenschaften, Sonderband 4
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 K. J. Ebeling:
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 Mikrosystemtechnik: Prozessschritte, Technologien, Anwendungen, Teubner Verlag, 2006
 N. Schwesinger, Carolin Dehne, Frederic Adler:
 Lehrbuch Mikrosystemtechnik: Anwendungen, Grundlagen, Materialien und Herstellung von Mikrosystemen;
 Oldenbourg Verlag München, 2009
 O. Solgaard:
 Photonic Microsystems – Micro and Nanotechnology Applied to Optical Devices and Systems, Springer
 Science+Business Media, 2009

as well as papers from current journals (ask the lecturer!)

5) For refreshing the basics in optics - zur Wiederholung der Grundlagen in Optik

F. and L. Pedrotti:

Introduction to optics, Prentice Hall, 1993

F. Pedrotti, L. Pedrotti, W. Bausch und H.

Schmidt: Optik - eine Einführung,
Prentice Hall, 1996

L. Bergmann und C. Schäfer:

Lehrbuch der Experimentalphysik, Band III, Optik, 1993

M. Born and E. Wolff:

Principles of optics, sixth edition, 1997, Cambridge University Press

6) For refreshing the basics in semiconductor electronics - zur Wiederholung der Grundlagen in Halbleiter-Elektronik

R. Müller:

Grundlagen der Halbleiter-Elektronik, Serie Halbleiter-Elektronik, Band 1, Springer Verlag

R. Müller:

Bauelemente der Halbleiter-Elektronik, Serie Halbleiter-Elektronik, Band 2, Springer
Verlag (Für Spezialisten und für später: Bände 3-15 von verschiedenen Autoren)

S. M. Sze:

Semiconductor devices, John Wiley & Sons, New York 1985.

S. M. Sze:

Modern Semiconductor Device Physics , John Wiley & Sons, New York 1998

K. Bystron/ J. Borgmeyer:

Grundlagen der Technischen Elektronik, Carl Hanser Verlag, München Wien, 1990

A. Möschwitzer:

Grundlagen der Halbleiter & Mikroelektronik, Band 1: Elektronische Halbleiterbauelemente, Carl
Hanser München 1993

P. Horowitz, W. Hill:

The art of electronics, Cambridge University Press, 1989

E. Böhmer:

Elemente der angewandten Elektronik, Vieweg Verlag

K. Hoffmann:

Systemintegration: Vom Transistor zur großintegrierten Schaltung, Oldenbourg Wissenschaftsverlag,
2003 H.- G. Wagemann, T. Schönauer:

Silizium- Planartechnologie: Grundprozesse, Physik und Bauelemente, Teubner Verlag, 2003

R. Sauer:

Halbleiterphysik – Lehrbuch für Physiker und Ingenieure, Oldenbourg Verlag, München 2009

7) Foundations in mathematics – Grundlagen der Mathematik

Erwin Kreyszig:

Advanced engineering mathematics, John Wiley & Sons, New York

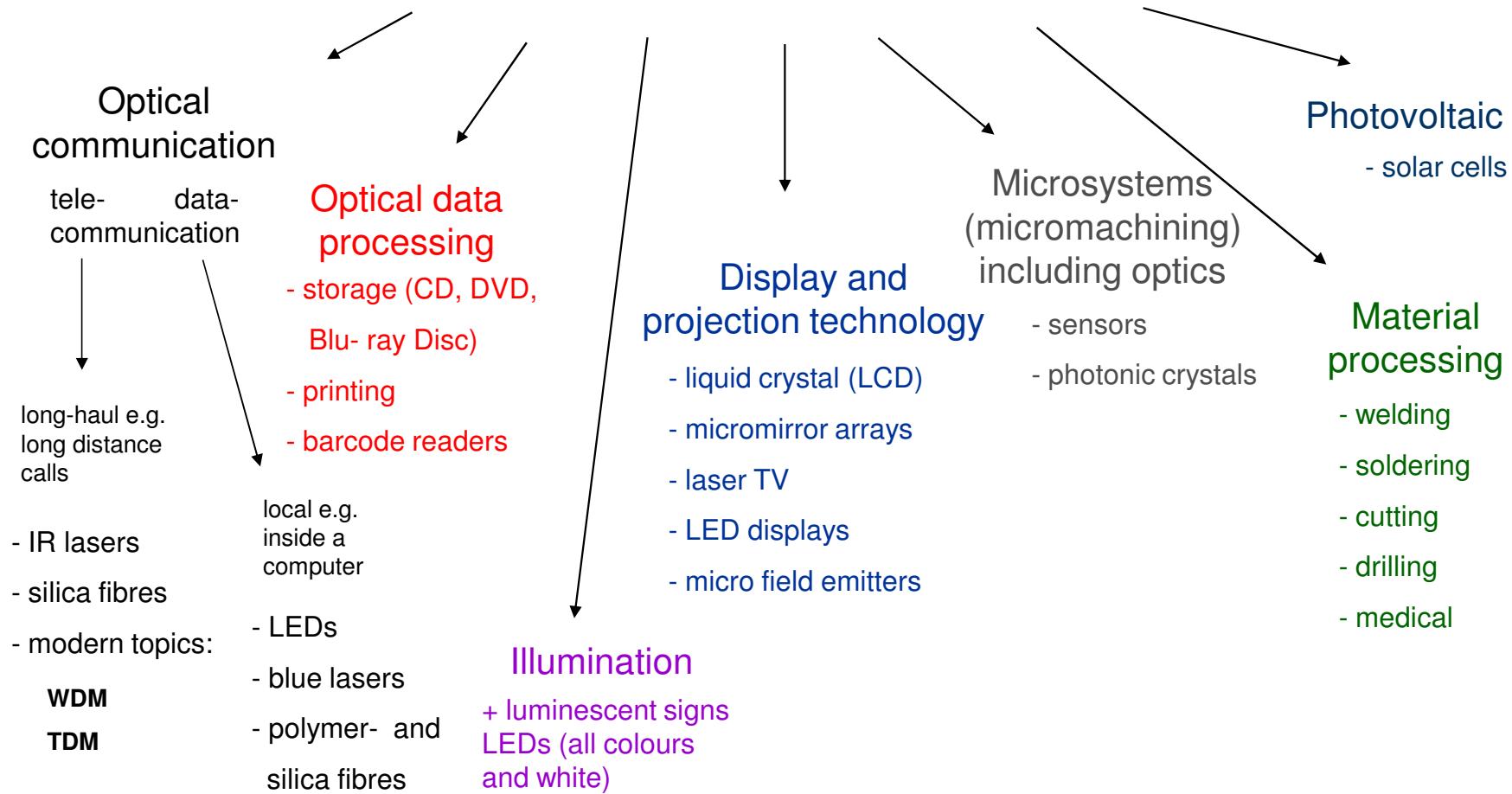
Motivation of the lectures

**optoelectronic devices
and
semiconductor lasers**

Chapter 1

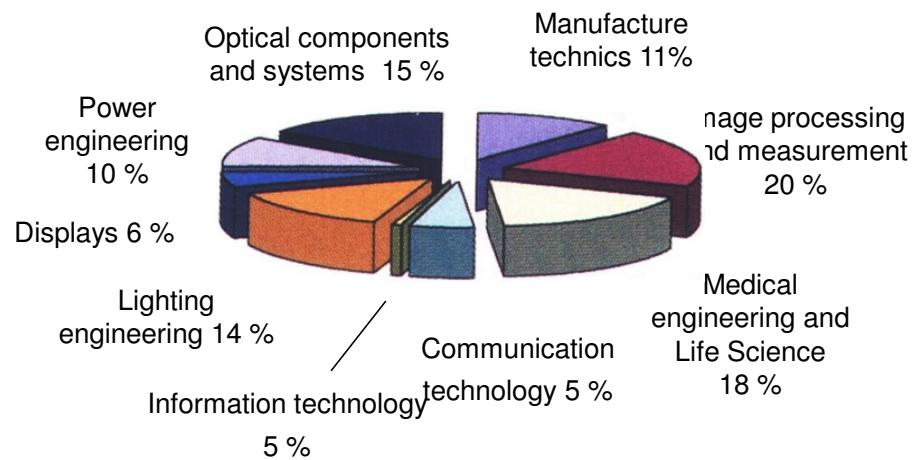
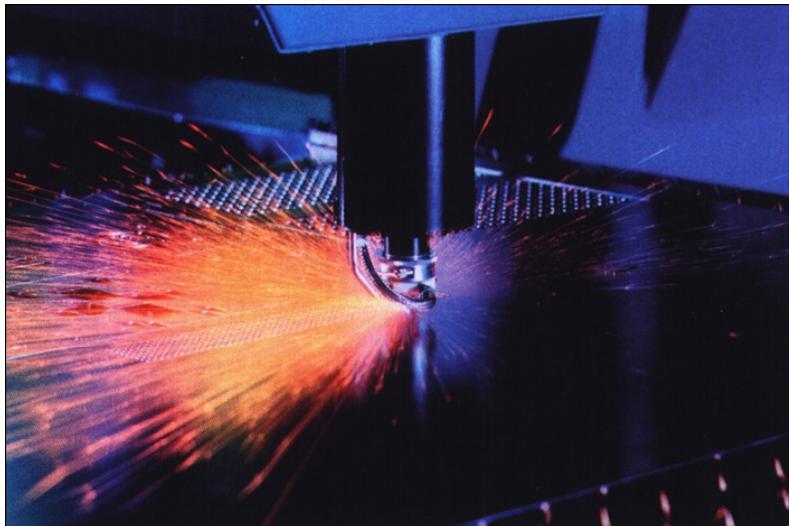
Introduction

Optoelectronics (Photonics)



Market segments of optical technologies

optoelectronic devices



Direct application of lasers : in production technology this laser drills highly precise holes (500 holes / min)

The optical technologies contain nine fields. The biggest fraction in Germany in 2005 was image processing and measurement field.

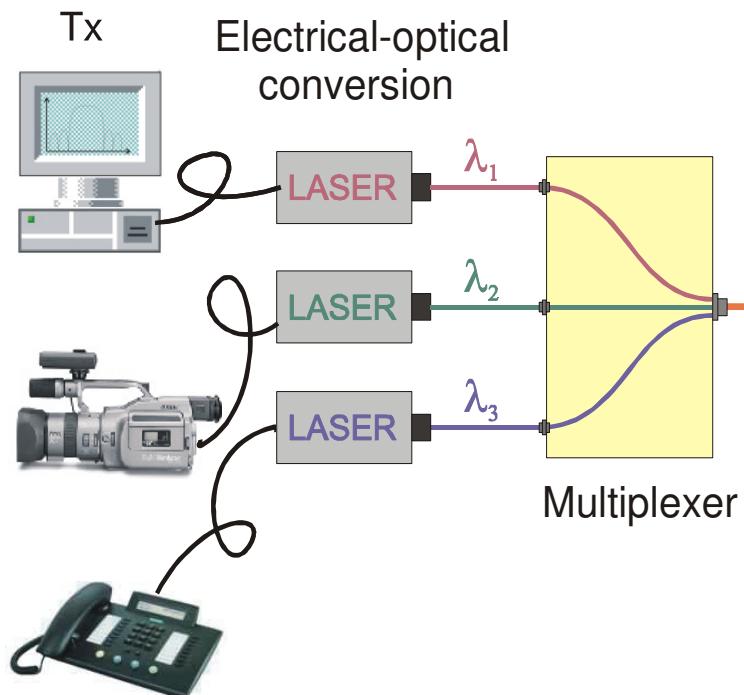
All direct applications: cutting, drilling, soldering, welding

Motivation I

Optical communication, ultra-high optical data rates optoelectronic devices

example for 3 wavelengths in a single fibre
(wavelength division multiplex)

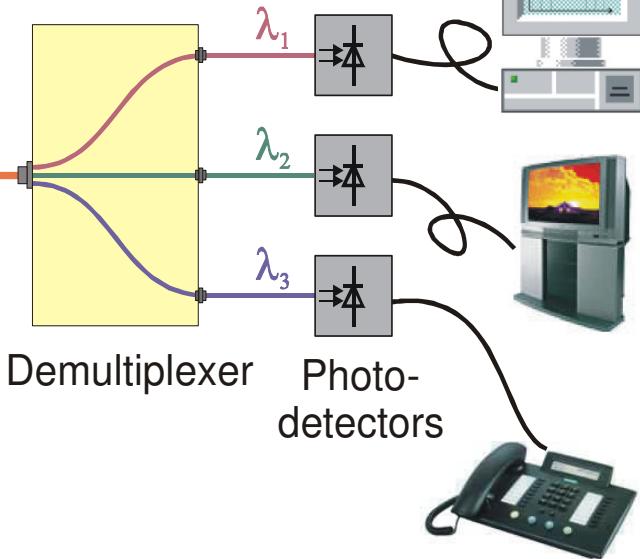
Transmitter



Transmission



Optical-electrical conversion



Receiver

Real-time transmission of video, control data, voice over 7000 km

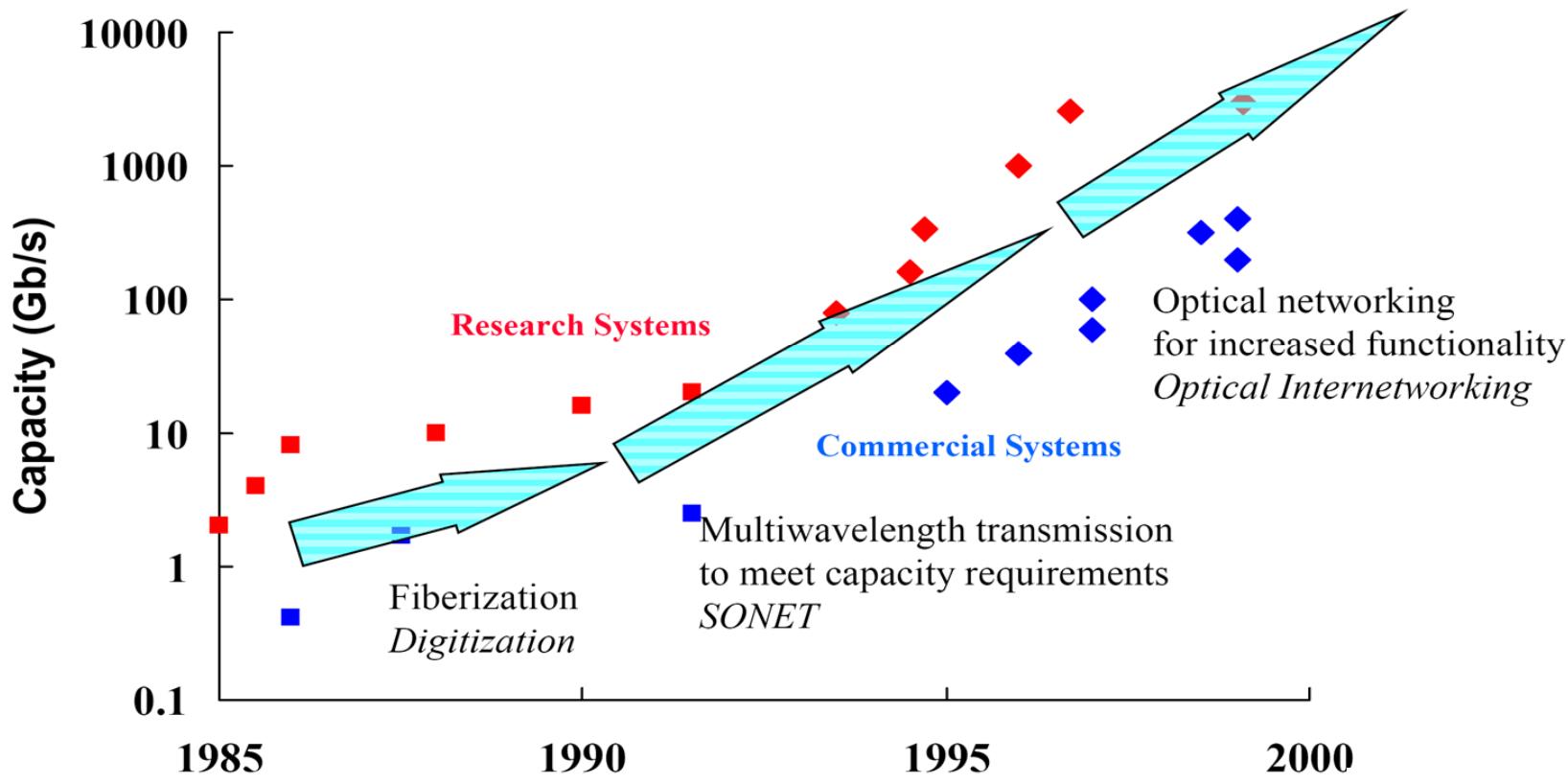


- **surgery on a human patient**
- **7000 km between**
 - Strasbourg, France (patient)
 - New York, USA (surgeon)
- **time delay 155 ms**
 - (for surgery to be feasible,
acceptable time delay < 330 ms)
- **operation performed in 54 min.**
- **high – speed 10 Gbit/s fibre optic link**
 - video
 - data for robotic system
 - telephone

Motivation II

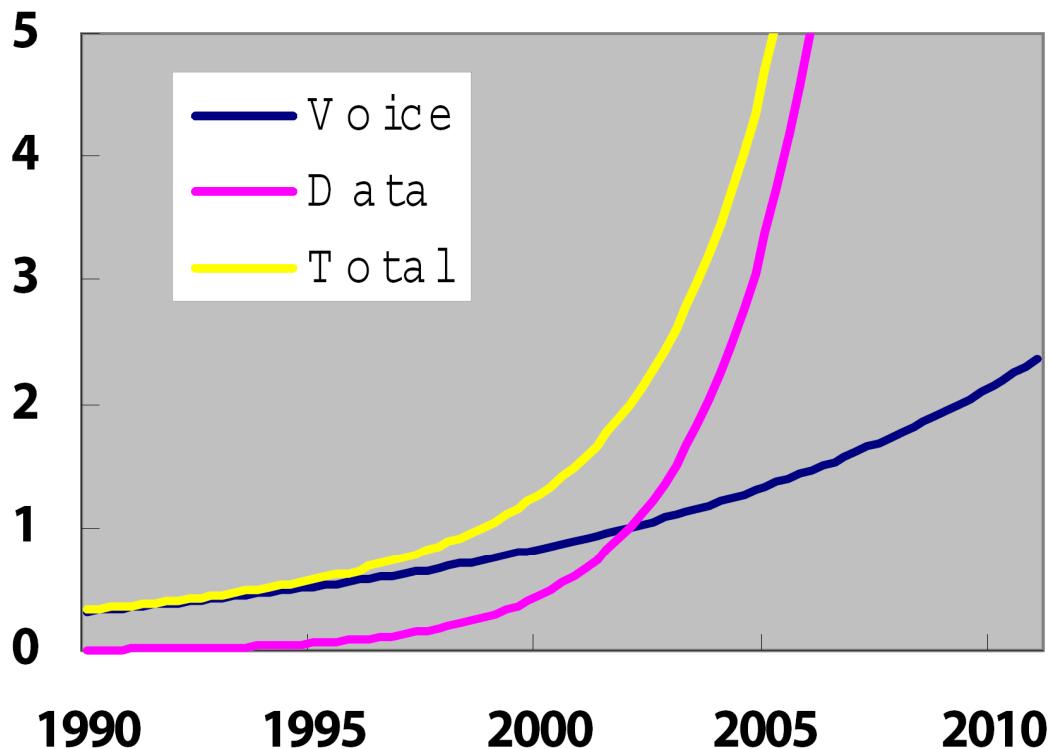
Lightwave technology eras

optoelectronic devices



Network traffic: the shift to data I

optoelectronic devices



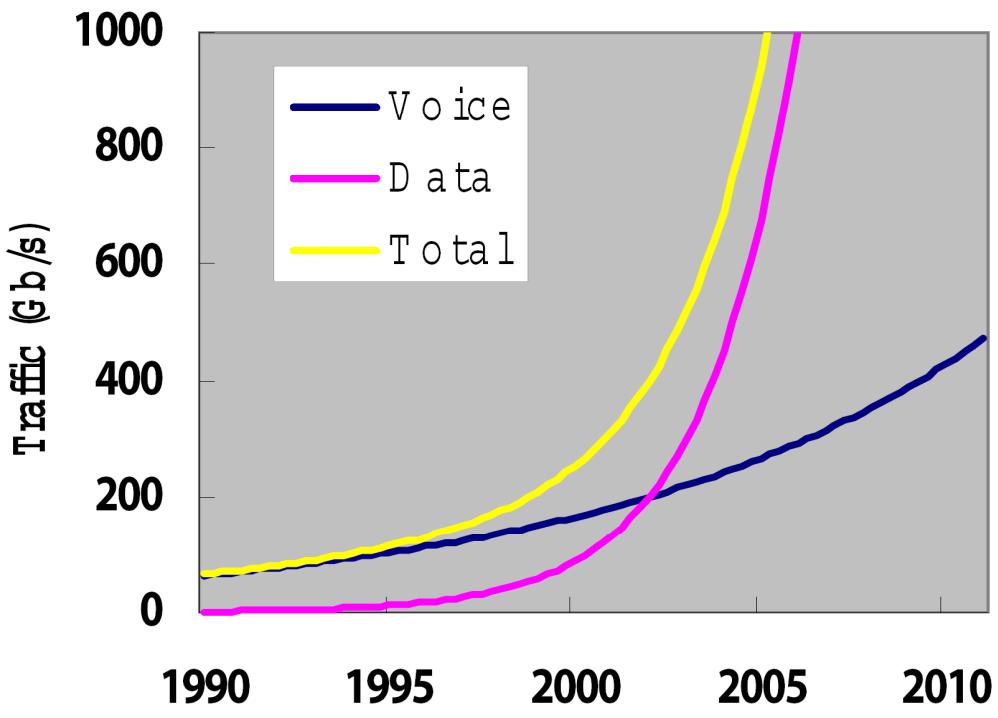
- ◆ Yearend 1997
- ◆ Voice growth assumed 10%
- ◆ Data growth assumed 50%
- ◆ Voice/Data crossover at 2002

K. G. Coffman and A. Odlyzko
AT&T Labs



Network traffic: the shift to data II

optoelectronic devices

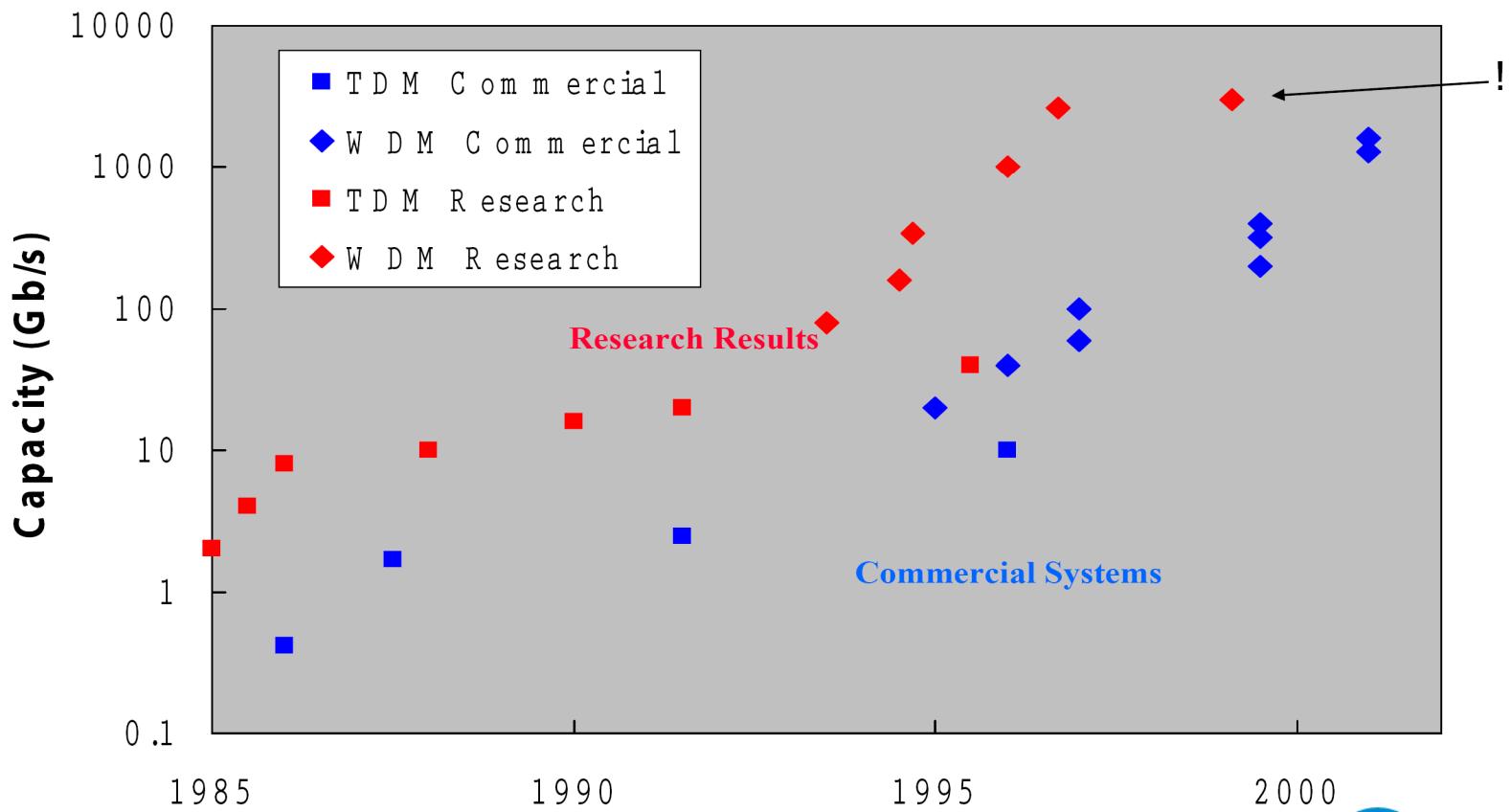


- ◆ Total backbone traffic is comparable to the capacity of new single-fiber systems
- ◆ Between the availability of new systems and the ubiquitous deployment of their capacity lies billions of dollars and tremendous effort
- ◆ Next generation systems have the potential to outstrip demand - maybe



Single fibre capacity

optoelectronic devices



Bionics

(a thrilling combination of
technics / engineering and biology)

... looks into the
principles of success in nature

... looking for possible applications in engineering

... a philosophy for advanced working engineers

Filters tuning light Quetzal family of trogones optoelectronic devices



Lives in ...

... rain forests of
central America

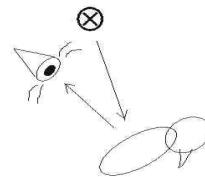
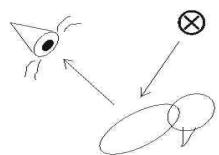
Flag bird of the state of
Guatemala

Generation of opalescent colours in nature

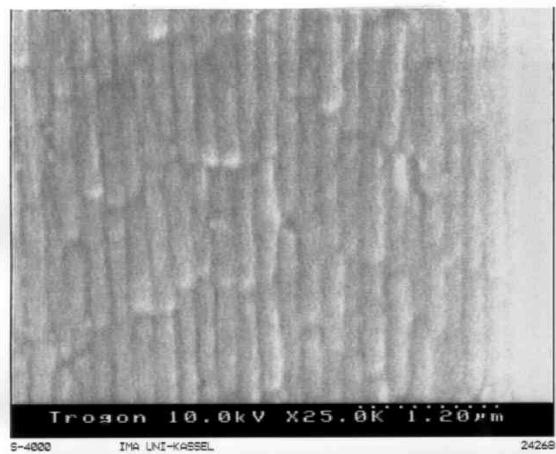
Bionics

optoelectronic devices

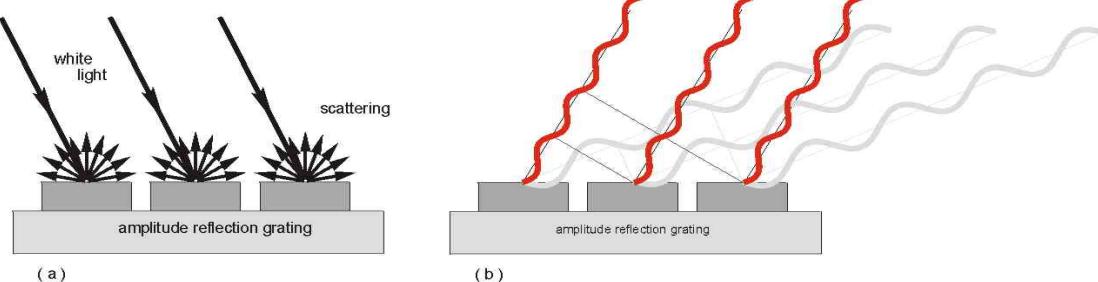
Colour tuning by moving light source



Periodic gratings on wingfeathers of a violet trogon



Colour filters based on
constructive interference

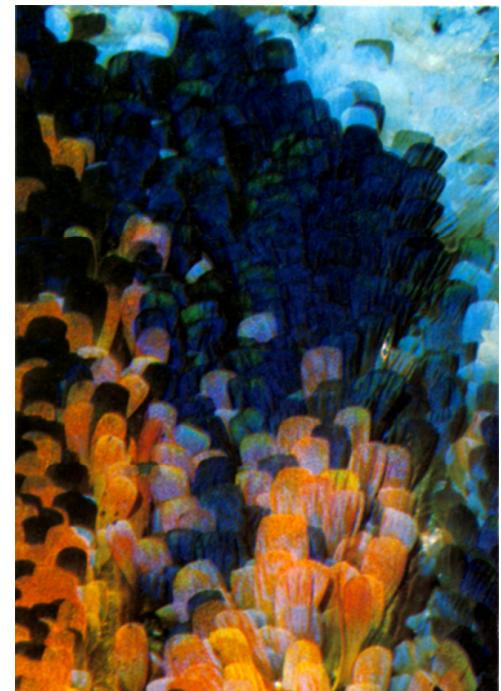
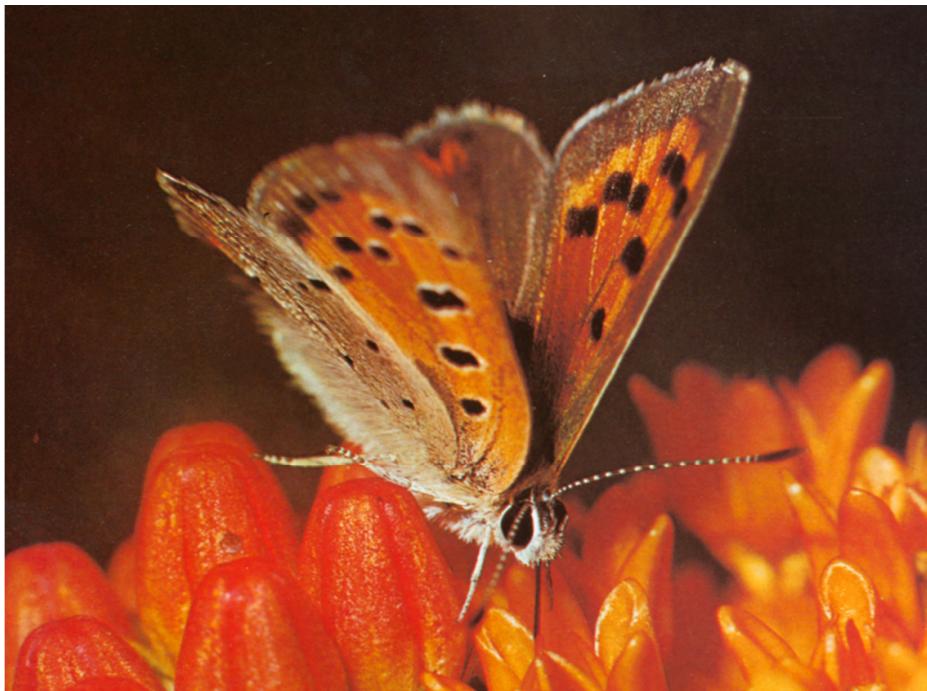


1D
photonic crystal

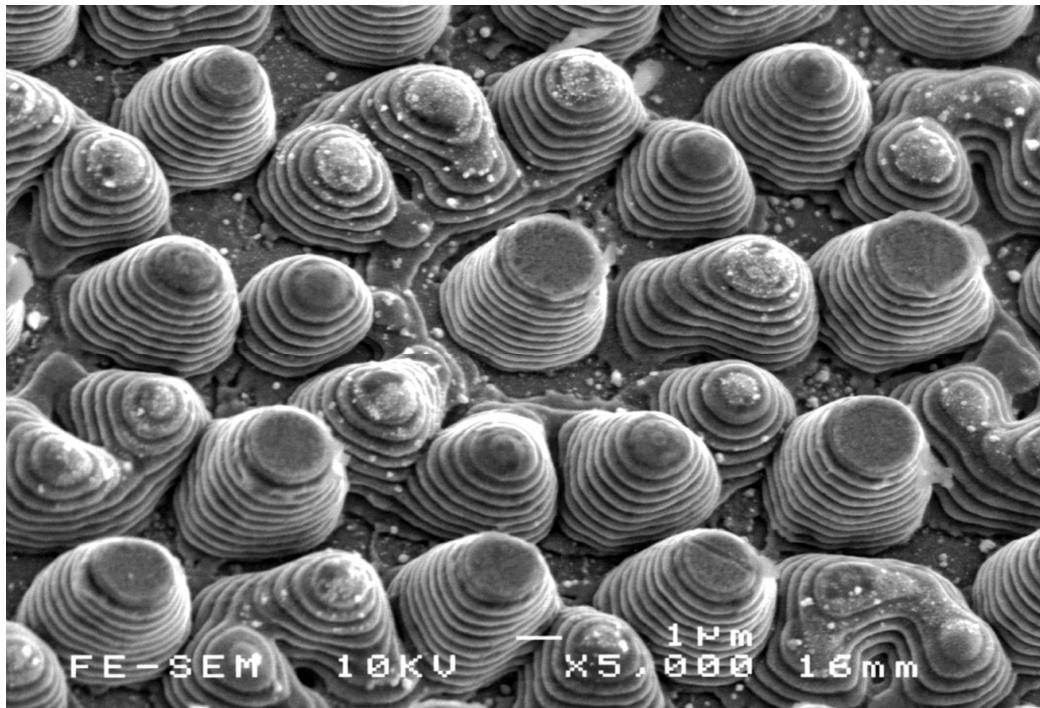
Colour tuning by tilting or rotation

colour appearance:

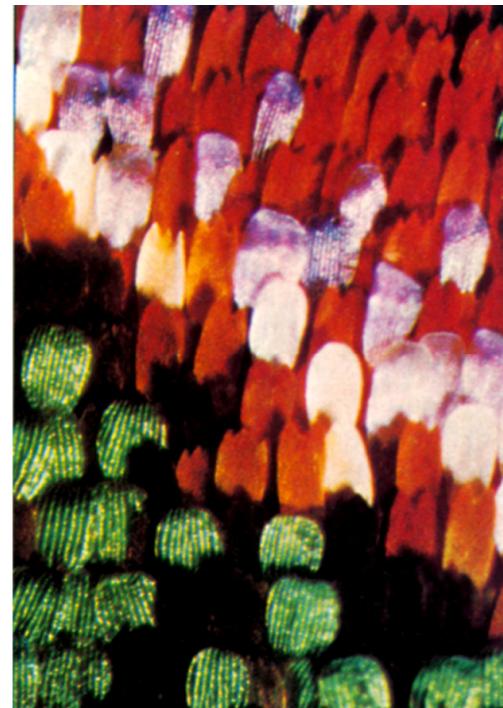
- a) pigments provide the colours
- b) periodic alignment of scales/layers



Example for a) south American castnia



FE-SEM 10kV — $\times 5,000$ 1 μm



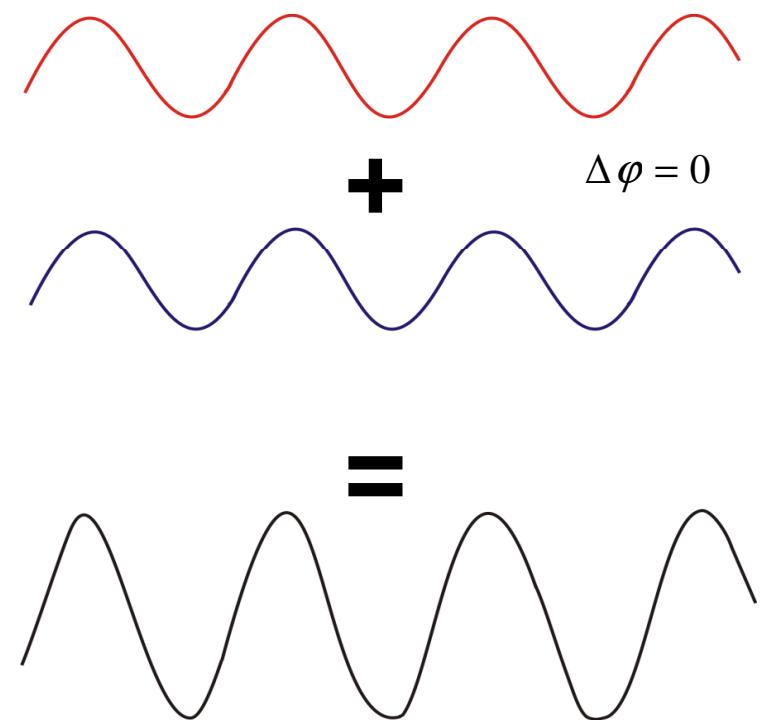
varying colour impression due to different observation angles
example for b)

Asian swallowtail
(*papilio machaon*)

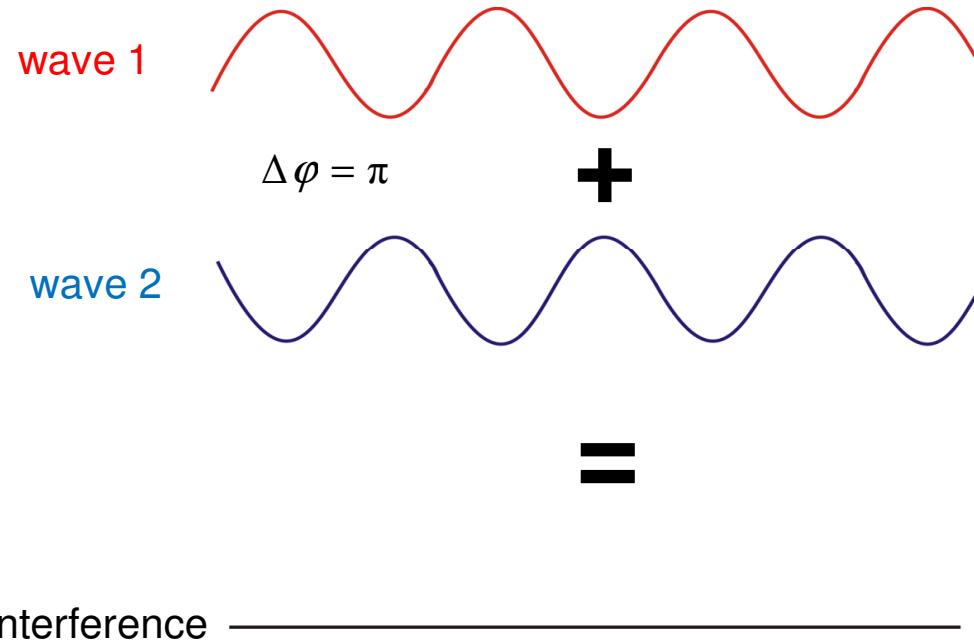
Interference of two waves of identical wavelength

optoelectronic devices

constructive Interference



destructive Interference

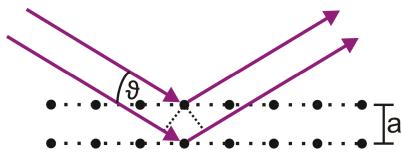


Micro- and Nanostructures

Light Wavelength Selection

optoelectronic devices

X-ray diffraction at
lattice planes of
solid state crystals

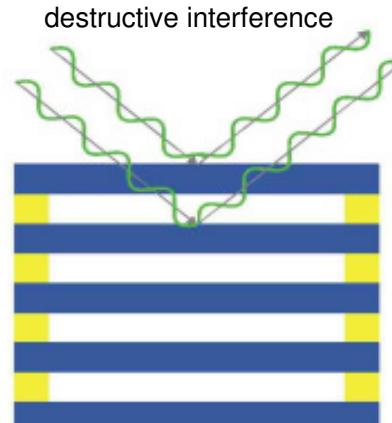
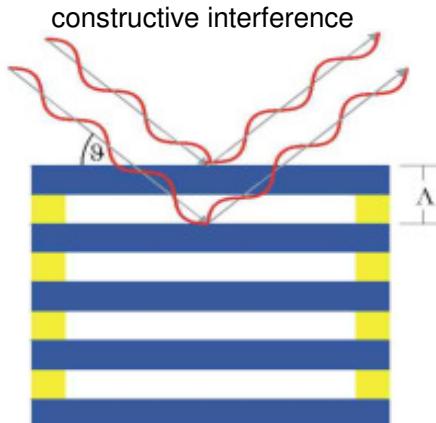


Bragg-condition:

$$2a \sin\vartheta = m\lambda$$

lattice constant: $a \approx 0.3 \text{ nm}$
X-ray wavelength λ
 $m=1, 2, 3\dots$

diffraction of light (IR) at periodically
aligned semiconductor layers



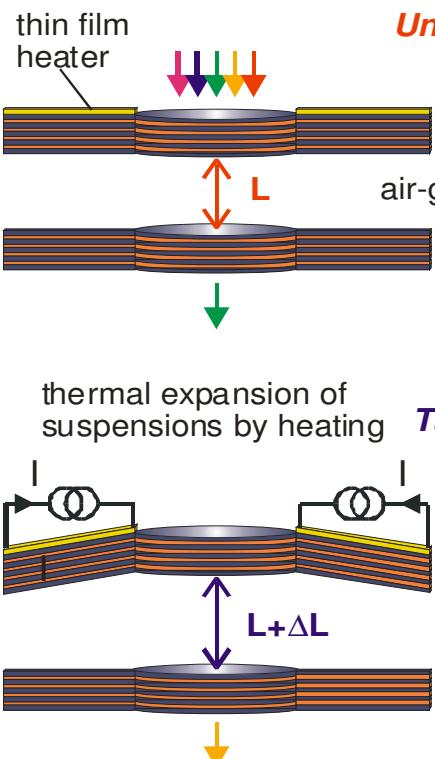
$$\Lambda = \frac{m \lambda_B}{2 \bar{n}_{\text{eff}} \sin \vartheta}$$

grating period $\Lambda = 90 \dots 250 \text{ nm}$
Light wavelength $\lambda_B = 0.6 \dots 1.5 \mu\text{m}$ (in air)

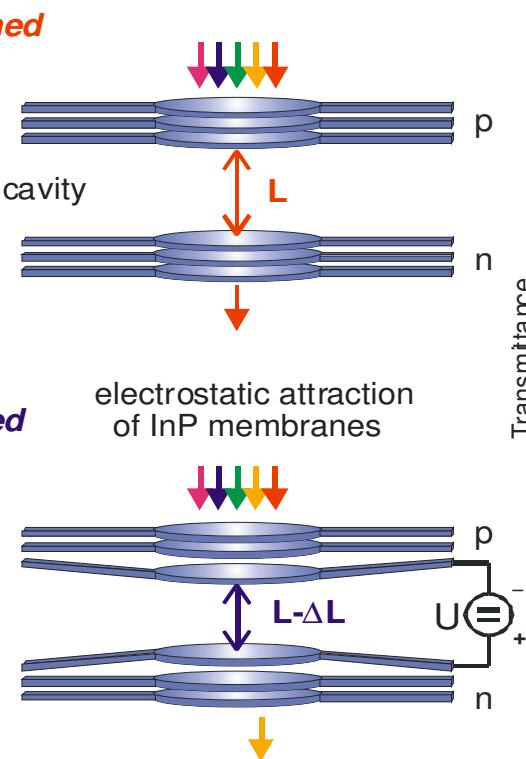
Application: Micromechanical Tunable filters, principles

optoelectronic devices

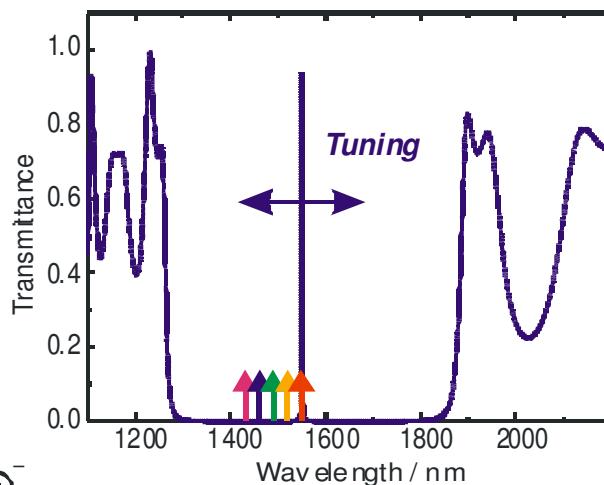
Thermal tuning
for dielectric mirrors



Electrostatic tuning for
semiconductor mirrors

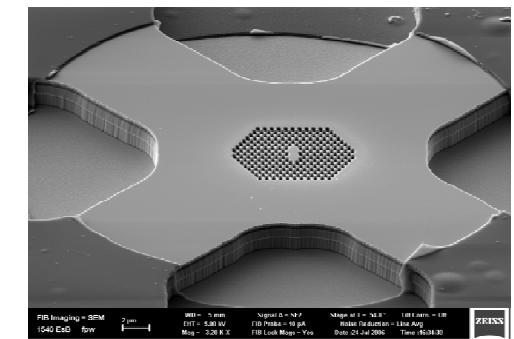
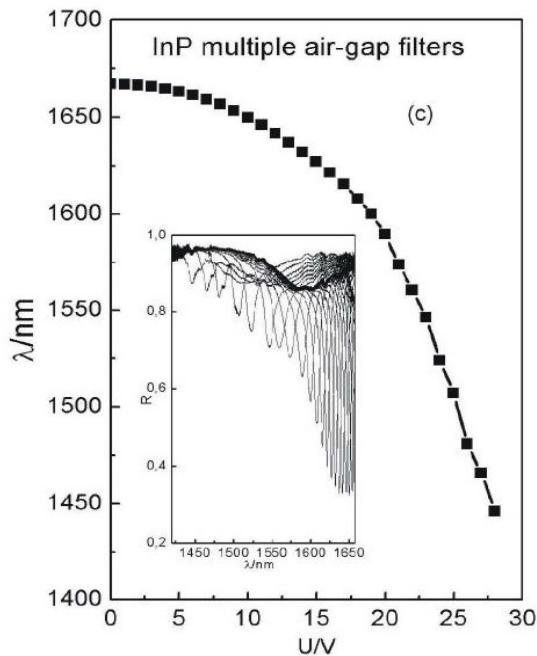
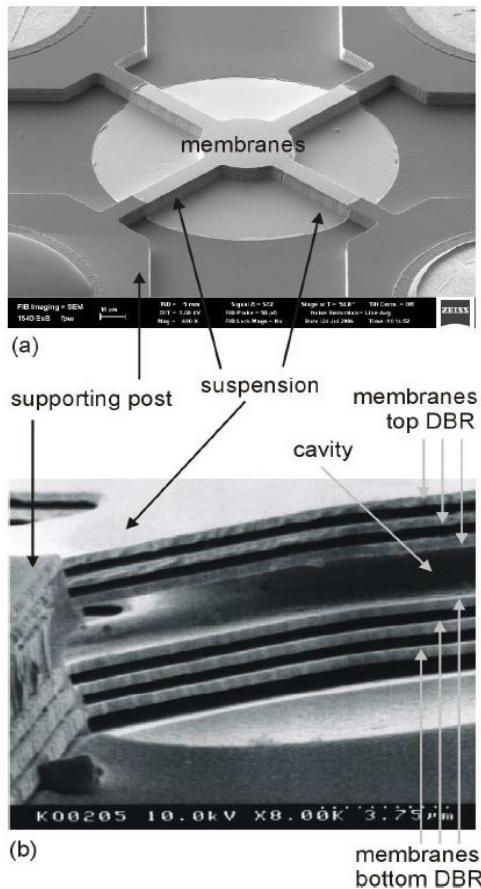


Wavelength tuning achieved
by change of cavity length L



Application of photonic crystals in micromachined tunable filters

optoelectronic devices



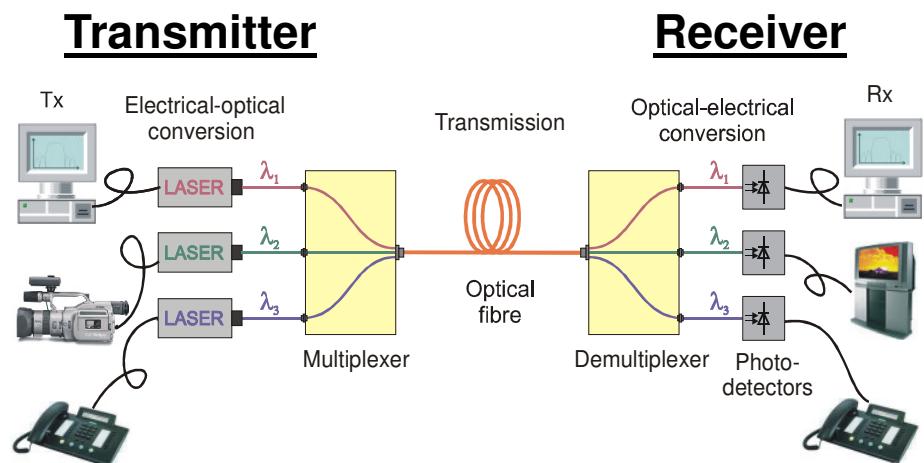
electrostatic actuation
ultra-wide tuning range : 221nm
actuation voltage : 0 ... 28V
continuous tuning
single tuning parameter
ultra-low power consumption
1μA in reverse current

Application of micromachined tunable Fabry Pérot filters

optoelectronic devices

- I. Datacommunication in-house fibre optical networks
- II. Computers, Industrial networks
- III. Sensorics and analytics
- IV. Measurement technology
- V. Confocal microscopy
- VI. Medical applications
- VII. Telecommunication,
in dense wavelength
division multiplexed
systems

example for 3 wavelengths in a single fibre
(wavelength division multiplex)



Institute of Nanostructure technology and Analytics (INA)

optoelectronic devices



Synergies

Electrical
engineering



Physics

NanoNetzwerk Hessen



NanoImprintKonsortium
Hessen



UniKasselTransfer

CINSTAT

Center for Interdisciplinary Nanostructure Science and Technology



- Deposition:
IBD, MBE, PECVD, evaporation, FIB
- Plasma and Ion beam supported etching:
RIE, CAIBE, barrel etching, FIB
- critical point drying
- Lithography: nanoimprint, ion beam, optical, e-beam
- analytics and measurement technology:
FIB, REM, AFM, STM, XRD, PL, REFL
faseroptical characterization (OSA,..)
white light interferometry, ellipsometry

Nanostructuretechnology

Nanophotonics

Nanoelectronics

Nanomechanics

Optoelectronics

Nanosystemtechnology

Ion beam deposition technology at INA in Kassel

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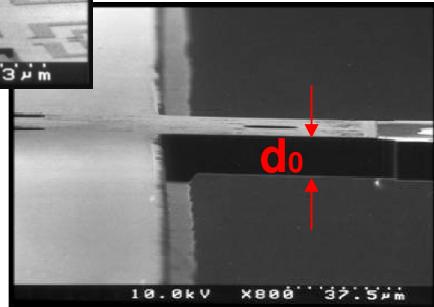
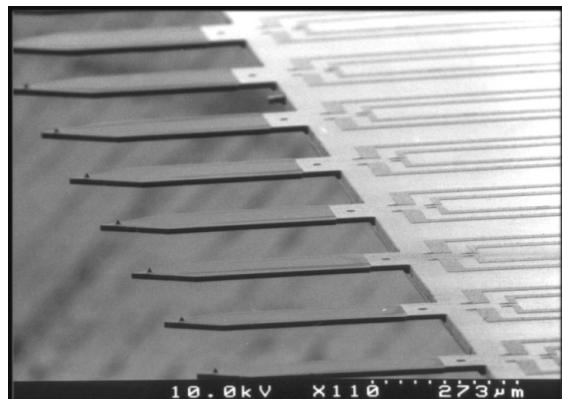
Deposition of multilayer structures:

TiO₂, ZrO₂, SiO₂, Y₃O₄, a-Si, Mo, Ta₂O₅, BC₃, C, ITO, Al₂O₃ ...

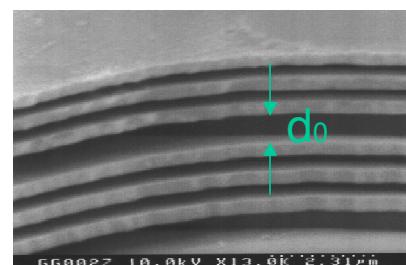
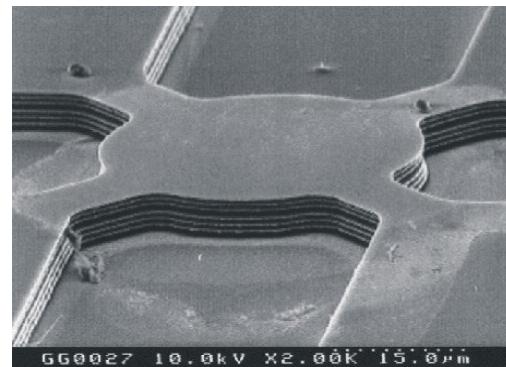
Motivation IV Atomic force microscopy (AFM) cantilever arrays and air gap filters

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AFM cantilever array



all air gap filter



resonant frequency $\sim d_0$

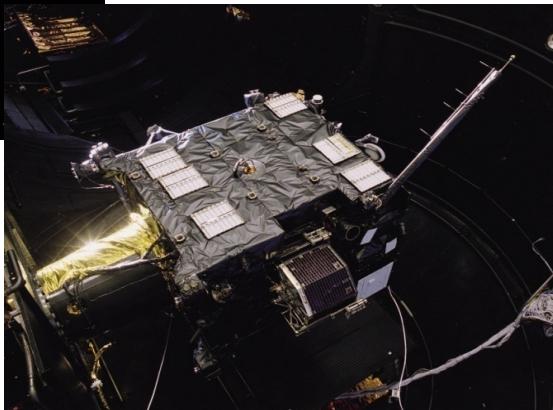
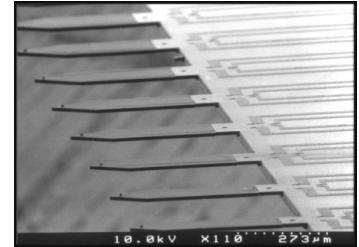
selected wavelength $\sim 2d_0$

AFM cantilever on Rosetta space

optoelectronic devices



use of AFM
cantilever arrays
for precise particle
and gas sensing, via changes
in resonant frequency



Launch date: March 2004

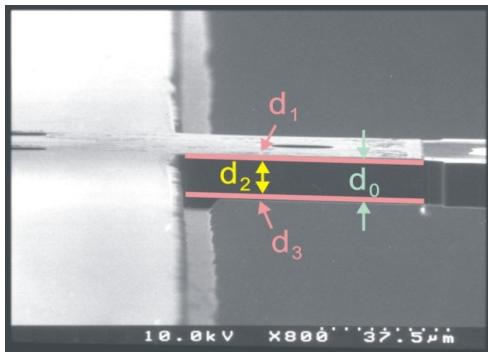
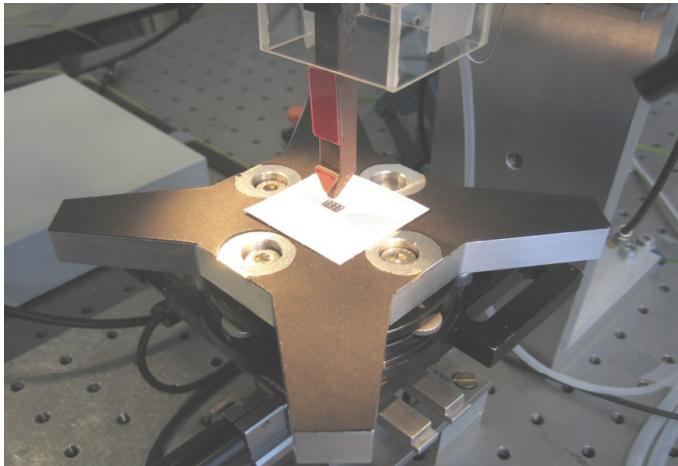
Goal: rendez-vous with comet
„Churyumov-Gerasimenko „

ETA: Mai 2014

images taken from <http://www.dlr.de/DLR-Rosetta/>

Experimental Characterization

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+ measurement of reflectance and transmission spectra as well as mode profiles

+ theoretical model calculations
(1D, up to quasi 3D)

+ line-shape fitting and parameter extraction

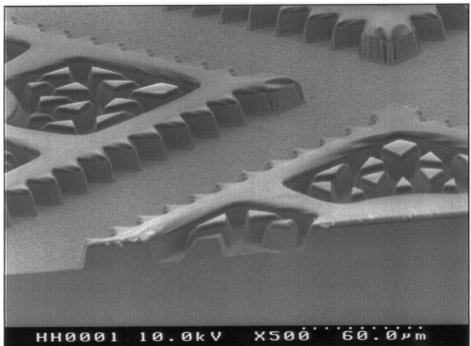
e.g.

variation of parameters d_1 , d_2 , d_3 to achieve optimum agreement

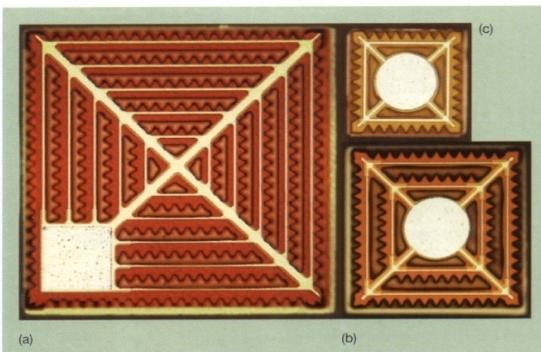
Motivation VI

Ultra-bright LEDs

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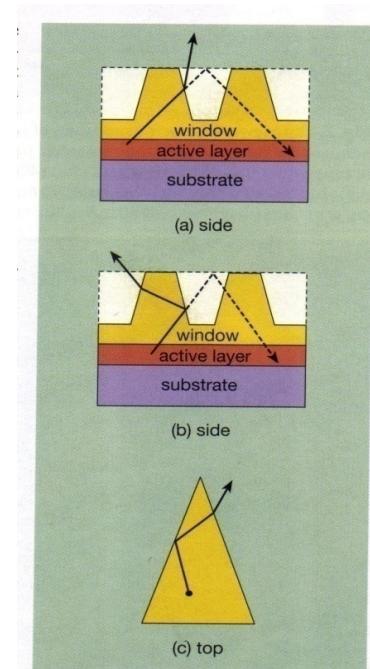
Technological Implementation:
Reactive Ion-Etching (RIE)
(INA Kassel for OSRAM)



Different models
(top-view)

OSRAM

improved
light - extraction



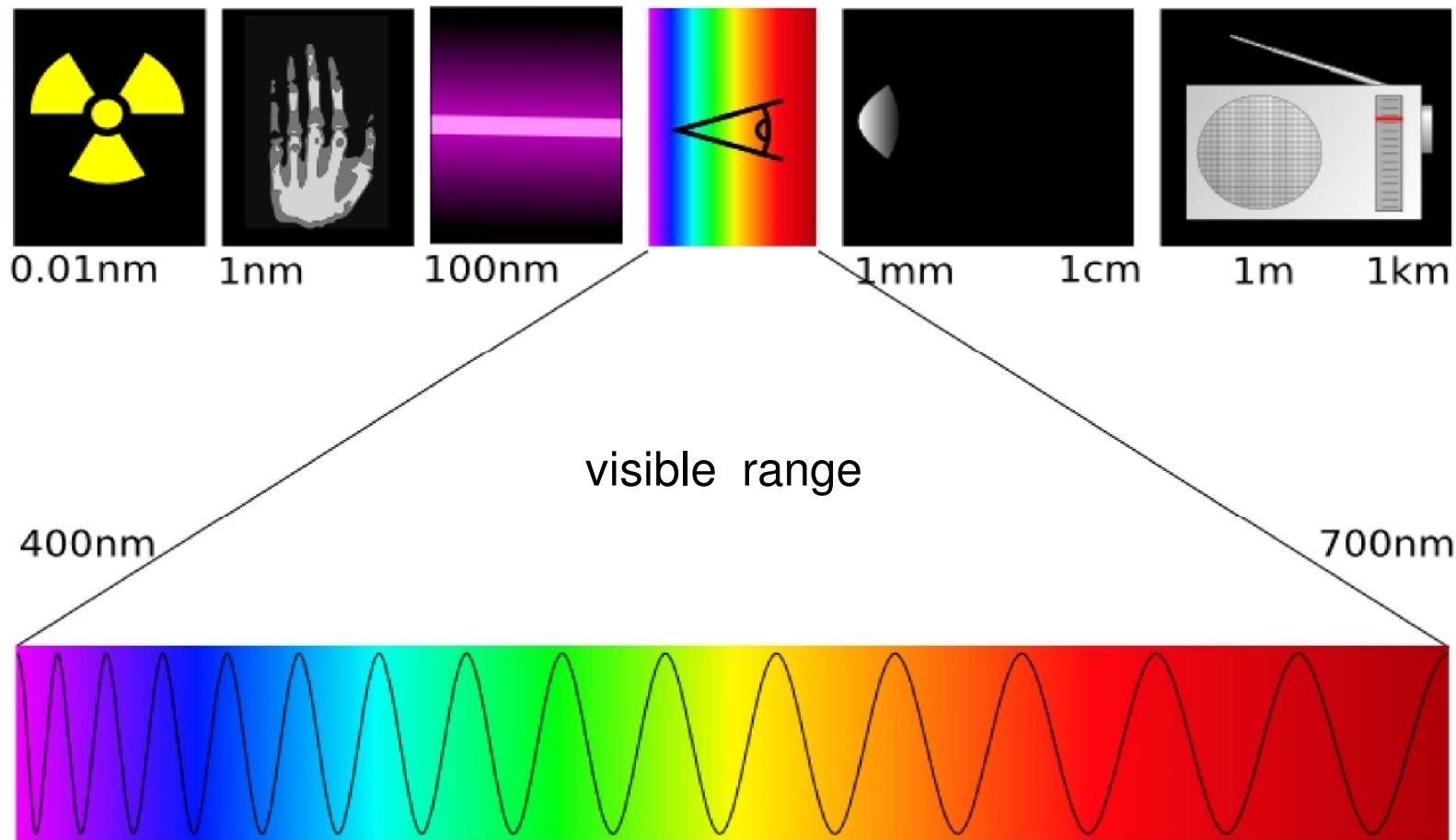
OSRAM

Chapter 2

General requirements on information transmission

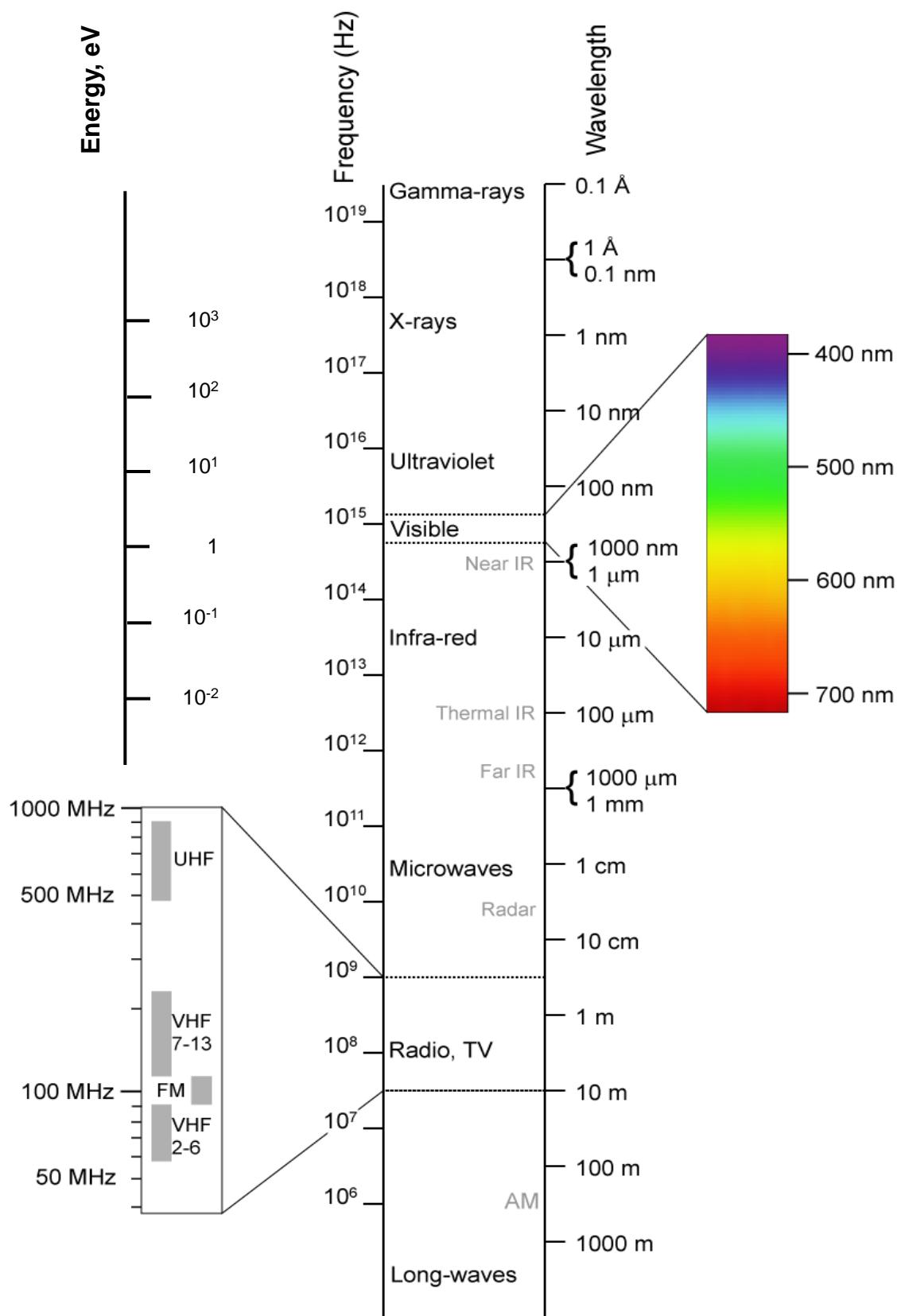
The electromagnetic spectrum

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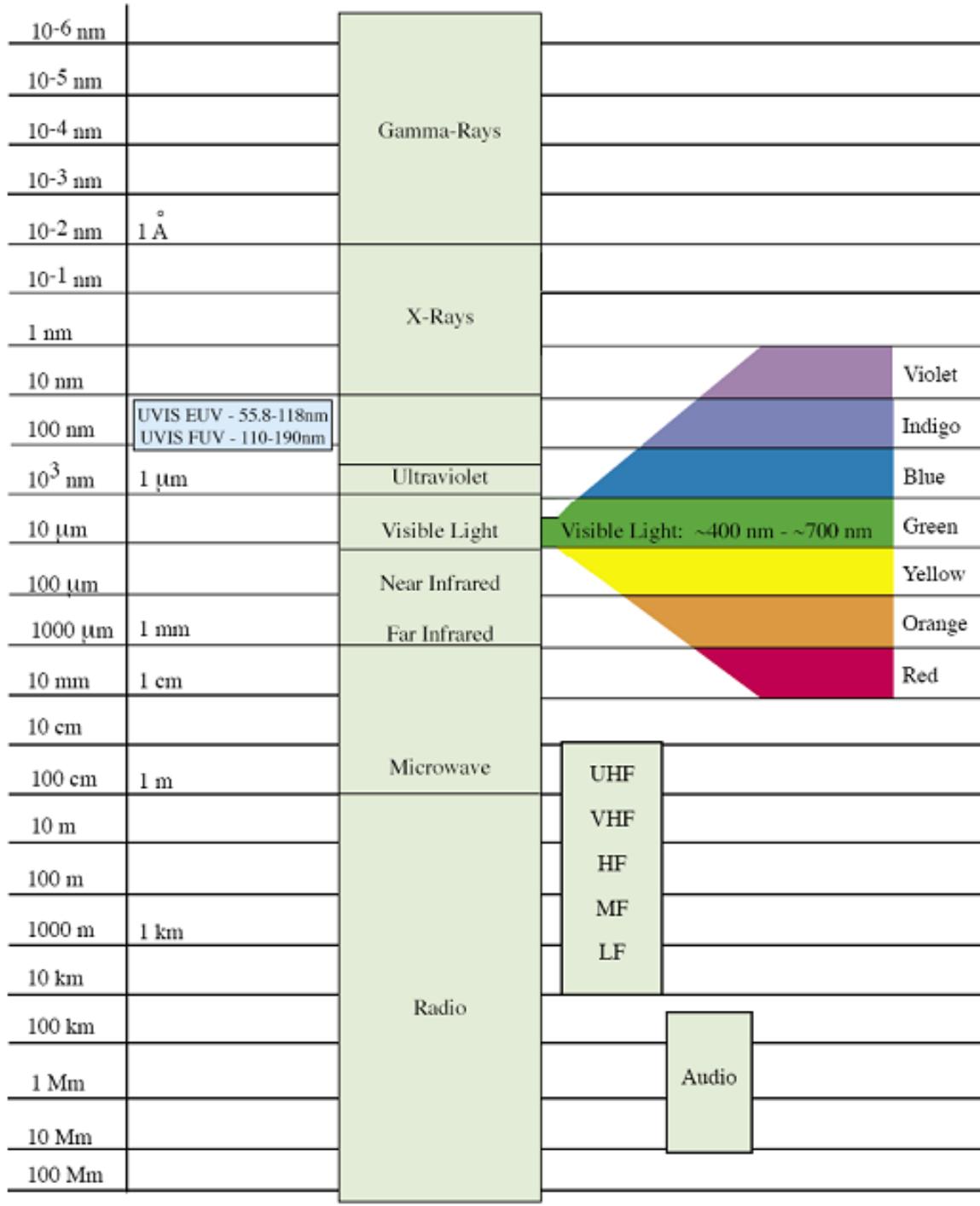
The electromagnetic spectrum

optoelectronic devices



The electromagnetic spectrum

optoelectronic devices

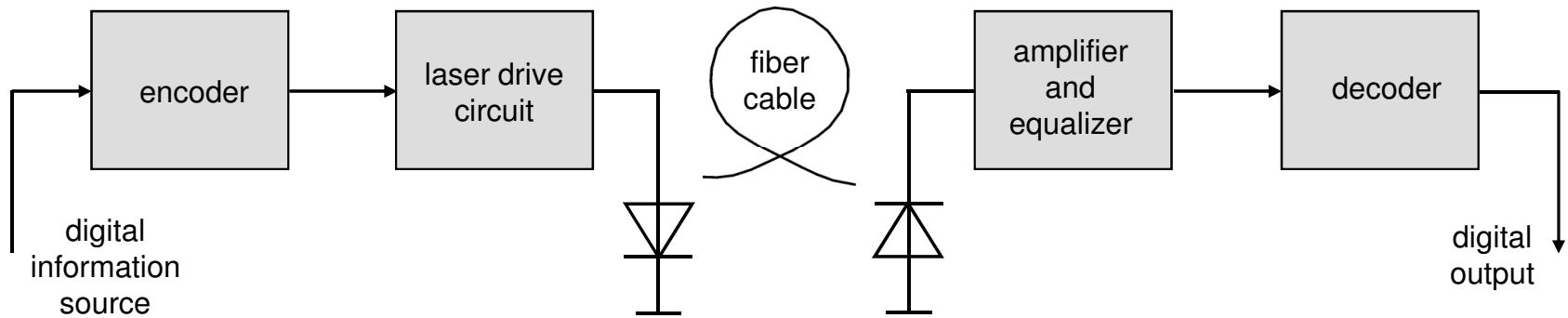


nm=nanometer, $\text{\AA}=angstrom$, $\mu\text{m}=micrometer$, mm=millimeter,
cm=centimeter, m=meter, km=kilometer, Mm=Megameter

Schematic set-up of an optical fibre communication system

1

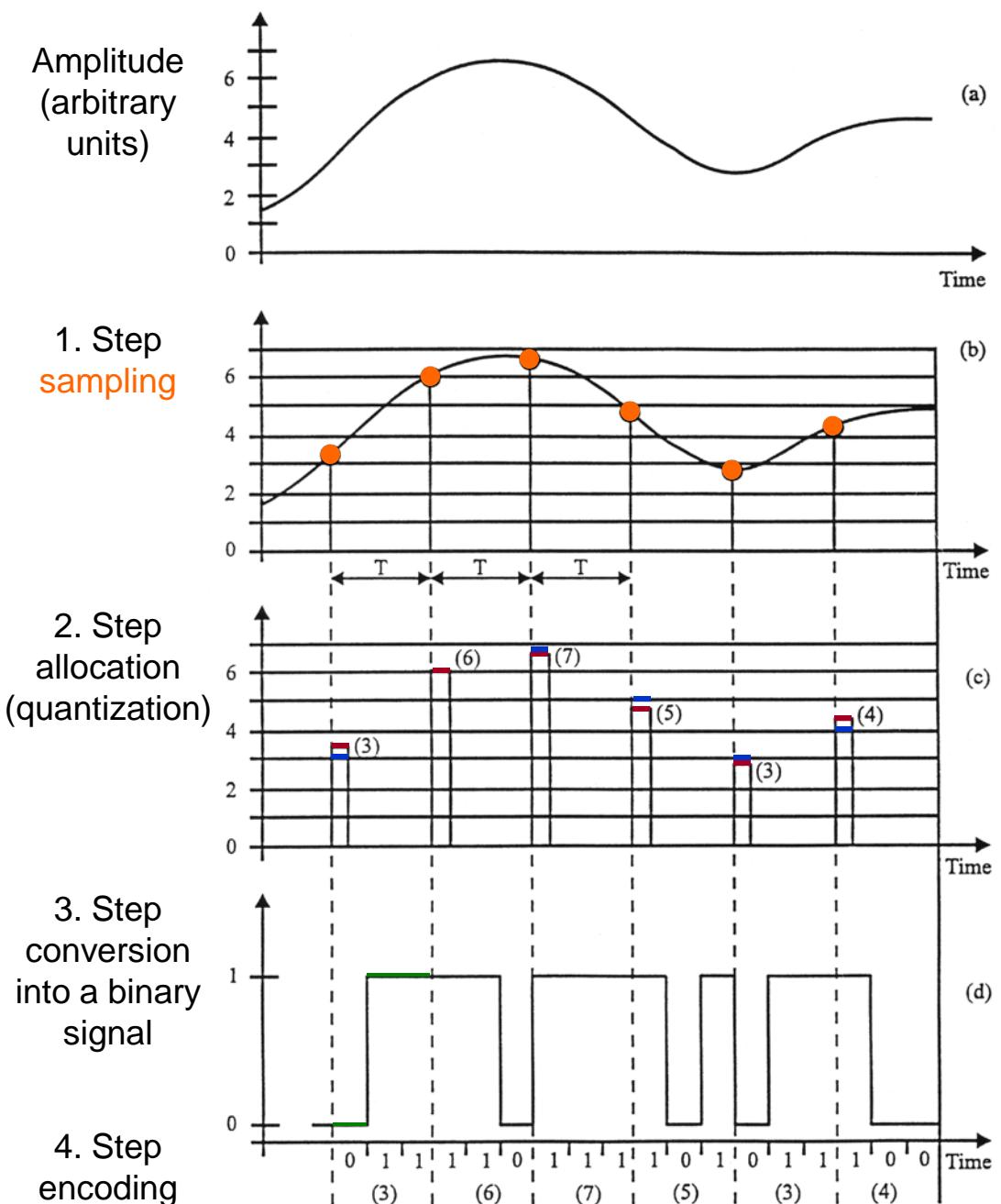
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Conversion of an analog signal into a binary digital signal

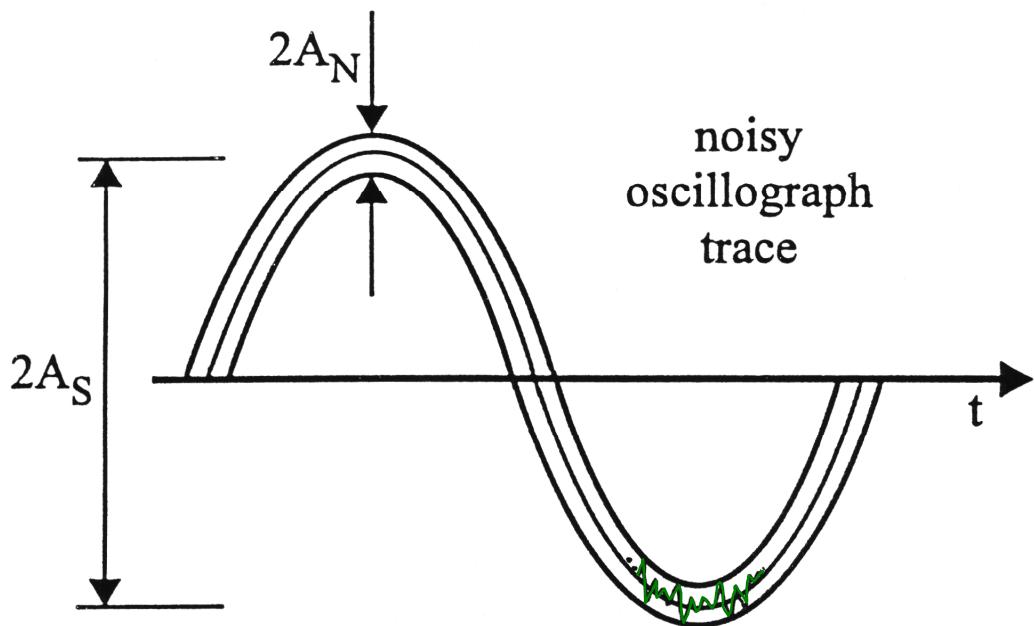
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1



Steps in the conversion of an analog waveform into a binary digital signal:

1. Part of an analog waveform
2. Analog waveform sampled at time intervals of T
3. The sampled waveform showing allocation of amplitude to one of $2^3 = 8$ levels
4. Sampled information converted to binary digital form with 3 bits / sample



$$\text{Signal-to-noise ratio (dynamic range)} = \frac{A_S}{A_N}$$

Required number of quantized levels
 → smallest integer larger or equal to

$$m = \lceil \frac{A_S}{A_N} \rceil$$

Required number of binary digits to encode the signal

$$M = \log_2 m$$

To guarantee that quantization noise \leq original noise of the waveform:

$$B = f_{\max} \cdot \log_2 \left(1 + \frac{A_S^2}{A_N^2} \right) = \text{minimum number of bits/s required}$$

is called shannon criterion.

describes

- minimum bit rate to digitally transmit an analog

waveform without excessive quantization noise

- channel capacity

Sampling Theorem

$$f_{\text{Sampling}} = 2 f_{\text{max}}$$

Shannon criterion

$$B = f_{\text{max}} \cdot \log_2 \left(1 + \frac{A_S^2}{A_N^2} \right) = \text{minimum number of bits/s required}$$

Examples for the information contents of written text, voice, video signals

Example 1. Printed book 250 pages $\approx 10^5$ words, in average 5 letters per word

ASCII code (each letter is represented by 7 binary digits)

$$7 \quad \times \quad 10^5 \quad \times \quad 5 \quad = \quad 3.5 \text{ Mbits}$$

Example 2. Telephone (speech channel)

Our speech includes frequencies from 300 Hz ... 3.4 kHz

→ normal tel. channel is specified with a bandwidth of 3 kHz

S/N = 30 dB ($A_S / A_N = 31.6$) is required

Nyquist and shannon criteria require:

- information rate $B = 0.332 \times 30 \times 3000 = 30 \text{ kbit / s}$
- encoding of e.g. 5 bits per sample
- minimum sampling frequency = 6 kHz

However in practice: 64 kbit / s, analog waveform is sampled at

$f_{\text{Sample}} = 8 \text{ kHz}$, each sample is encoded into an 8 bit word.

Example 3. Fabricating an ADD compact disc from a historic recording

50 min music, signal bandwidth = 20 kHz (what a human ear can detect)

dynamic range 80 dB (e.g. a symphony by L.v. Beethoven)

Encoding: 14 bits per sample, $f_{\text{Sample}} = 44.33 \text{ kHz}$

→ $B = 620 \text{ kbit / s}$

→ total information content = $60 \times 50 \text{ s} \times 620 \text{ kbit/s} = 1.86 \text{ Gbit}$

Today more bits per sample are used.

Example 4. Video film (movie), (625 line PAL color TV signal)

required f_{Max} 5.5 MHz, S/N = 50 dB for good quality

→ min. information rate $B = 0.332 \times 50 \times 5.5 \times 10^6 = 91 \text{ Mbit / s}$

100 min movie : → total information content 550 Gbit

Encoding is satisfactory using 8 bits per sample

$f_{\text{Sampling}} = n \times 4.43 \text{ MHz} = \text{e.g. } 17.7 \text{ MHz}$ (n an integer)

→ $B = 8 \times 17.7 = 142 \text{ Mbit / s}$

However in most movies only a small fraction of the picture changes from frame to frame.

→ considerably reduction in the encoding

→ not too fast changing sceneries can be satisfactorily transmitted at 2 ... 10 Mbit/s

Example 5. Movie on DVD,

100 min movie : → total information content 4.7 GB (4482 Mbyte)

for video and audio; audio standard date rate 256 Kbit/s :

$256 \text{ Kbit/s} * 60 \text{ s/min} * 100\text{min} = 1536000 \text{ Kbit} (= 187,5 \text{ Mbyte})$

residual content for video : 4482 Mbyte - 187,5 Mbyte – 100Mbyte (safety margin) = 4194,5 Mbyte

$4194,5 * 8 * 1024 / 6000 = 5715 \text{ Kbit/s}$ date rate for video

→ $B = 5,9 \text{ Mbit/s}$ medial bit rate

Example 6. Movie on blue ray discs

100 min movie : → total information content 25 GB (23841 Mbyte)

for video and audio; audio standard date rate 256 Kbit/s :

$256 \text{ Kbit/s} * 60 \text{ s/min} * 100\text{min} = 1536000 \text{ Kbit} (= 187,5 \text{ Mbyte})$

residual content for video : 23841 Mbyte - 187,5 Mbyte – 100Mbyte (safety margin) = 23553,5 Mbyte

$23553,5 \text{ Mbyte} * 8 * 1024 / 6000 = 32158 \text{ Kbit/s}$ date rate for video

→ $B = 32 \text{ Mbit/s}$ medial bit rate

Multiplexing techniques

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= simultaneous transmission of a number of independent signals

TDM

time division multiplex



increase of
information
transmission
capacity

WDM

wavelength division multiplex

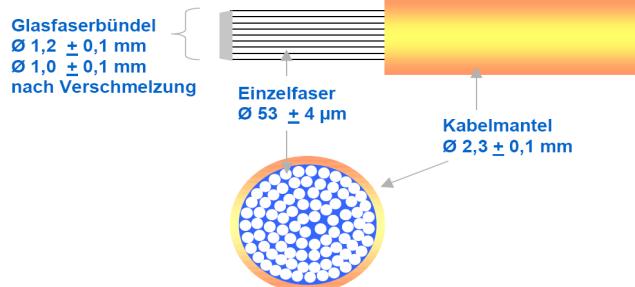
(unique for optical communication)
various signals are transmitted at diff.
wavelength (colours) across the same
fibre

Certain time slots are allocated to a certain signal

e.g. 30 telephone signals (64 kbit/s) can be
transmitted over a channel of 2.048 Mbit/s capacity

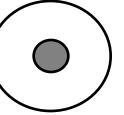
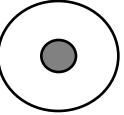
SDM

space division multiplex



Communication systems

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Advantages of optical systems	Compared to electrical systems
<p>1. larger bandwidth</p> <p>optical frequency ~ 10^{14} Hz (NIR) theoretical limit ~ 50 THz today : 10 Gbit/s (practice), 20 - 60 Gbit/s (research) attenuation in optical fibres much less → considerably larger distances between repeaters</p>	<p>Limit ~ 1 GHz (attenuation ↑ with f ↑) than in coaxial cables</p>
<p>2. material : glass or polymers → small size and weight interesting for mobiles (cars and aircrafts)</p>	Material : copper
<p>3. no potential problems (since insulators)</p>	Serious potential problems
<p>4. no interference or crosstalk between neighbor fibres (no shielding required)</p>	Interference or crosstalk
<p>5. Nearly perfect signal security</p>	Weak signal security
<p>6. low transmission loss 0,18 dB/km (1,55 μm) independent of modulation frequency</p>	 For single mode fibre
	 20 dB/km at 100MHz For core diameter 3,3 μm; cladding diameter 18,5 μm

Chapter 3

Fundamental principles in optics

Four key phenomena

which are important
if electromagnetic waves are superimposed :

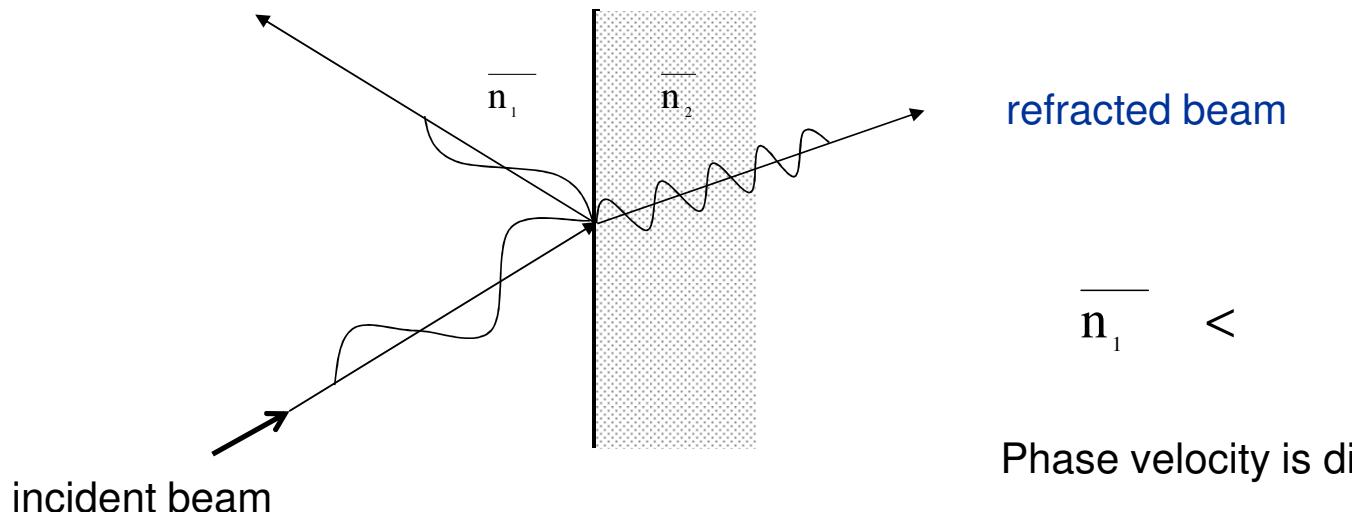
- Polarization
- Interference
- Diffraction
- Coherence

Example : let us consider a semiconductor crystal

a) $\lambda \gg a$ lattice constant of the crystal ($a \approx 0.3 \text{ nm}$)

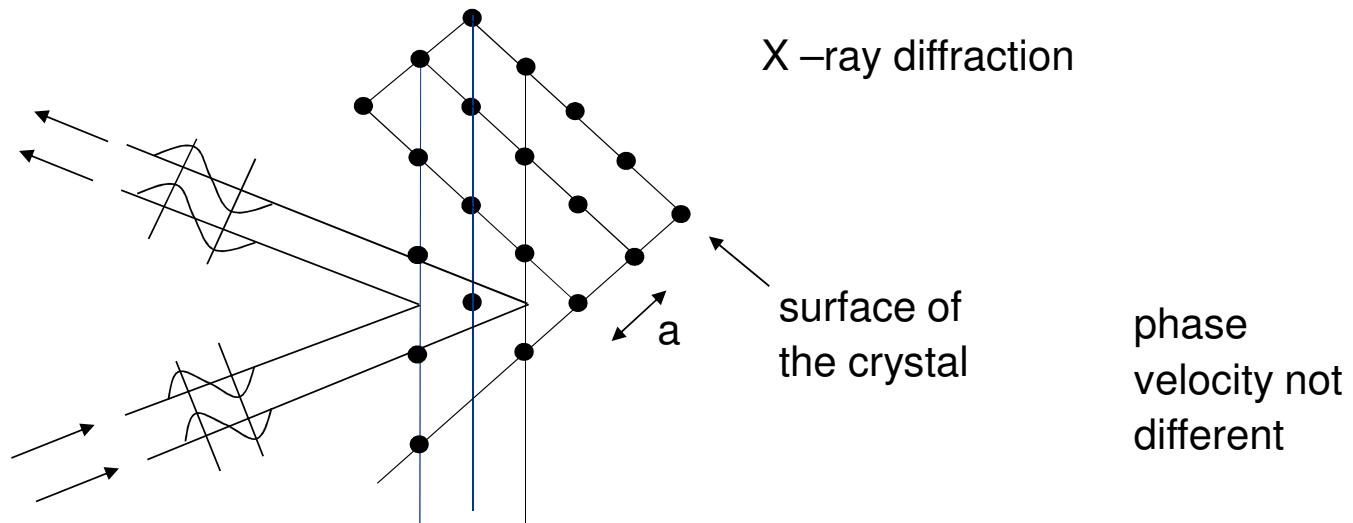
Light wave experiences (feels) a continuum → the optical density of the medium is described by an averaging refractive index \bar{n}

reflected beam



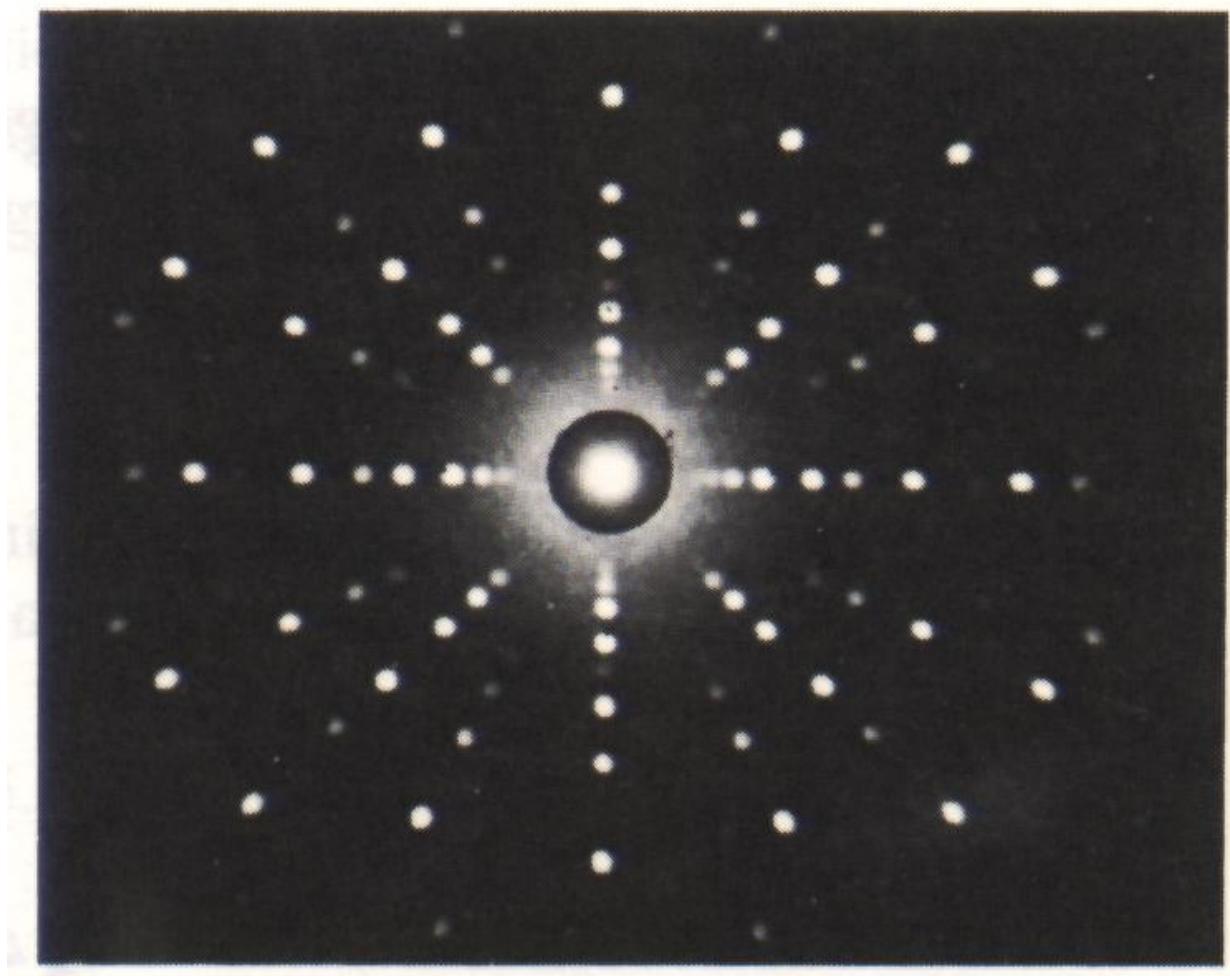
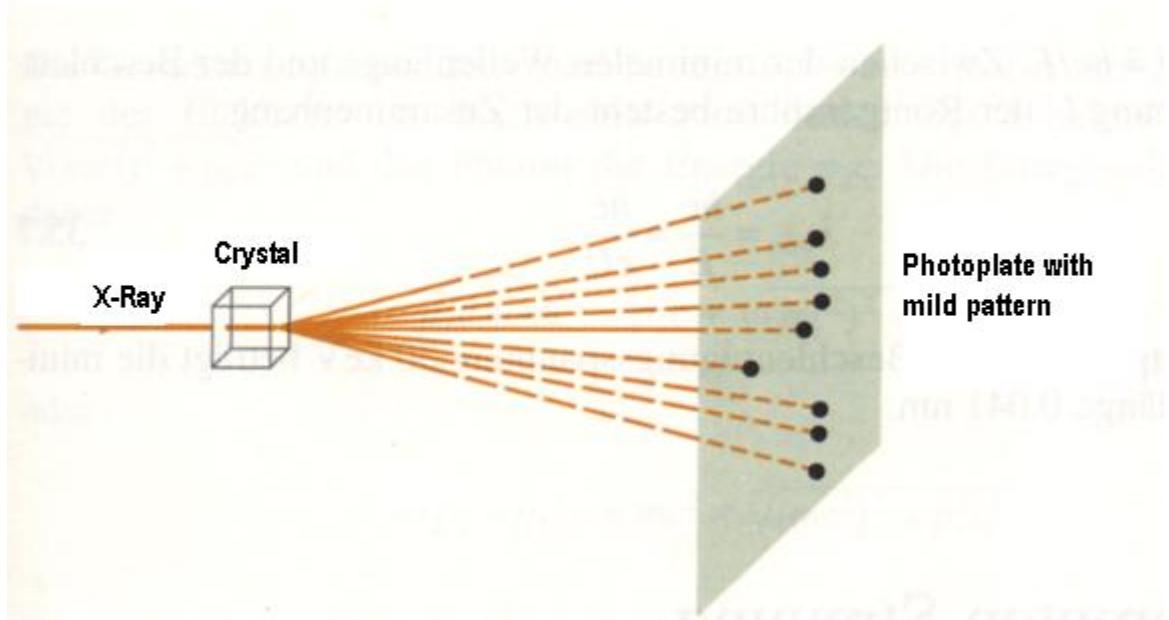
Phase velocity is different

b) λ (X – rays) \lesssim a lattice constant of the crystal



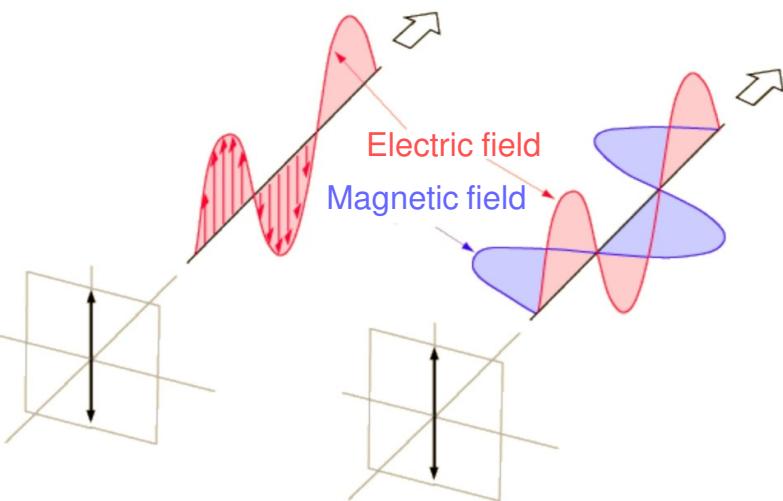
Diffraction pattern

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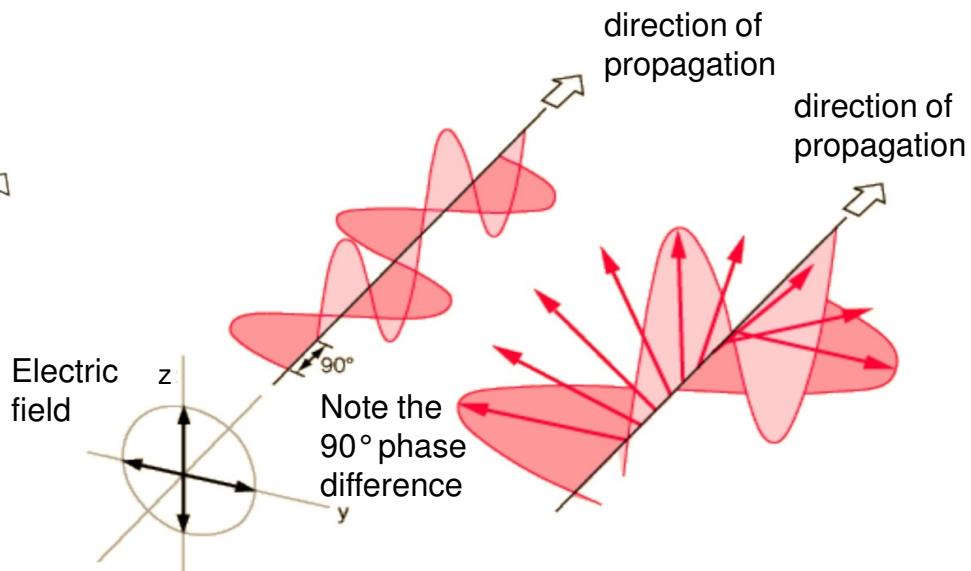


Classification of Polarisation

linear



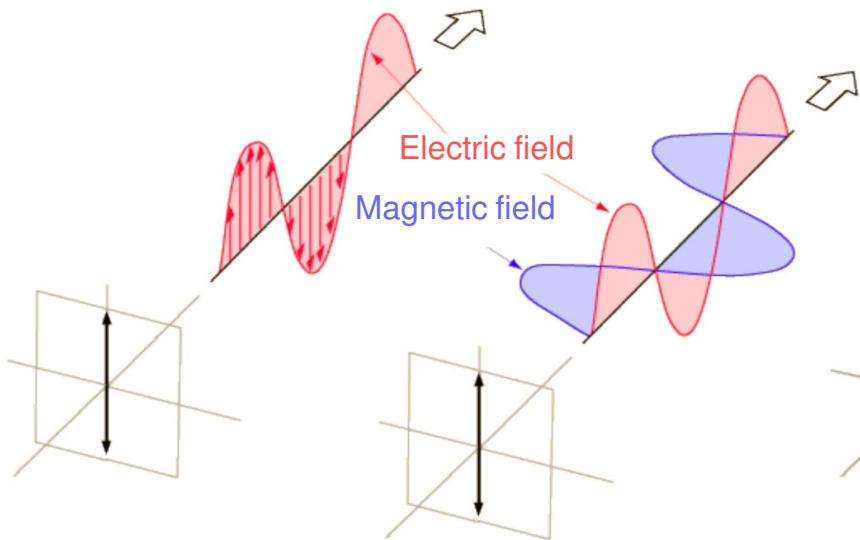
circular



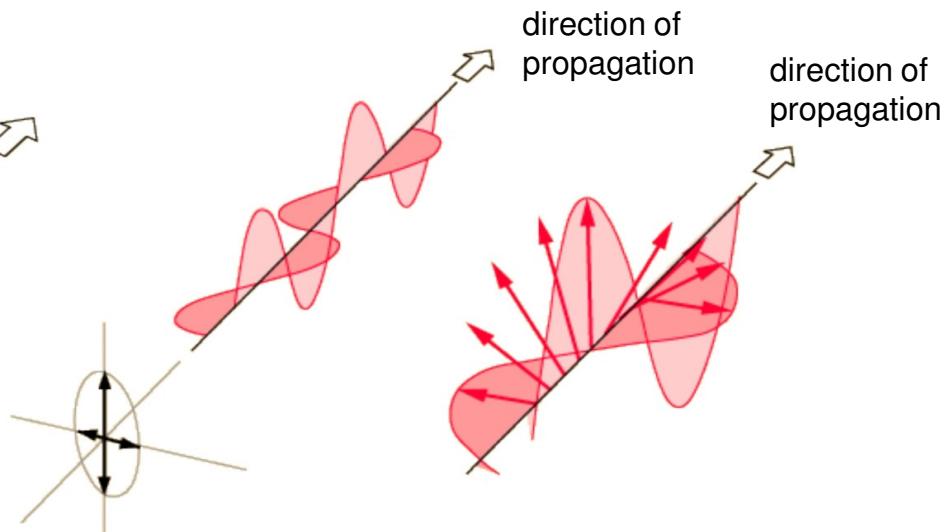
If this wave is approaching an observer, its electric vector would appear to be rotating counter clockwise. This is called right – circular polarisation.

Classification of Polarisation

linear



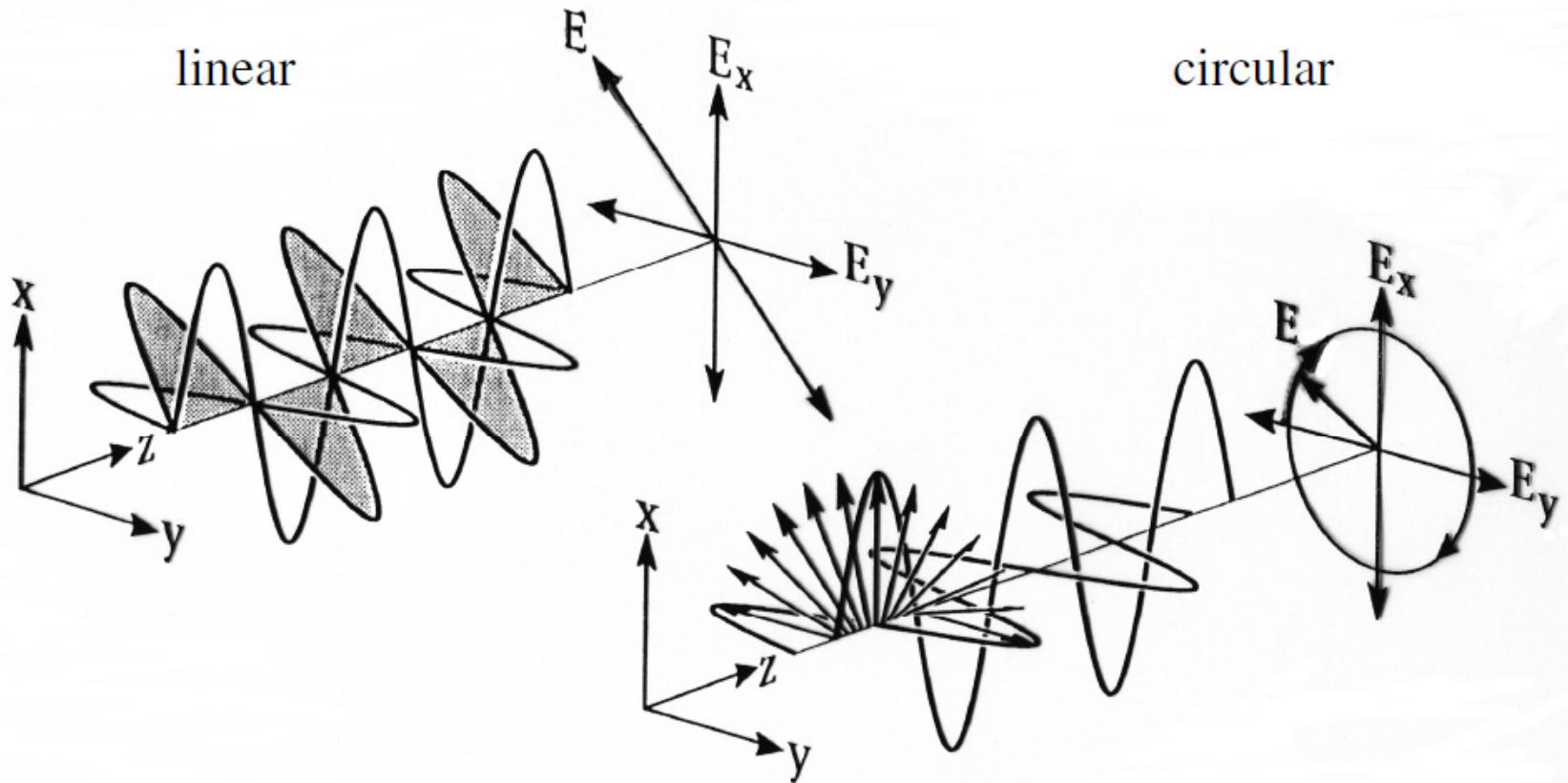
elliptic



If this wave is approaching an observer, its electric vector would appear to be rotating counter clockwise. This is called right – elliptic polarisation.

Polarisation III

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0 ← phase difference → $\Pi/2, 3\Pi/2$ (elliptical polarisation: if the 2 wave have different amplitude)

Implementation of polarisation : by polarizers

Rotation of polarisation : e.g. quarter-wave plate

Interference of two waves

electric fields $E_1 = E_1(t)$, $E_2 = E_2(t)$, both complex,

since $\bar{E}_1 // \bar{E}_2$ scalar properties can be considered.

$\langle \quad \rangle$, indicates a time average

$*$ = conjugate complex

$$E_{\text{total}} = E_1 + E_2$$

$$\begin{aligned} I_{\text{total}} &\sim \langle |E_{\text{tot}}|^2 \rangle = \langle E_{\text{tot}} E_{\text{tot}}^* \rangle \\ &= \langle (E_1 + E_2)(E_1 + E_2)^* \rangle \\ &= \langle (E_1 + E_2)(E_1^* + E_2^*) \rangle \\ &= \langle E_1 E_1^* \rangle + \langle E_1 E_2^* \rangle + \langle E_2 E_1^* \rangle + \langle E_2 E_2^* \rangle \\ &= \langle |E_1|^2 \rangle + \langle 2 \operatorname{Re}\{E_1 E_2^*\} \rangle + \langle |E_2|^2 \rangle \\ &= I_1 + \langle 2 \operatorname{Re}(E_1 E_2^*) \rangle + I_2 \end{aligned}$$

$I_1 = I_2$, \bar{E}_1 indicates the amplitude

Often a superposition of a wave with itself after a retardation τ occurs :

$$E_1(t) = \hat{E}_1 \exp(-j\omega t),$$

$$E_2(t) = E_1(t + \tau) = \hat{E}_1 \exp(-j\omega(t + \tau)),$$

$$\begin{aligned} I_{\text{total}} &\sim \langle |E_1 + E_2|^2 \rangle \\ &= \langle |E_1|^2 \rangle + \langle |E_2|^2 \rangle + 2 \cdot \langle \operatorname{Re}\{E_1 E_2^*\} \rangle \\ &= \langle |E_1|^2 \rangle + \langle |E_1|^2 \rangle + 2 \cdot \langle |E_1|^2 \rangle \cdot \\ &\quad \cdot \langle \operatorname{Re}\{\exp(-j\omega t) \cdot \exp(j\omega t) \cdot \exp(j\omega\tau)\} \rangle \\ &= 2I_1 + 2I_1 \operatorname{Re}\{\exp(j\omega\tau)\} \\ &= 2I_1 + 2I_1 \cos(\omega\tau) \\ &= 4I_1 \cos^2 \frac{\omega\tau}{2} \end{aligned}$$

The resulting interference pattern is \cos^2 – like

Maximum intensity = $4 I_1$

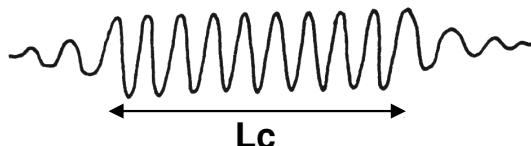
Minimum intensity = 0

Average intensity = $2 I_1 = I_1 + I_2$ according to energy conservation

for a good efficiency of diffractive elements: coherence length of the light very important

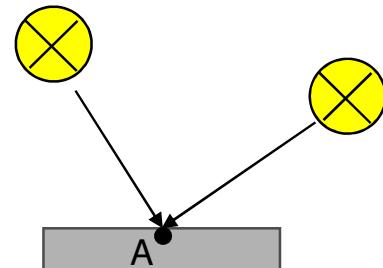
L_c = length of wave packet in which a fixed phase relation exists (no phase jumps within the coherence length).
 → the more monochromatic the longer L_c

light interferes if - temporal coherence - spatial coherence } is fulfilled



Characteristic for incoherence

if $I_{\text{total}} = I_1 + I_2$ in point A



Characteristic for coherence

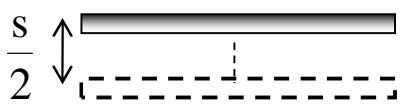
A schematic diagram of a Michelson interferometer. Light enters from the left and hits a beam splitter. One path goes up to a mirror, reflects back down, and hits the beam splitter again. The other path goes down to a mirror, reflects back up, and hits the beam splitter again. From the beam splitter, two paths emerge.

$$I_{\text{Total}} = I_1 + I_2 + 2 \cdot \sqrt{I_1 \cdot I_2} \cdot \cos\left(\frac{2\pi \cdot s}{\lambda} + \Delta\phi\right)$$

brace under the term: interference term

Michelson
Interferometer

Enables to measure coherence length L_c



maximum possible path difference so $\frac{L_c}{2}$
 that interference still occurs

Coherence II

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Wave propagates with the light velocity c

→ L_C corresponds to a coherence time $\tau_c = L_C / c$

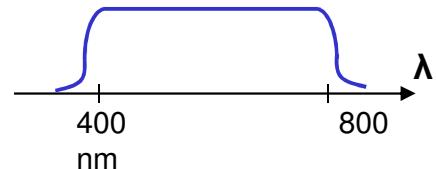
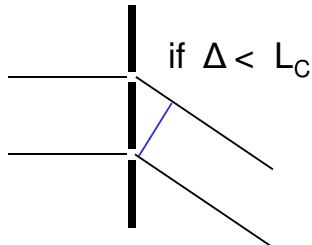
Coherence time τ_c is connected to linewidth (bandwidth) Δf via Fourier Theorem

$$\Delta f = \frac{1}{2\pi \cdot \tau_c} = \frac{c}{2\pi \cdot L_C}$$

→ temporal coherence is a measure for spectral purity

Example	L_C	τ_c	$\Delta f / f$
Low pressure spectral lamp, Ne	3 cm	0.1 ns	$3.4 \cdot 10^{-6}$
Low pressure spectral lamp, Kr	100 m	300 ns	$1.1 \cdot 10^{-9}$
Laser, HeNe, 633 nm	500 km	1.6 ms	$2.1 \cdot 10^{-11}$
Laser, InGaAlAs / InP, 1.55 μm	60 m	200 ns	$5 \cdot 10^{-9}$

Interference with „white light“ ?



A) Quasi white light (finite bandwidth)

→ interference occurs since $\Delta < L_C$ (spectrometer work due to this fact)

B) Ideally white light (infinite bandwidth) → no interference $\Delta > L_C$!

The different orders overlap completely and homogeneously

Laser type	Coherence length
Fibre laser stabilized/ unstabilized	100km / 50μm
HeNe stabilized/ unstabilized	1km / 20cm
Semiconductor Diode laser with external Resonator	0,1- 1km / < 1mm
Dye laser	5- 250m
Ar or Kr with Etalon	1m
flash- lamp pumped Nd: YAG	1cm

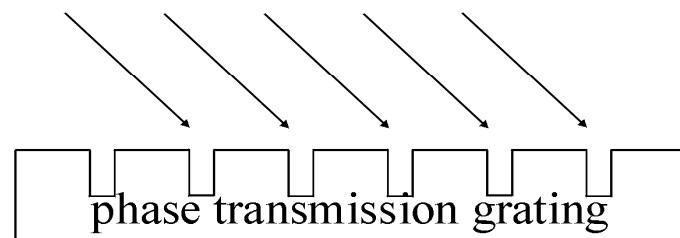
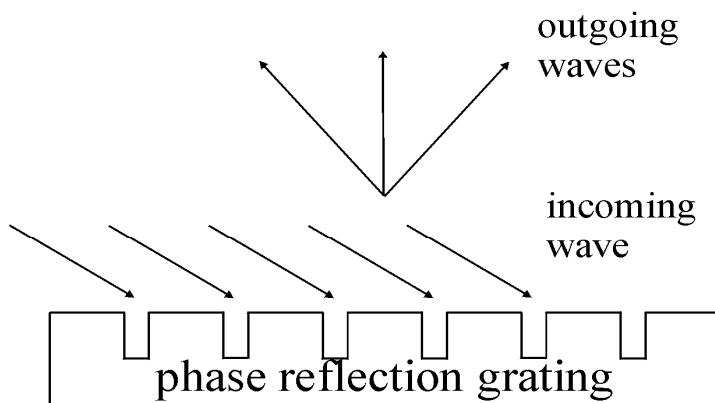
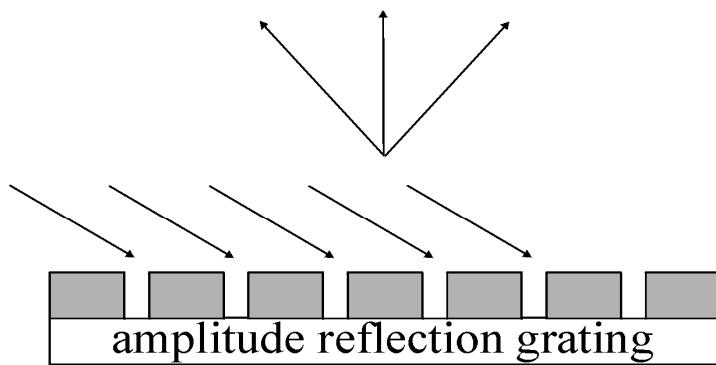
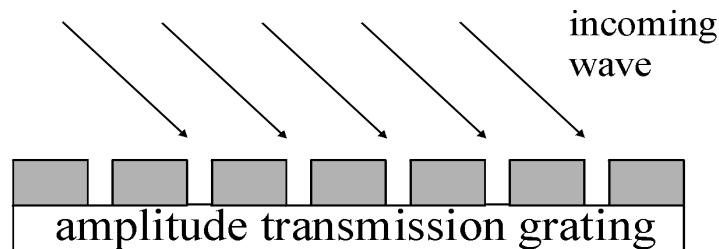
For temporal coherence

$$L_c \approx \frac{132m}{\Delta f}$$

for a Gaussian beam profile

Examples of different types of gratings

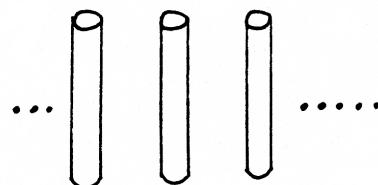
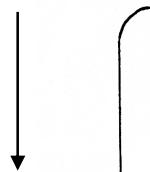
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Examples of gratings

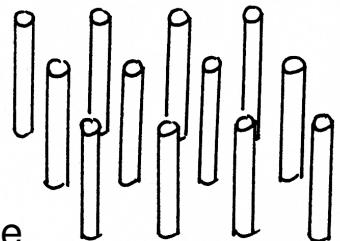
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Operating in



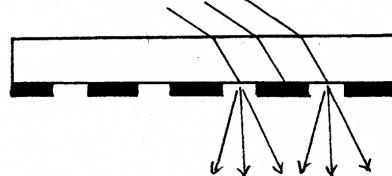
1D

amplitude
gratings

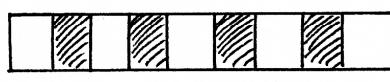
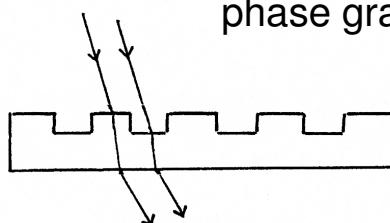


2D

transmission

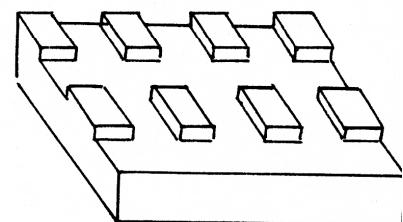


phase gratings

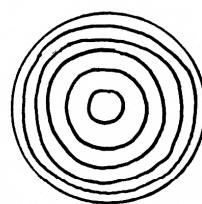


$\bar{n}_x \bar{n}_z$

1D

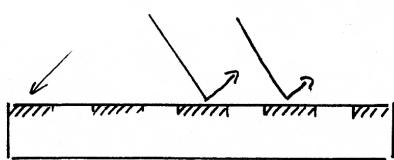


2D

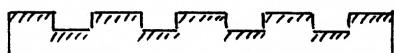


1D

reflection



amplitude gratings

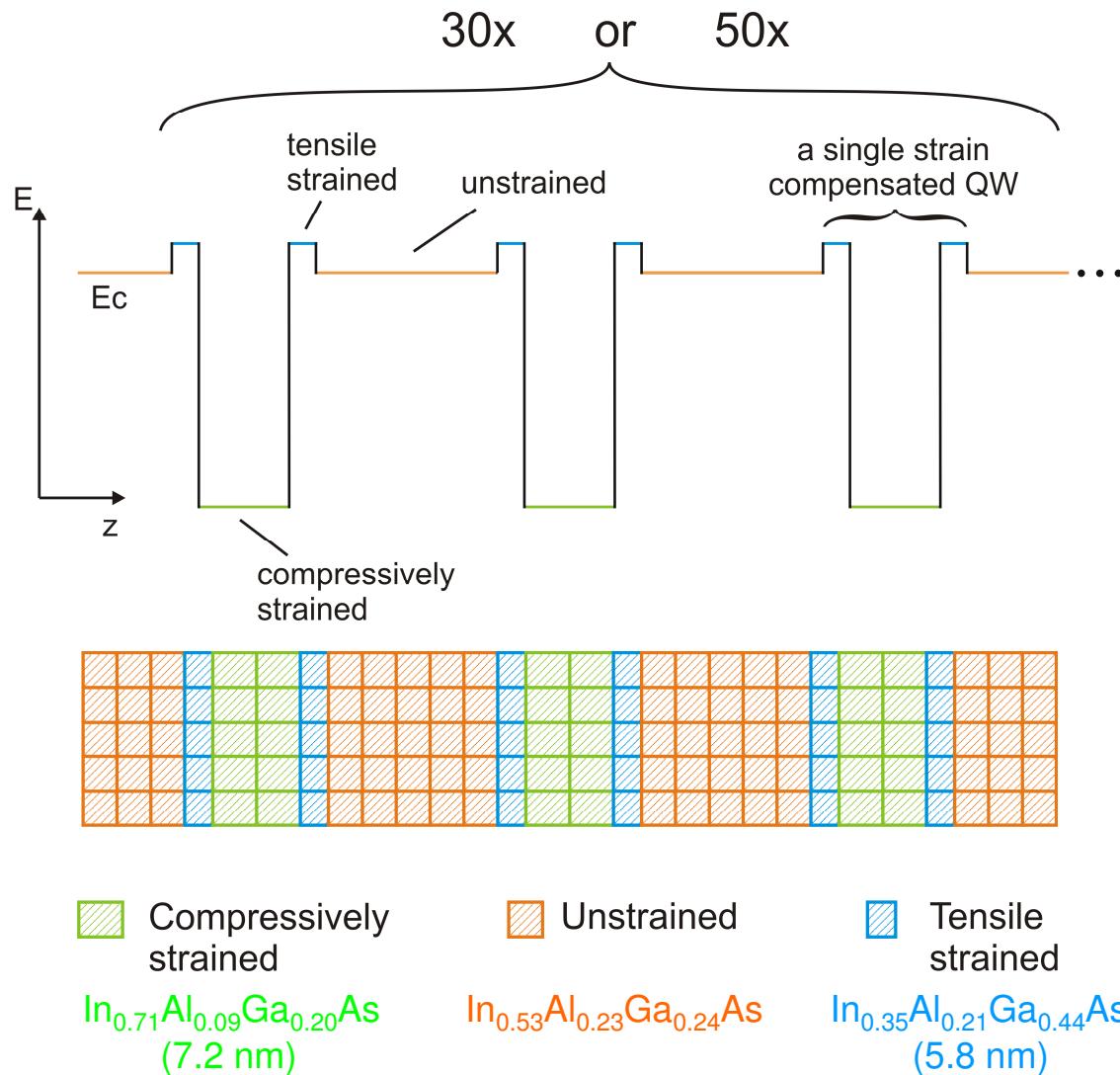


phase gratings



X-ray diffraction (XRD) at a strain compensated multiple quantum well structure

optoelectronic devices



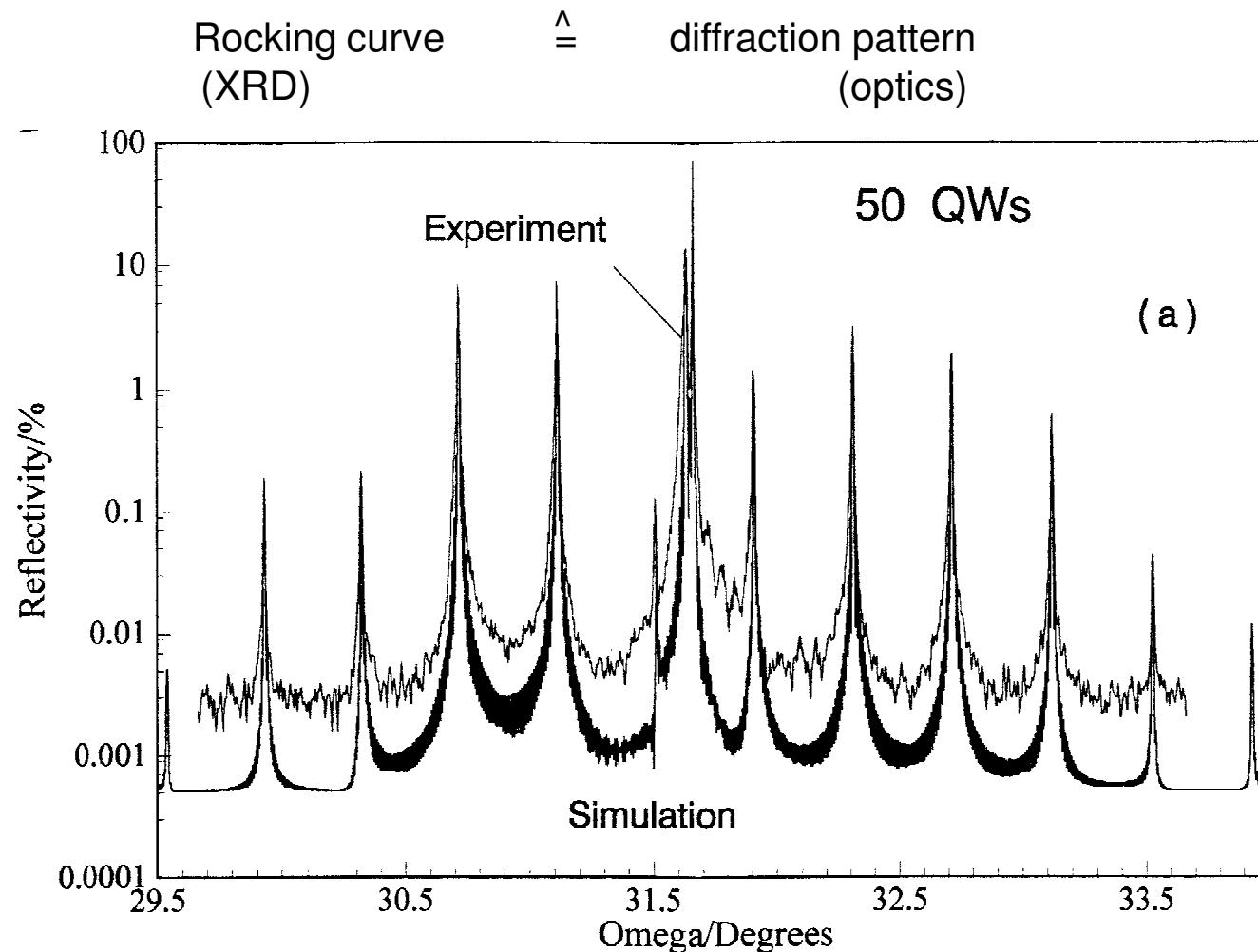
10x is used for the active layer of ultrafast semiconductor lasers

a single square represents a cubic uni cell here

For the lecture a smaller number of unit cells is displayed as in reality

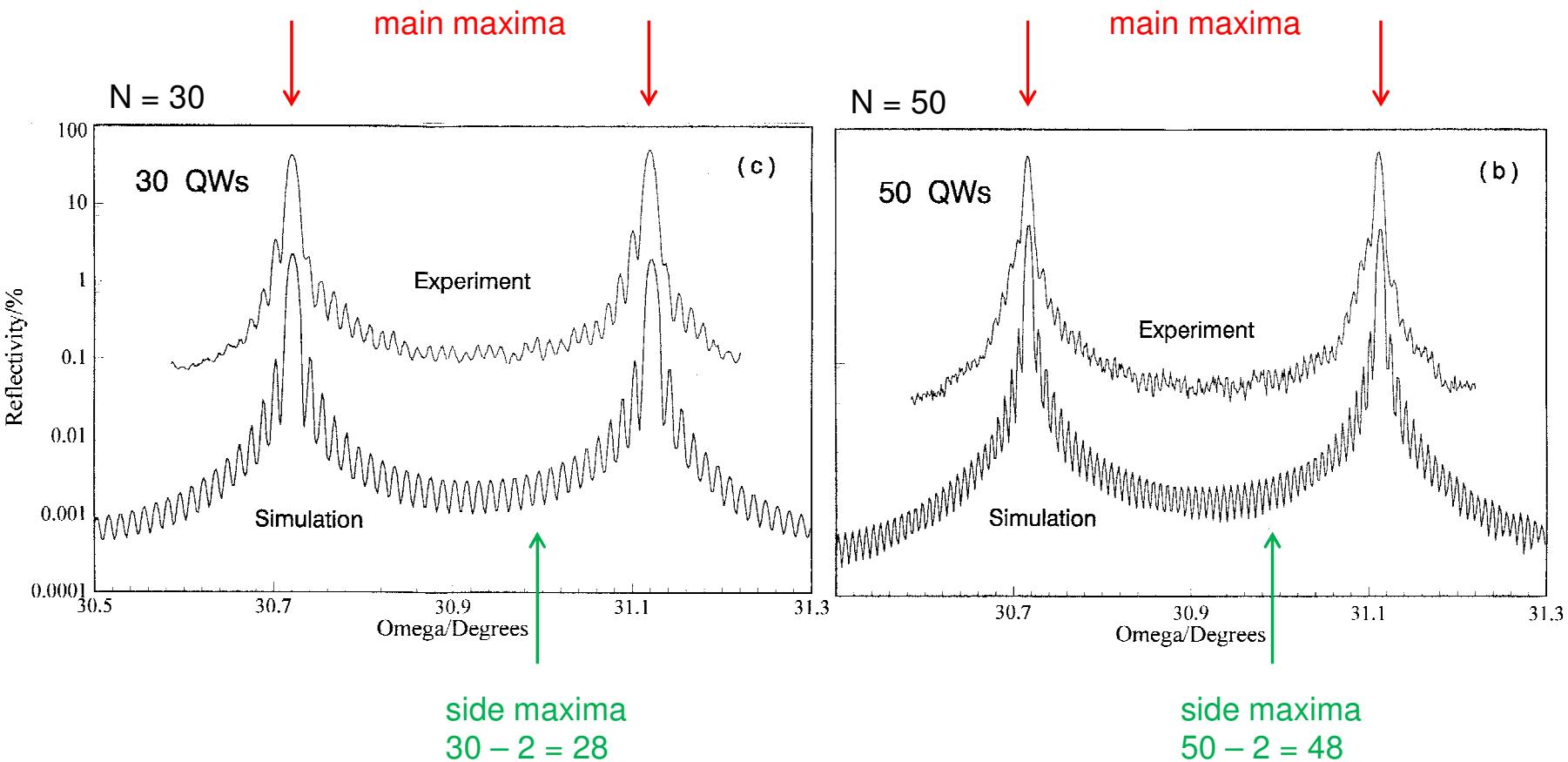
X-ray diffraction (XRD) at a strain compensated multiple quantum well structure

optoelectronic devices



X-ray diffraction (XRD) at a strain compensated multiple quantum well structure

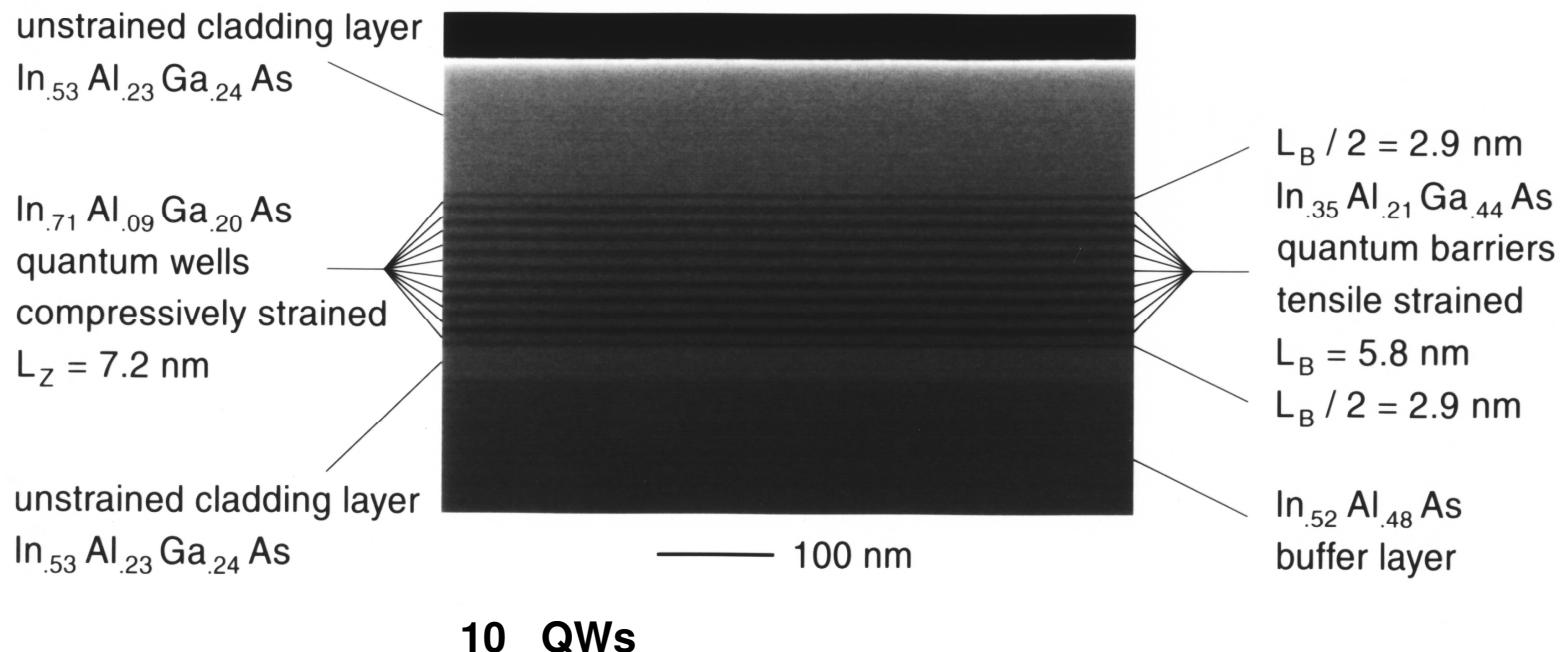
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X-ray diffraction (XRD) at a strain compensated multiple quantum well structure

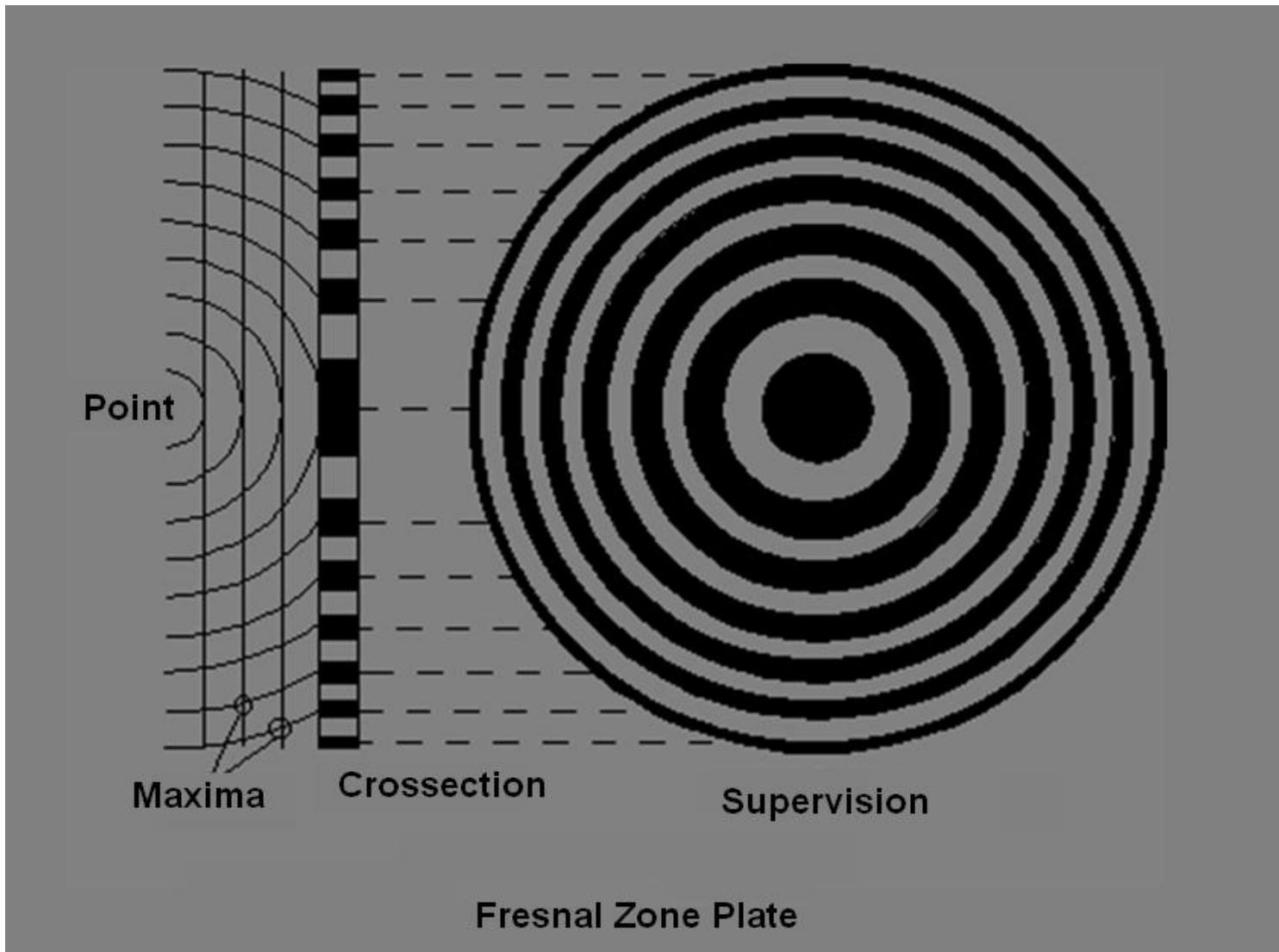
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MBE grown strain - compensated multiple quantum well heterostructure
for high - speed 1.55 μm laser diodes



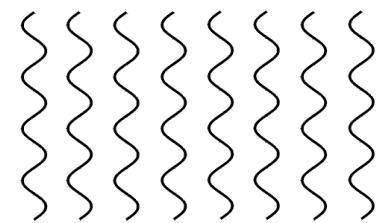
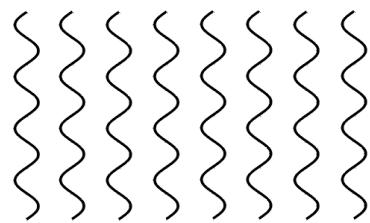
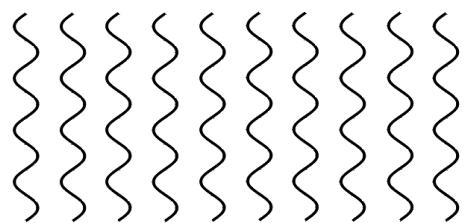
Fresnel Zone plate

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Interaction of light with objects of different size

optoelectronic devices



a

b

c

?

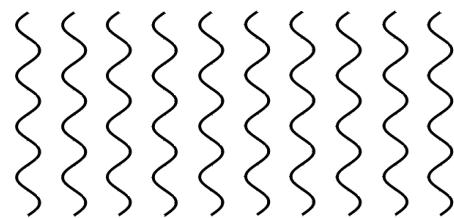
?

?

Interaction of light with objects of different size

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Size of structure $> \lambda$



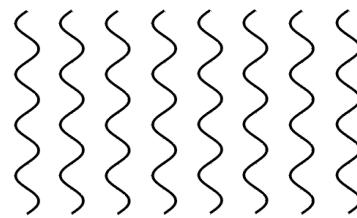
a

shadows

Daily life

fabrication of integrated circuits (ideal case)

Size of structure $\sim \lambda$



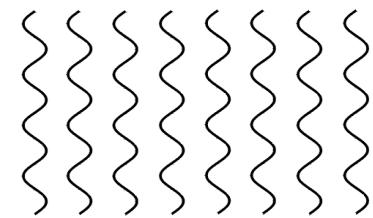
b

diffraction

Opalescent colors in nature

electron diffraction,
x-ray diffraction, micro lasers, micro filters

Size of structure $<< \lambda$



c

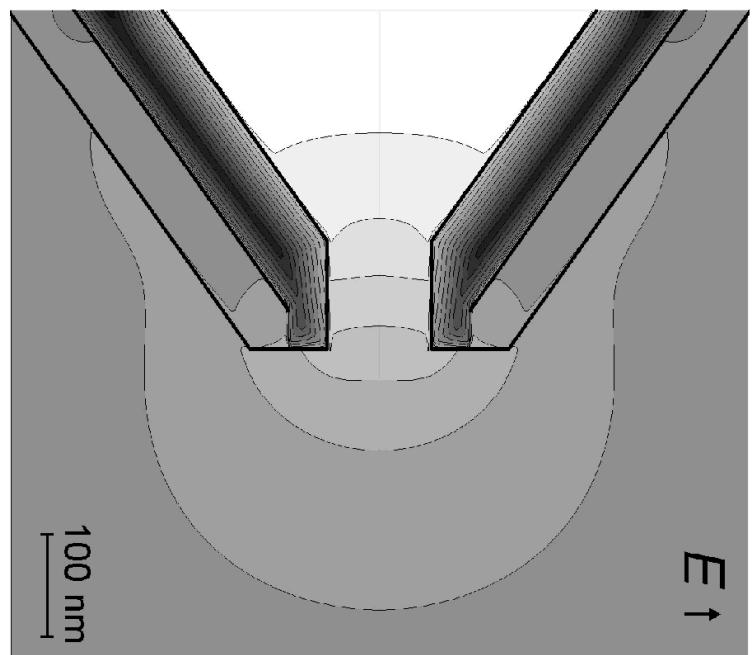
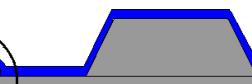
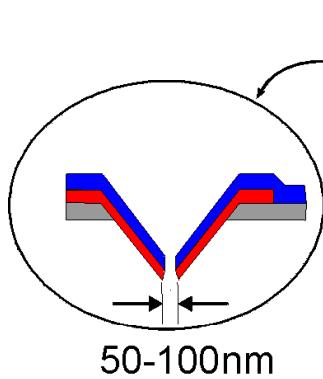
Under distinct circumstances we are able to observe something

fabrication off new synthetic materials, optical near field microscopy

Near field microscopy

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Resolution << wavelength

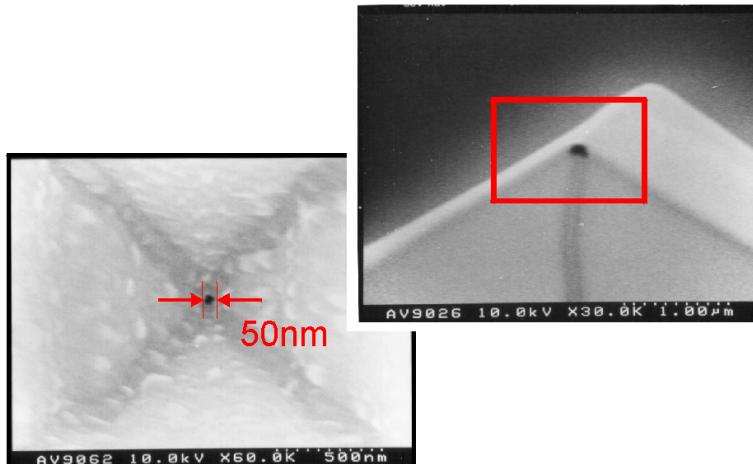


~~resolution
conventional microscope~~

$$\Delta x_{\min} = 0,61 \frac{\lambda}{NA}$$

(Rayleigh-criterium)

logarithmic intensity distribution (factor 10 between grey levels, respectively)

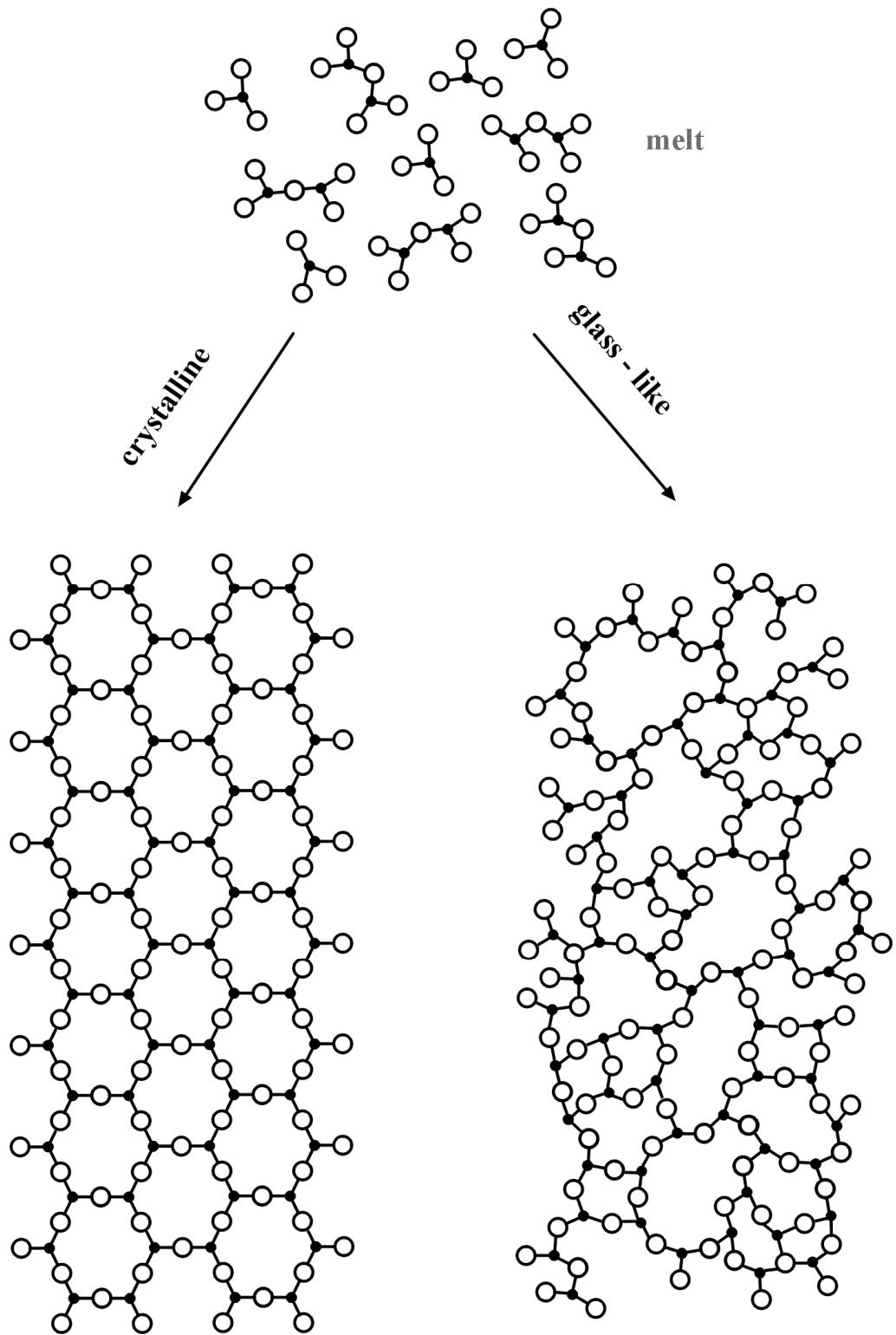


Chapter 4

Optical Waveguiding

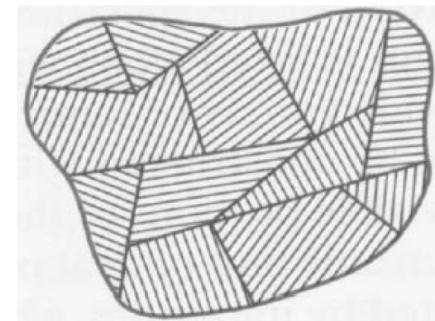
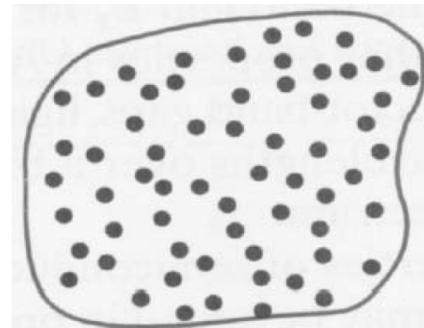
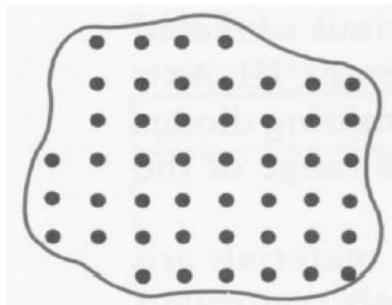
Fused silica vs. glass

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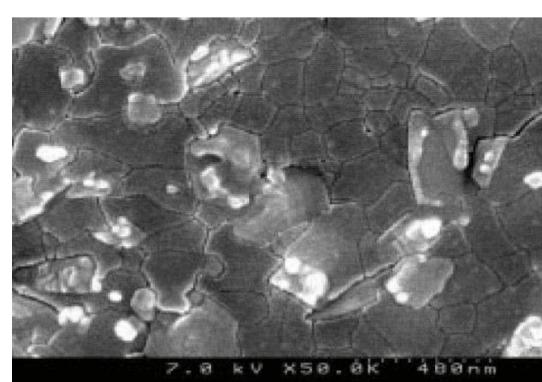


Classification of solids

optoelectronic devices



crystalline



amorphous or glass-like

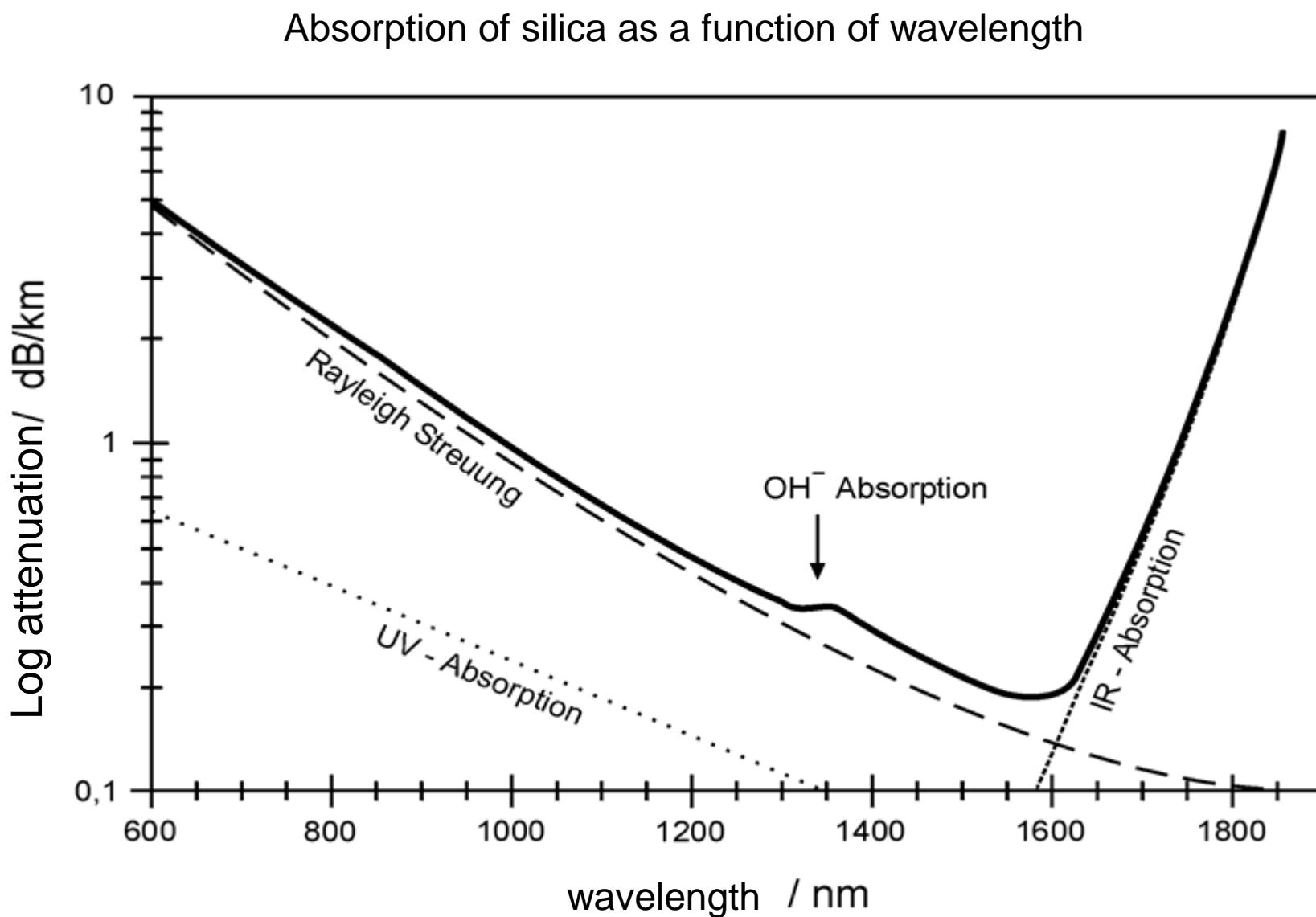
(within this lecture the minor differences
between both classes are not focussed)



polycrystalline

Spectral attenuation of a silica fibre

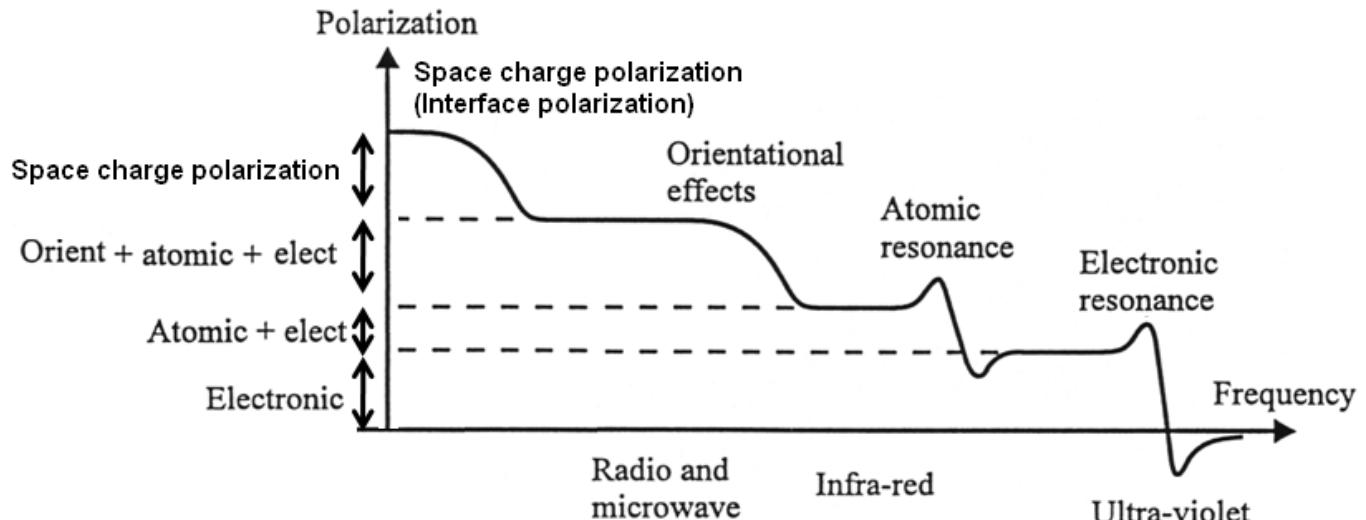
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Refractive index of silica glass

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A propagating electromagnetic wave excites atomic groups (molecules), atoms and electrons to forced, damped oscillations. At low frequencies f : each of these oscillators follows the forced oscillations; if f is further increased they come into resonance (power is absorbed from the wave field and reemitted in different directions); at very high f the oscillator is unable to follow the forced oscillations. The resonance f for vibrations is located at lower f than for electrons. The polarisation P „describes“ the amplitude of the forced oscillations.



Dispersion means $\bar{n} = \bar{n}(\lambda)$ or $\omega = \omega(k)$

$$\text{or } f \text{ is not simply proportional to } 1/\lambda : f = \frac{c_0}{n(\lambda)} \cdot \frac{1}{\lambda}$$

Since the relative permittivity $\epsilon = 1 + \frac{P}{\epsilon_0 E}$

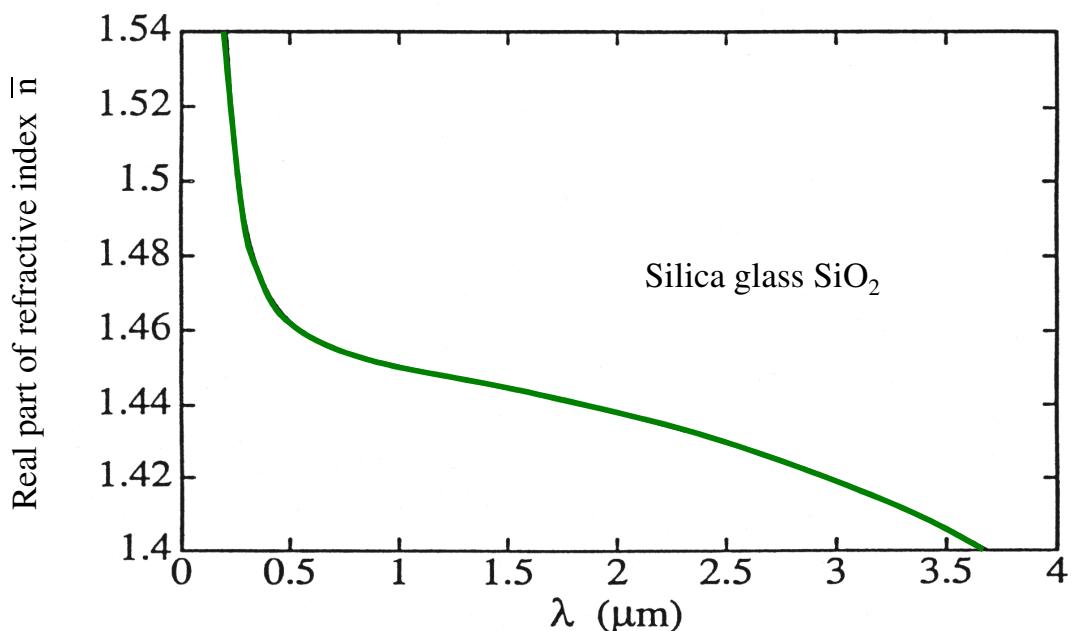
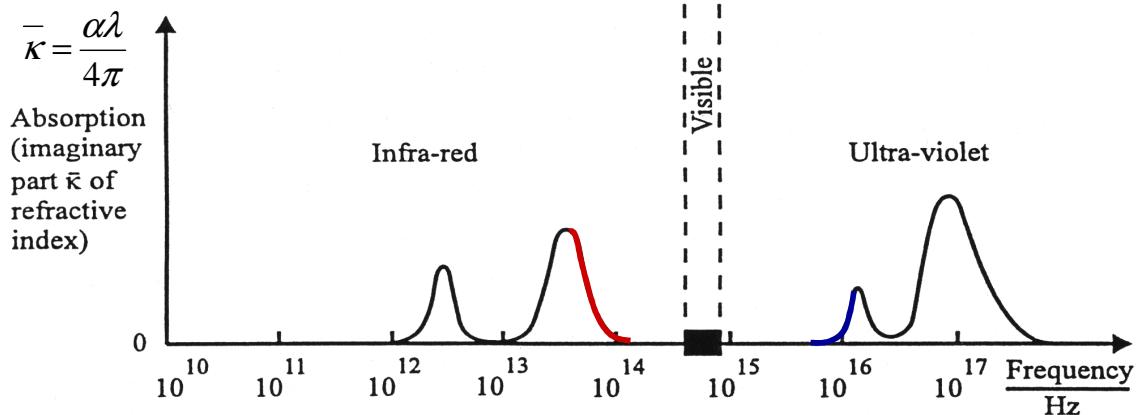
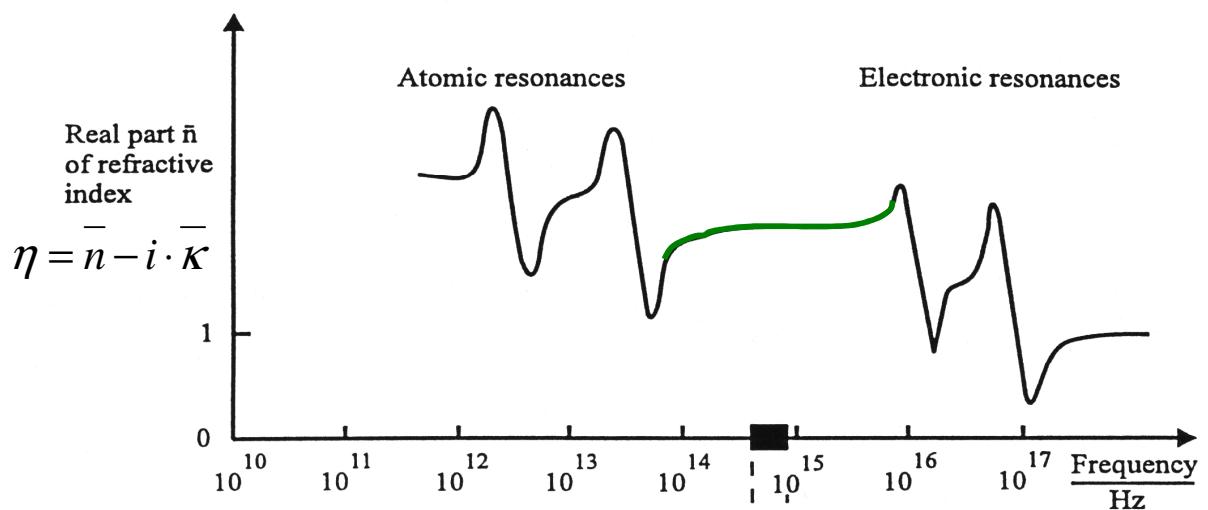
a quality similar picture can be drawn for \bar{n} (= dispersion curve)

Each resonance in the dispersion curve is accompanied by a resonance

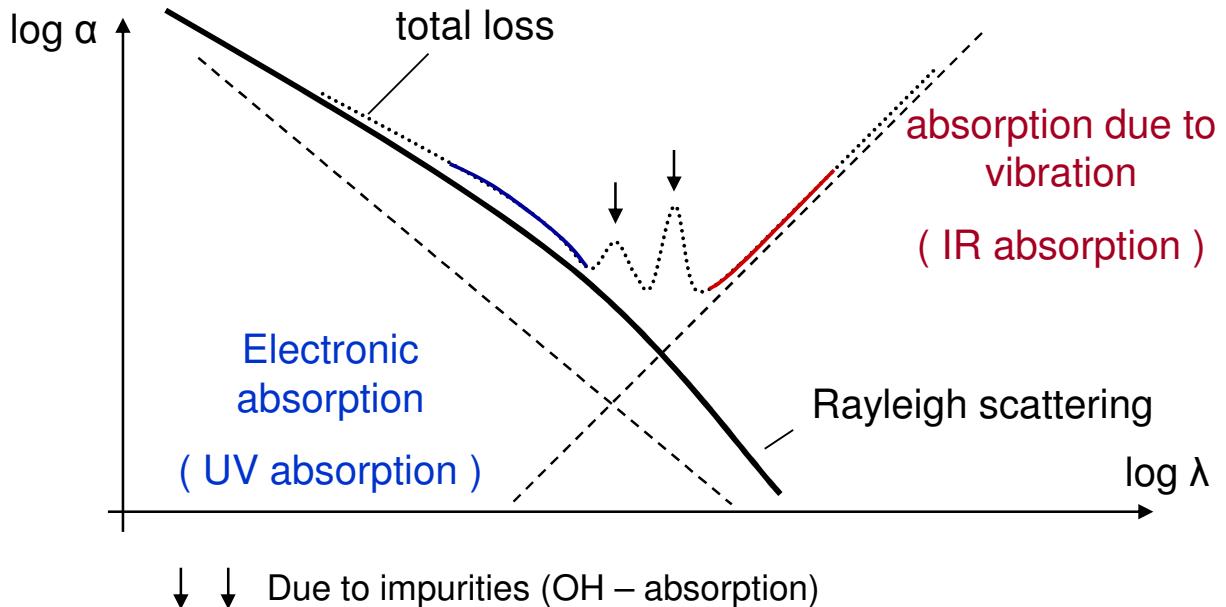
in the absorption curve

→ this relates \bar{n} and α (Kramers – Kronig relation, causality).

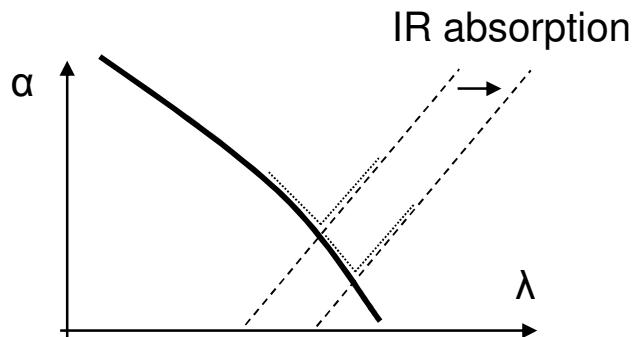
The complex refractive index $\eta = \bar{n} - i \cdot \bar{\kappa}$ optoelectronic devices



- a) These phenomena already explain important parts of the absorption curve of a silica fibre:

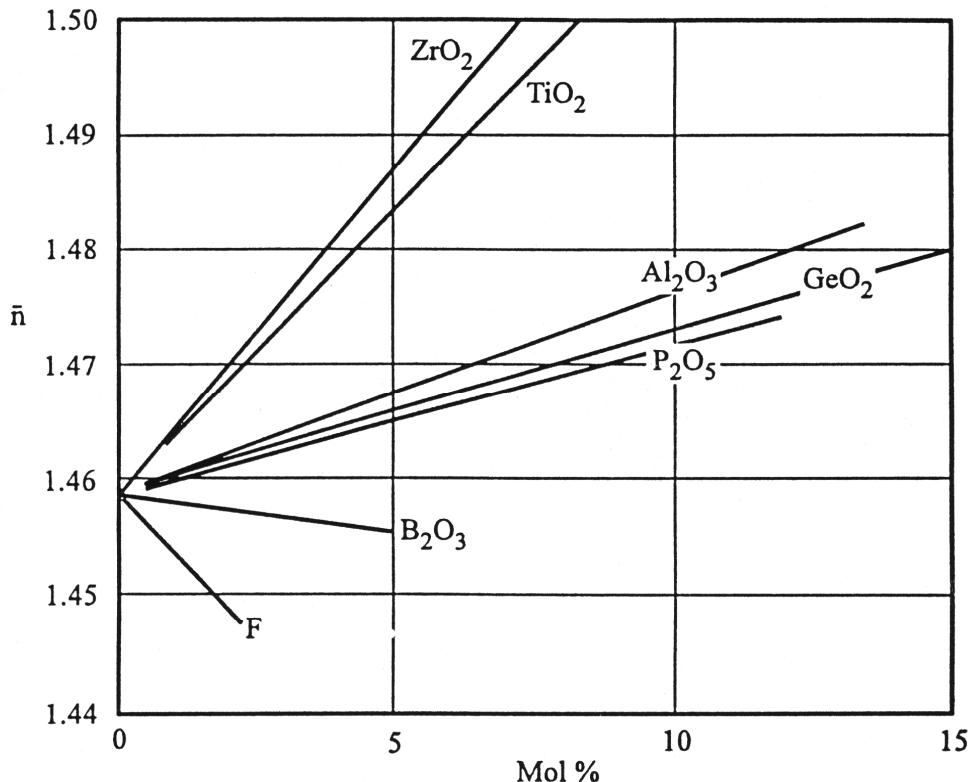


- b) If silica is replaced by heavy metal fluorine glasses the absorption in the fibre in the IR (vibrations) is shifted to higher λ (due to the larger masses of the atoms). This is studied in current research: → absorption minimum is shifted to larger λ
(application : long-haul oceanic communication links)

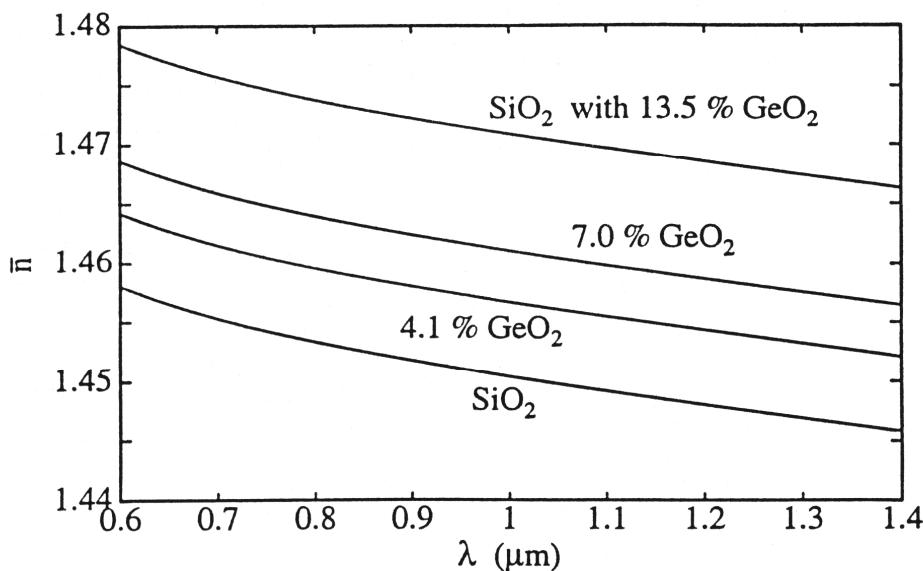


- c) At shorter λ , cheap polymer fibres can be used over short distances

Adding oxide impurities to $\text{SiO}_2 \rightarrow$ variation of \bar{n} (application : index profiles in fibres)



Silica fibre doped with various impurities



Ray model in optical fibres

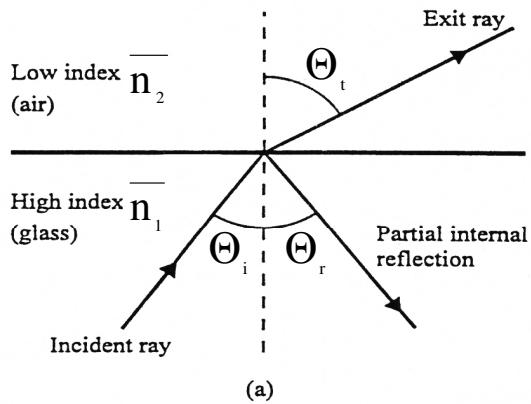
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Law of reflection $\theta_i = \theta_r$ ($i = \text{incident}; r = \text{reflected}$)

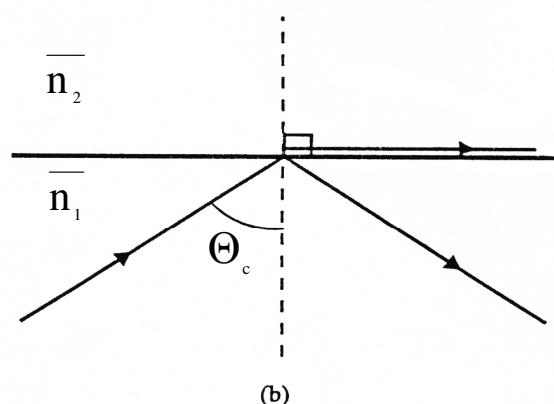
Snell's law $\bar{n}_1 \sin \theta_i = \bar{n}_2 \sin \theta_t$ (deutsch: Brechungsgesetz)

for $\theta_i > \theta_c$ critical angle \rightarrow only a reflected beam

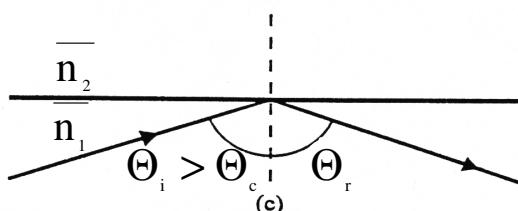
Snell's law can no longer be fulfilled with real angles θ_t .



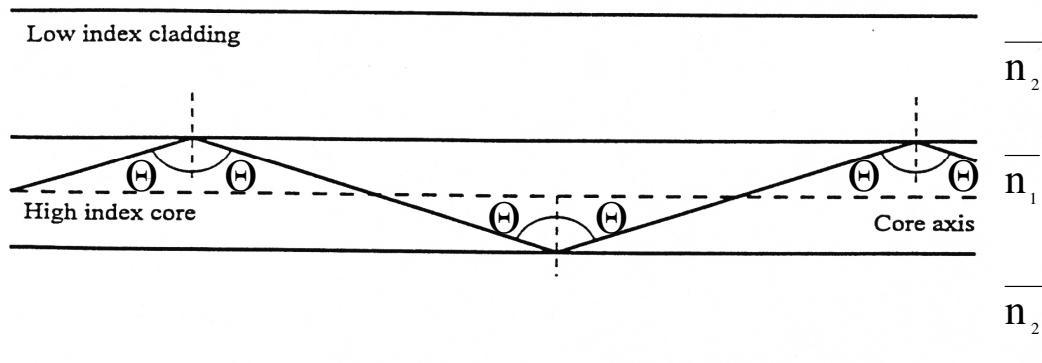
(a)



(b)



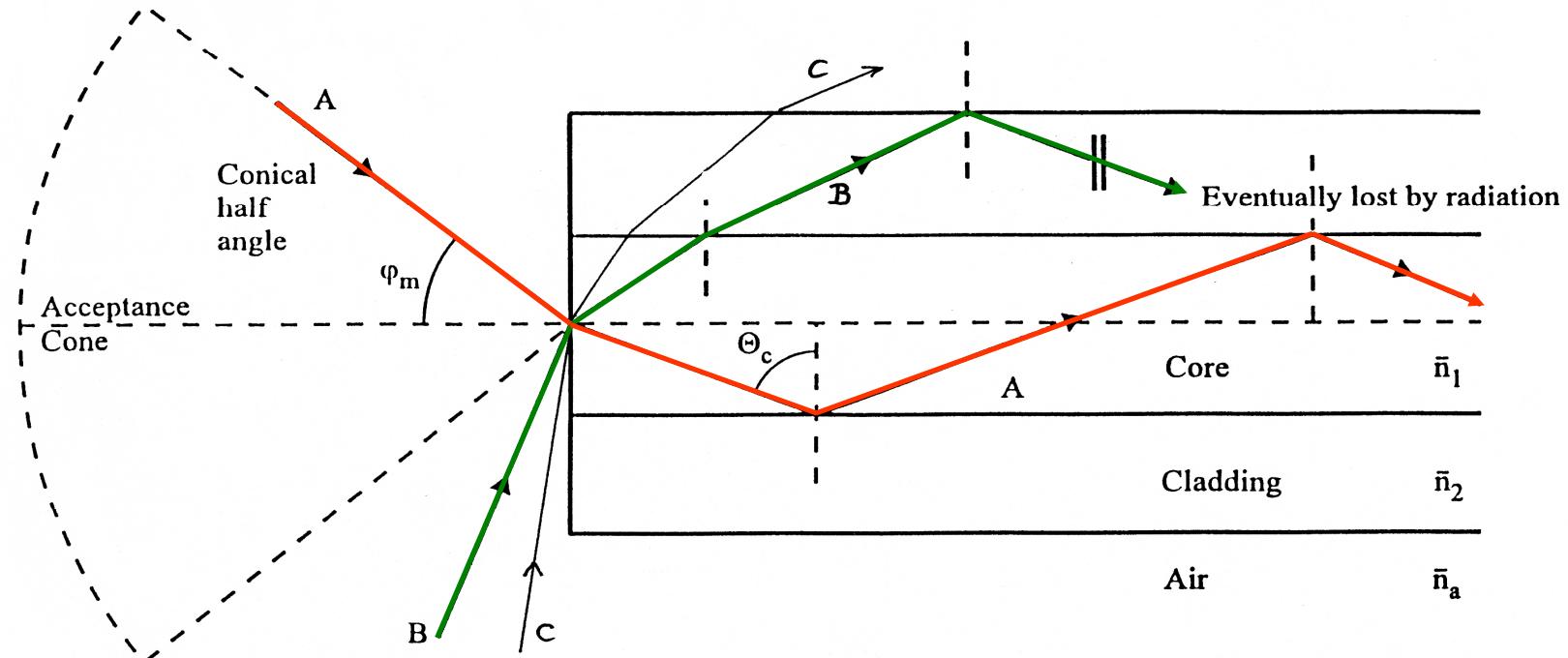
Light rays incidence on high to low refractive index interface. (a) Refraction and partial reflection. (b) Limiting case of $\theta_i \geq \theta_c$ where the transmitted beam travels under an angle of 90° with respect to the normal. (c) Total internal reflection for $\theta_i > \theta_c$.



Guiding of a light ray by total internal reflection in a high index medium \bar{n}_1 surrounded by a low index medium \bar{n}_2 ($\bar{n}_2 < \bar{n}_1$) as in a perfect optical fibre.

Acceptance angle of fibre waveguides

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Rays A and B are launched into the fibre. An incident ray is refracted at the core-air interface. For sufficiently small angles φ : total internal reflection at the core-cladding interface (zig – zag path).

A - core mode or guided mode

B - cladding mode ($\varphi > \varphi_m$) , high losses, due to interface roughness

C - radiation mode

Maximum acceptance angle φ_m , numerical aperture optoelectronic devices

using $\theta = \theta_c$ and Snell's law

refractive index difference

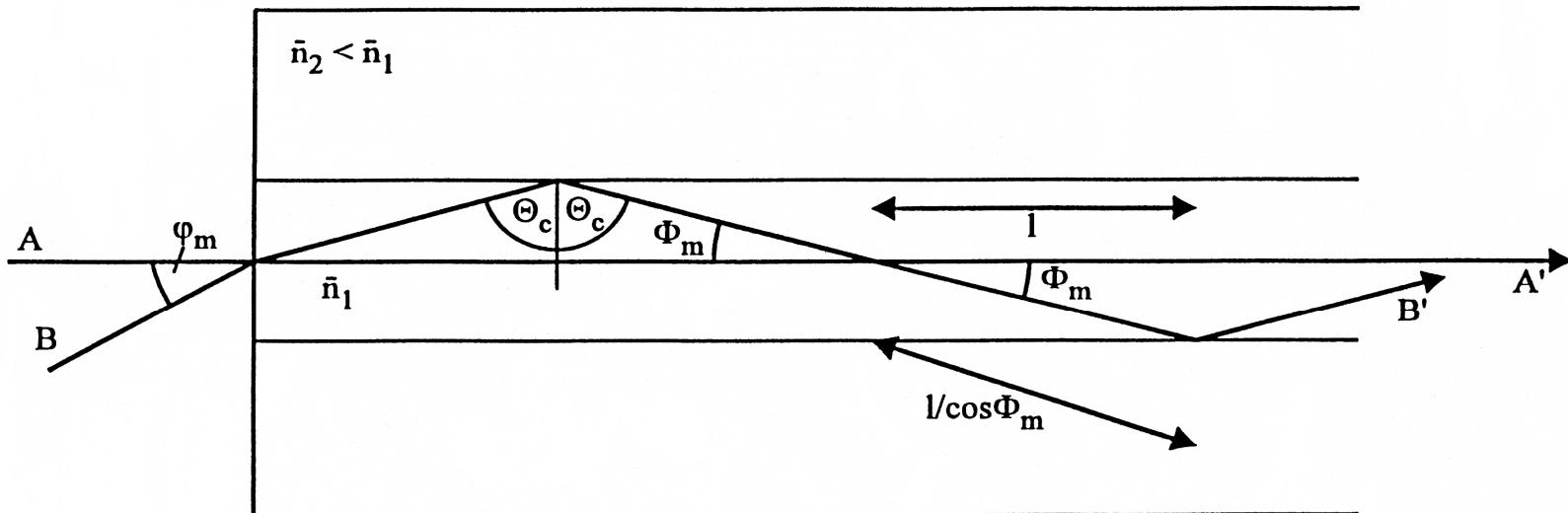
$$\Delta n = \bar{n}_1 - \bar{n}_2$$

$$\bar{n} = (\bar{n}_1 + \bar{n}_2)/2$$

mean refractive index

$$\varphi_m = \arcsin \sqrt{2 \cdot \bar{n} \cdot \Delta n}$$

$$\text{numerical aperture } NA = \sin \varphi_m$$



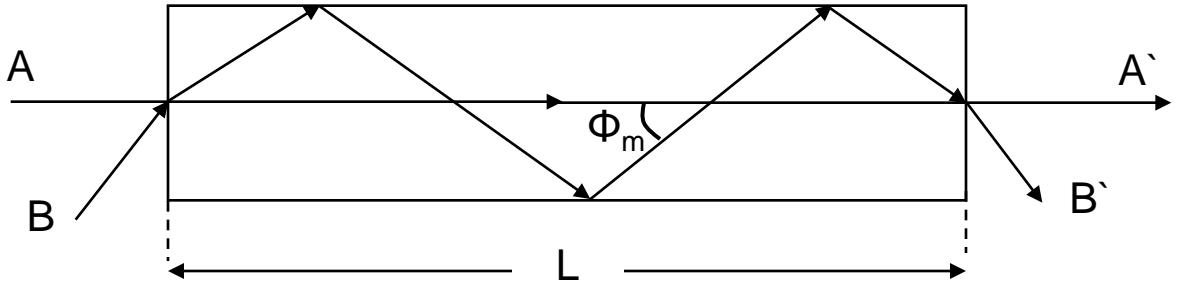
AA' : axial ray

BB' : critical core mode (total internal reflection at the core-cladding interface)

due to symmetry reasons the max. acceptance angle and the radiation angle at the end of the fibre are identical

Modal dispersion in a step-index fibre optoelectronic devices

Different guided modes propagate on zig-zag paths under different angles.



AA` is approximated. Since Φ_m is very small, AA` is called the axial path.

propagation of a δ – pulse:

$$\text{AA}': \text{travelling time } t_a = L \frac{\bar{n}_1}{c} \quad \Phi_m = 90^\circ - \theta_c$$

$$\text{BB}': t_b = \frac{L}{\cos \Phi_m} \cdot \frac{\bar{n}_1}{c} = \frac{L}{\sin \theta_c} \cdot \frac{\bar{n}_1}{c} = \frac{\bar{n}_1^2 L}{n_2 \cdot c}$$

time difference (pulse spreading)

$$\Delta t = t_b - t_a = \frac{\bar{n}_1 L}{n_2 \cdot c} \Delta \bar{n}$$

modal dispersion (= multipath time dispersion)

$$\frac{\Delta t}{L} = \frac{\bar{n}_1 \Delta \bar{n}}{n_2 \cdot c}$$

(this model provides the correct result but is too simple and will be corrected later.)

(length related to pulse spreading)

to avoid intersymbol interference of „1“ and „0“

$$\text{max. bit rate: } B = \frac{1}{\Delta t} = 2 f_{\max}$$

bandwidth – length product:

$$f_{\max} \cdot L = \frac{c \cdot \bar{n}_2}{2 \Delta n \cdot \bar{n}_1}$$

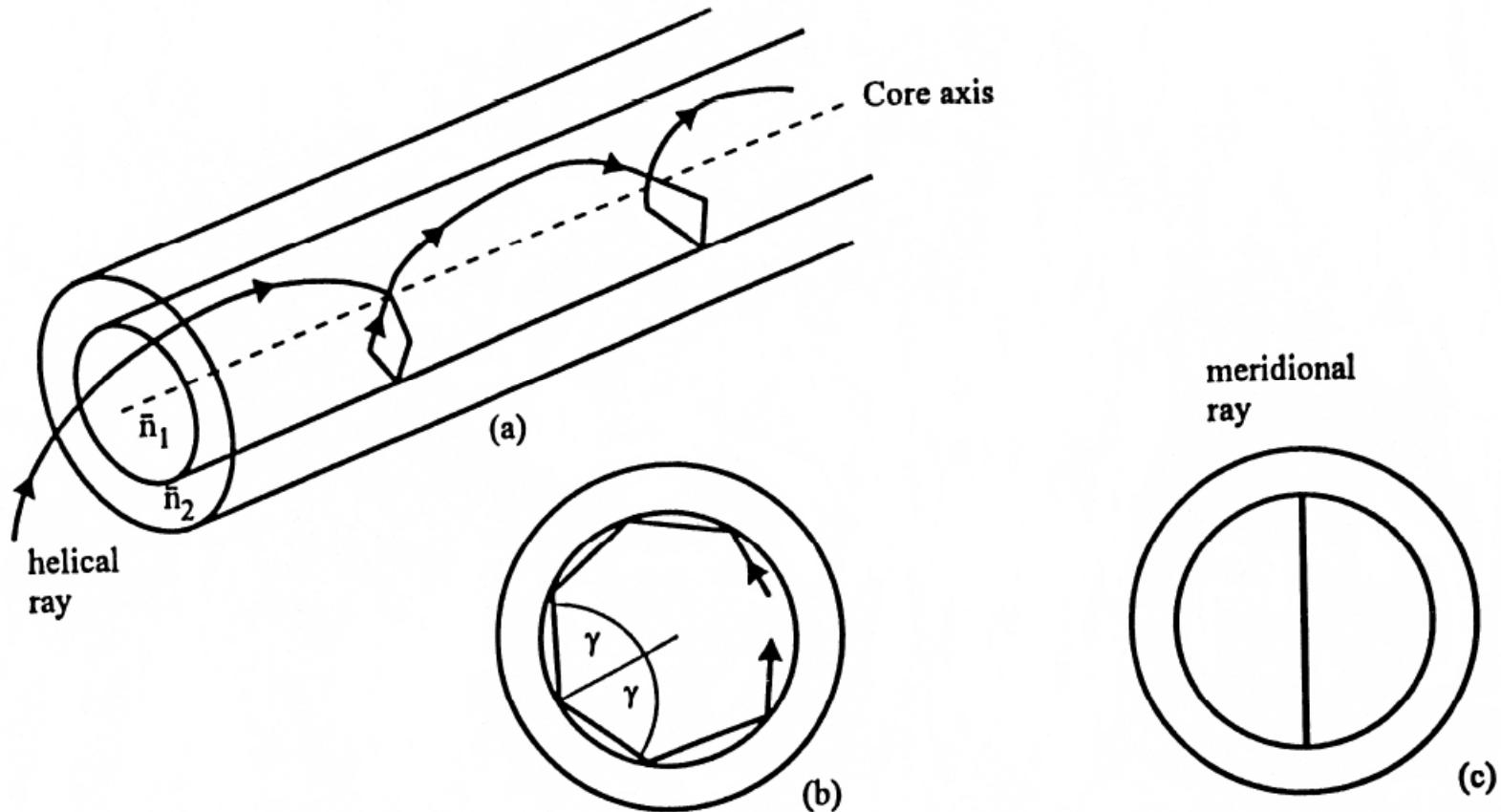
bit – rate – length product:

$$BL = c \cdot \bar{n}_2 / (\Delta n \cdot \bar{n}_1)$$

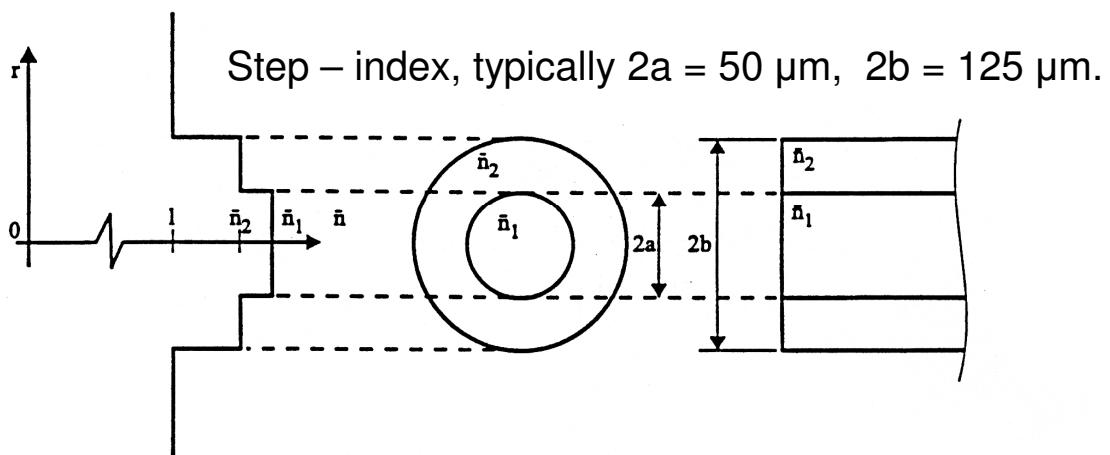
Helix modes

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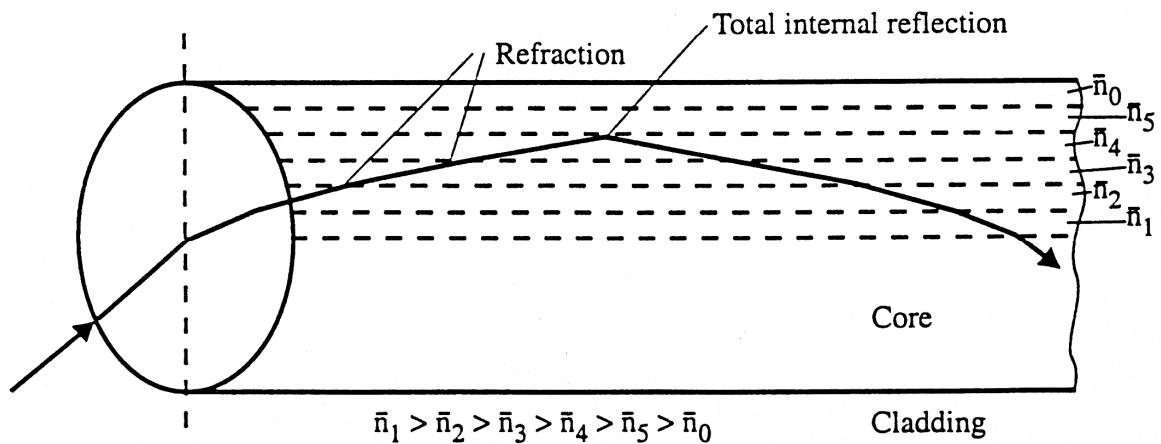
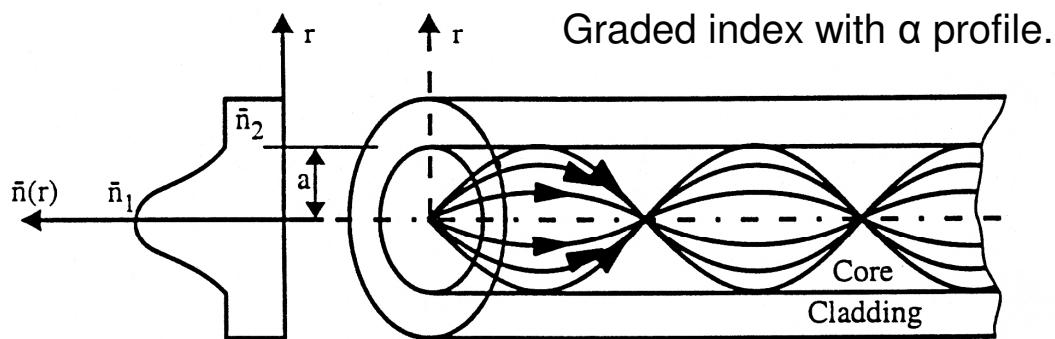
Up to now meridional rays, traveling through the fibre axis were considered.



However, a larger number follows helical paths, undergoing a much larger number of reflections at the core-cladding interface → higher losses and higher modal dispersion but less important as meridional modes.

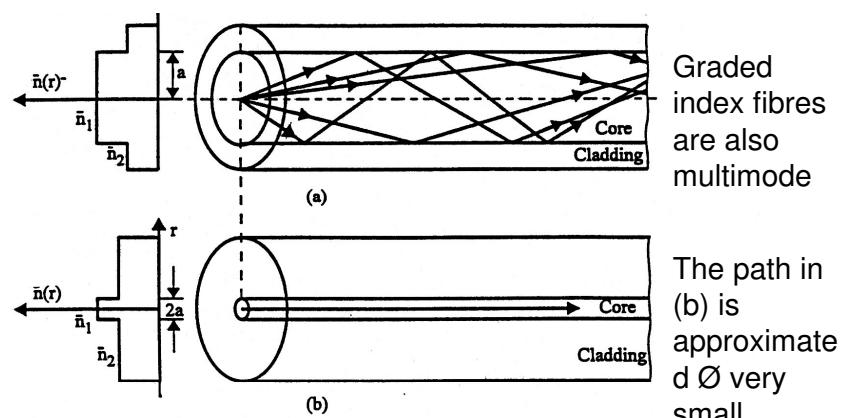


The relatively small bit – rate – length product of step – index fibres initiated the development of graded – index fibres.



multi –mode fibre

here: step – index

**single – mode
fibre**

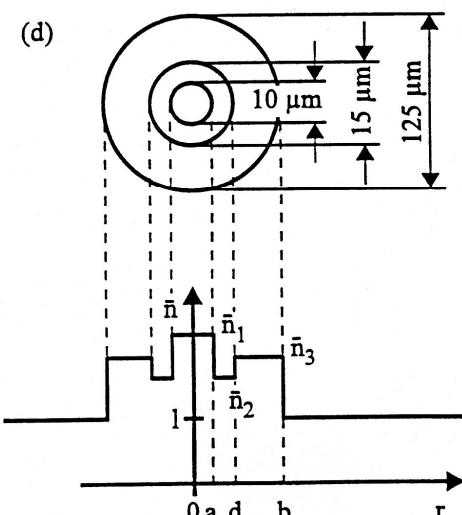
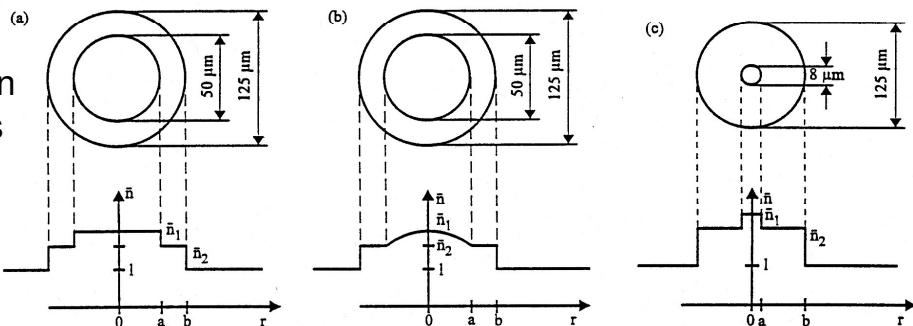
Graded index fibres
are also
multimode

The path in
(b) is
approximate
 $d \varnothing$ very
small

The importance of graded index fibres has somewhat declined due to the development of single – mode fibres ($\Delta n = 0.01$, narrow core : $2a = 8 \mu\text{m}$).

Single – mode fibres : only a single zig-zag path under a well defined angle.
Description requires a wave – theoretical model .

In comparison
again 4 types
of fibres :



- Step – index multimode fibre
- Graded index multimode fibre
- Step – index single-mode fibre
- Single-mode fibre

Modern and future single mode fibre types

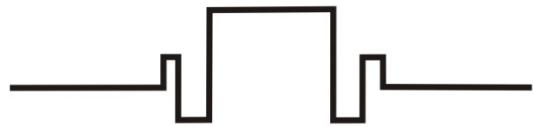
Single-clad fibre



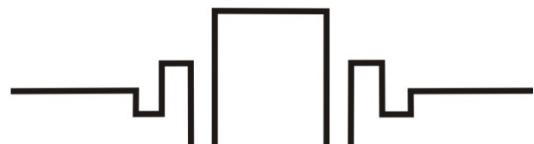
Double-clad fibre



Triple-clad fibre



Quadruple-clad fibre



Refractive index profile of an α-type graded index fibre

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$$\bar{n}(r) = \begin{cases} \bar{n}_1 \left(1 - 2\Delta \left(\frac{r}{a} \right)^\alpha \right)^{\frac{1}{2}} & \text{for } r > a \text{ in the core} \\ \bar{n}_1 (1 - 2\Delta)^{\frac{1}{2}} = \bar{n}_2 & \text{for } r > a \text{ in the cladding} \end{cases}$$

$$\Delta = \frac{\bar{n}_1^2 - \bar{n}_2^2}{2\bar{n}_1} \approx \frac{\bar{n}_1 - \bar{n}_2}{\bar{n}_1}$$

Refractive index profile of a graded index fibre with α – profile. Δ is the mean relative refractive index difference between core and cladding (the approximation holds for $n_1 \approx n_2$). $\rightarrow \Delta \ll 1$.

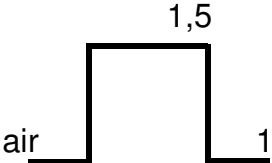
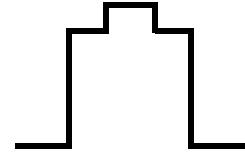
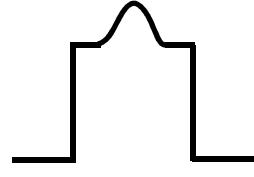
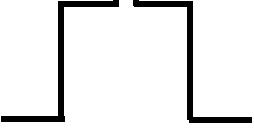
The profile parameter $\alpha = 0 \dots \infty$. The optimum is usually close to the parabolic profile ($\alpha = 2$). In practice α has to be carefully controlled during the technological process.

Sinusoidal trajectories for the ray propagation in the core.

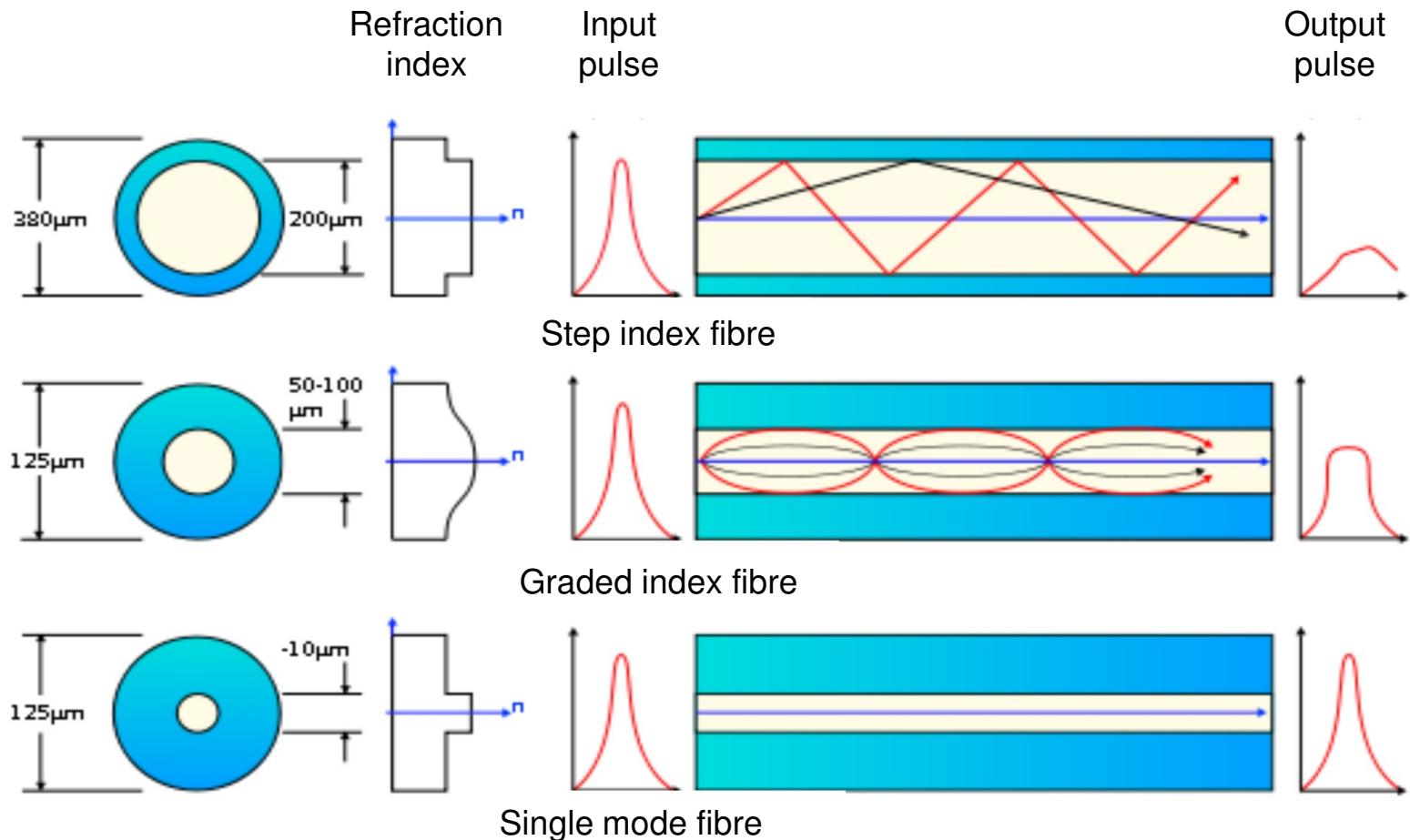
- Rays close to the axis : shorter paths but with higher \bar{n} \rightarrow lower propagation velocity
- Rays in the outer regions : longer paths but also lower \bar{n} regions \rightarrow higher propagation velocity.

The difference in propagation velocity path compensates for the path difference
 \rightarrow multiple path dispersion reduced to

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Fibre type	 air			
Modal dispersion $\Delta t / L$	2500 ns / km	30 ns / km	0,1 ns / km	This is no longer a problem for single mode fibres. The limits are there dominated by the remaining spectral dispersion (which, however, is much smaller than modal dispersion)
Bit-rate length product $B \cdot L$	$500 \frac{\text{kbit}}{\text{s}} \cdot \text{km}$	$30 \frac{\text{Mbit}}{\text{s}} \cdot \text{km}$	$10 \frac{\text{Gbit}}{\text{s}} \cdot \text{km}$	

optoelectronic devices

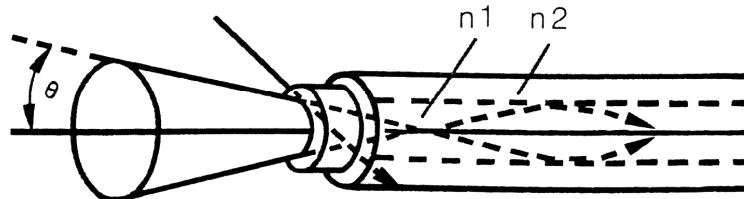


Conclusion: fibre

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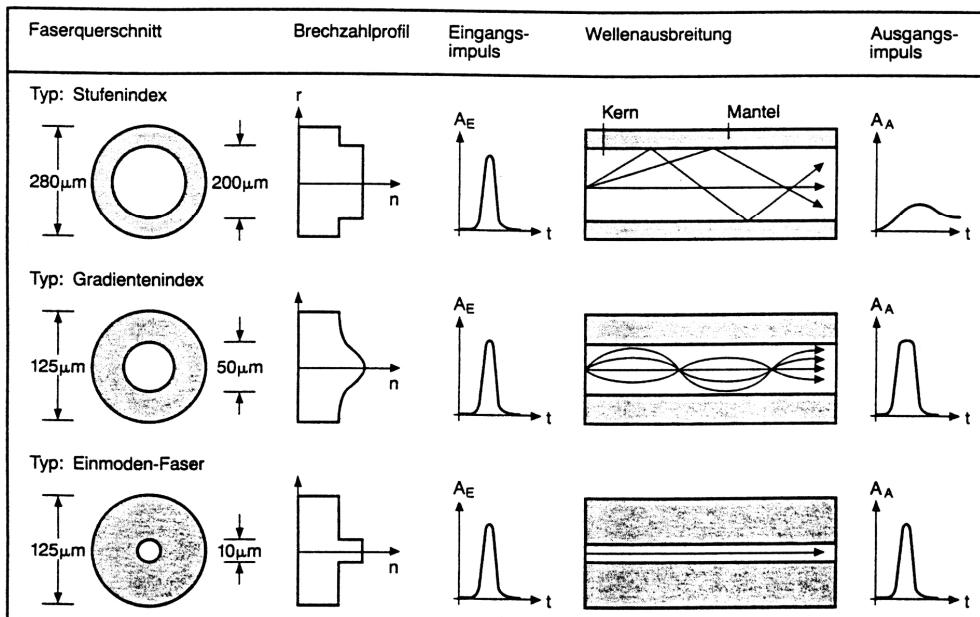
Optical fibre consists of a transparent core and a cladding material with low attenuation. Used to transmit informations by light waves.

Basic principle for optical transmission is the total internal reflection based on the law of refraction. All light is reflected when a ray of light strikes a medium boundary at an angle larger than a particular critical angle with respect to the normal to the surface and the refractive index is lower on the other side of the boundary.



3 types of optical fibres can be differentiate with regard to the geometrical dimensions and the optical transmission characteristics:

- multimode fibre with step-index profile
- multimode fibre with graded-index profile
- single mode fibre with step-index profile



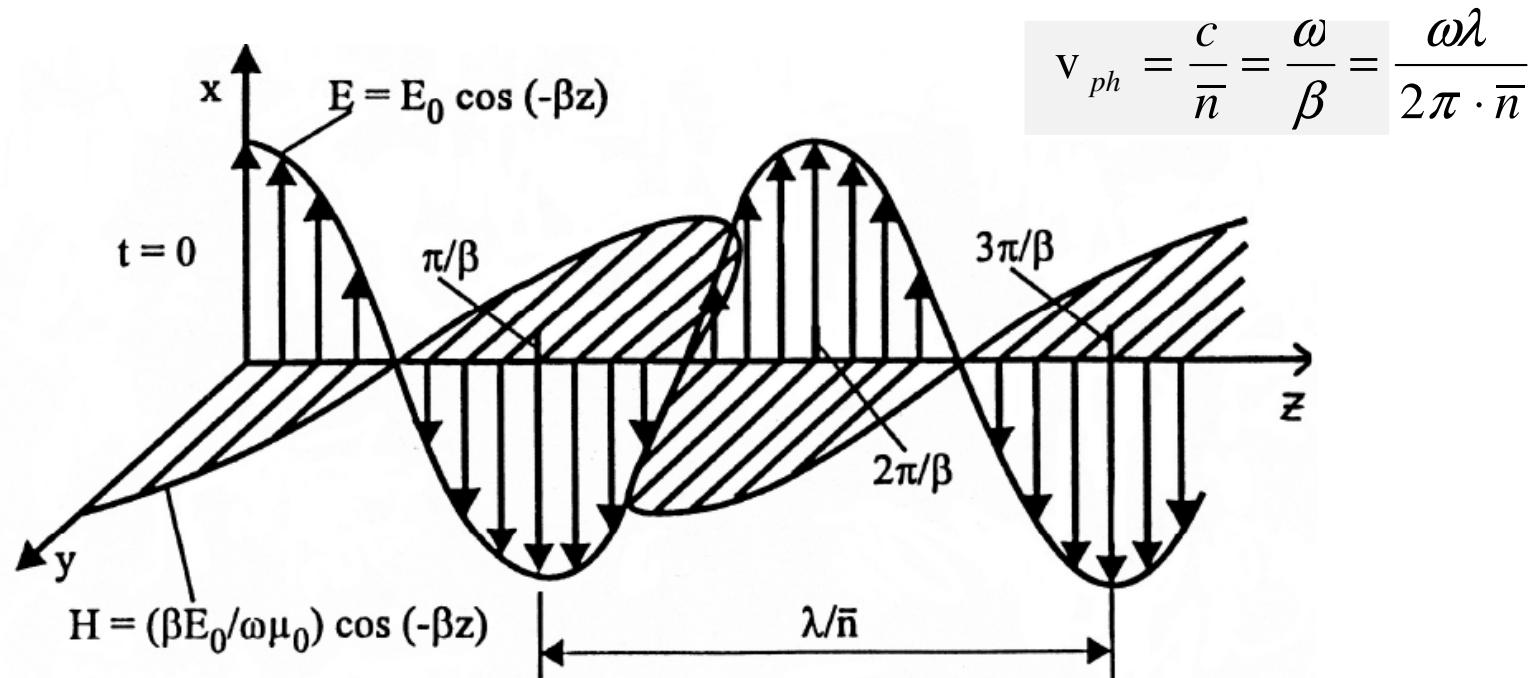
Plane electromagnetic wave

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Linear polarized wave of angular frequency ω propagating in z – direction :

$$E(x, y, z, t) = E_0 \exp(i\omega t - i\beta z), \quad E_0 = \text{complex amplitude}$$

a) lossless media: propagation constant is real: $\beta = \frac{2\pi}{\lambda/\bar{n}} = \frac{\omega \cdot \bar{n}}{c}$

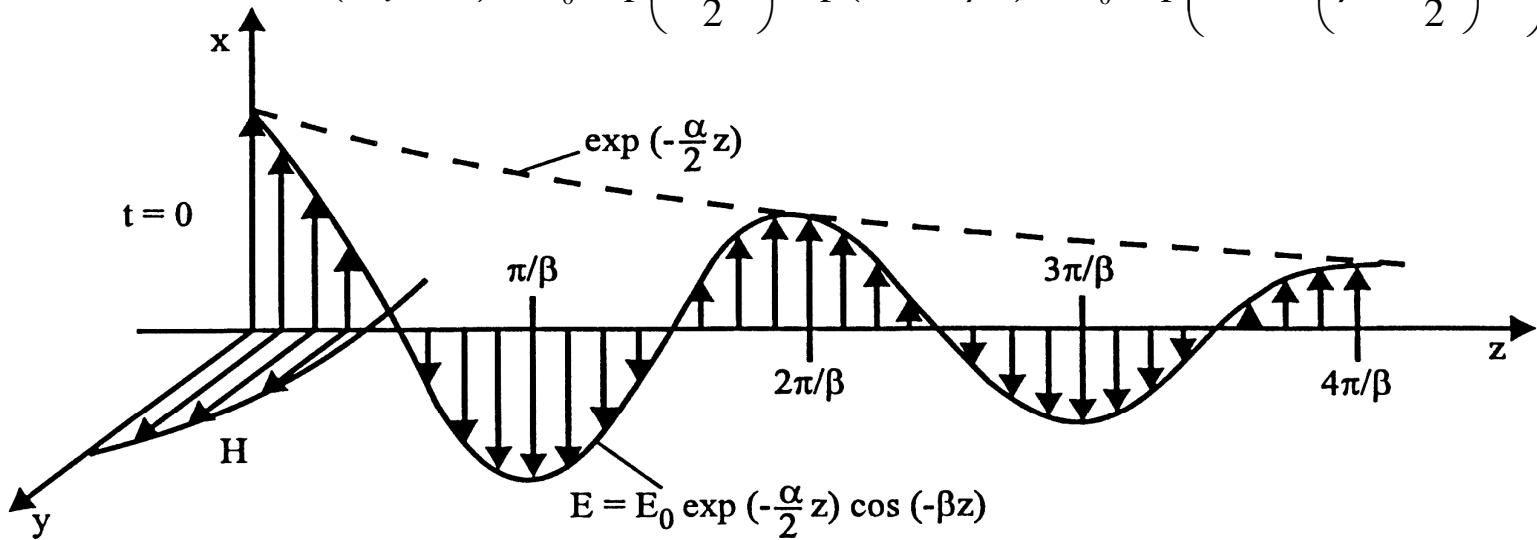


Plane electromagnetic waves II

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b) lossy media: $I(z) = I_0 \exp(-\alpha z) \sim |E_0|^2 \exp(-\alpha z)$

$$E(x, y, z, t) = E_0 \exp\left(\frac{-\alpha z}{2}\right) \exp(i\omega t - i\beta z) = E_0 \exp\left(i\omega t - i\left(\beta - \frac{i\alpha}{2}\right) \cdot z\right)$$



propagation constant
is complex

refractive index is
complex

extinction
coefficient

$$\gamma = \beta - i \cdot \frac{\alpha}{2} = \frac{\omega}{c} (\bar{n} - i \kappa)$$

$$\bar{\eta} = \bar{n} - i \kappa$$

$$\kappa = \frac{c \alpha}{2 \omega} = \frac{\alpha \lambda}{4 \pi}$$

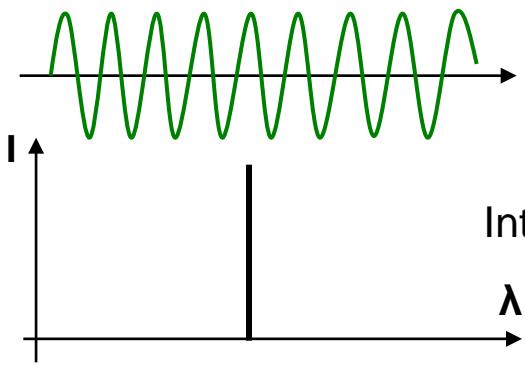
Propagation of light in media

optoelectronic devices

Often the same problems in understanding occur → first a short overview

Overview:

Monochromatic wave



$$\frac{\lambda}{n} \cdot f = \frac{c}{n}$$

f - frequency

c - vacuum light velocity

$$\beta = \frac{2\pi}{\lambda/n}$$

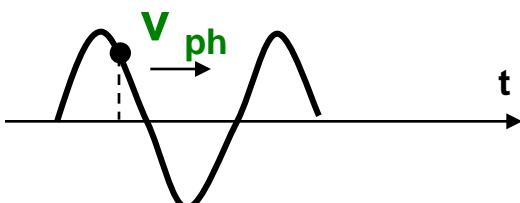
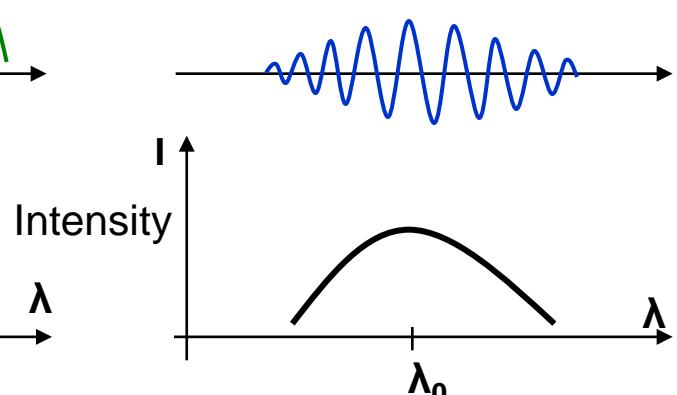
λ - vacuum wavelength

ω - angular frequency

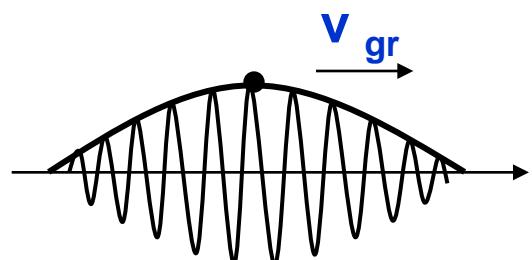
$$\omega = 2\pi \cdot f$$

β - propagation constant (wave vector)

wave packet (pulse in time domain)



propagation velocity of a point of fixed phase



Propagation velocity of the envelope of the packet (group velocity of the wave packet = phase velocity of the envelope)

$$v_{ph} = \frac{\omega}{\beta} = \frac{c}{n(\lambda)}$$

v_{ph} - phase velocity

\bar{n} - phase refractive index

$$v_{gr} = \frac{d\omega}{d\beta} \Big|_{\beta=\beta_0} = \frac{c}{n_{gr}(\lambda)}$$

v_{gr} - group velocity

\bar{n}_{gr} - group refractive index

$$\bar{n}_{gr} = \bar{n}(f_0) + f_0 \frac{\partial \bar{n}}{\partial f} \Big|_{f_0}$$

$f(t)$ and $F(f)$ connected by Fourier transformation:

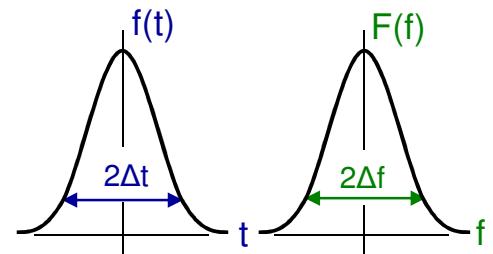
$$f(t) = \int_{-\infty}^{\infty} F(f) \cdot e^{i2\pi \cdot f \cdot t} df \quad F(f) = \int_{-\infty}^{\infty} f(t) \cdot e^{-i2\pi \cdot f \cdot t} dt$$

i.e. $f(t)$ is composed of elementary sinusoidal oscillations

1. Bell-shaped pulse (Gaussian pulse)

$$f(t) = \frac{1}{\Delta t} \cdot \exp\left(-\pi \frac{t^2}{\Delta t^2}\right)$$

$$F(f) = \exp\left(-\pi \cdot \Delta t^2 \cdot f^2\right) = \exp\left(-\pi \frac{f^2}{\Delta f^2}\right)$$



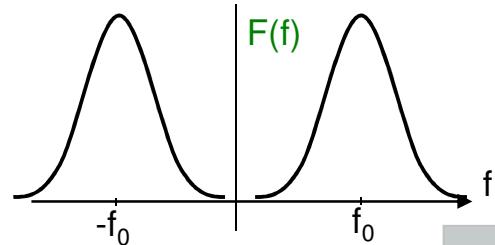
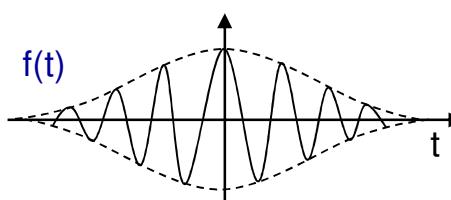
Δt , Δf – characteristic widths in time and spectral domains are inversely related $\Delta f = (\Delta t)^{-1}$ → broad pulses in time produce narrow pulses in spectrum and vice versa.

2. Gaussian pulse with high frequency carrier $\omega_0 = 2\pi f_0$

$$f(t) = \frac{1}{\Delta t} \cdot \exp\left(-\pi \frac{t^2}{\Delta t^2}\right) \cos \omega_0 t = \frac{1}{2\Delta t} \exp\left(-\pi \frac{t^2}{\Delta t^2}\right) [e^{i\omega_0 t} + e^{-i\omega_0 t}]$$

envelope again gaussian

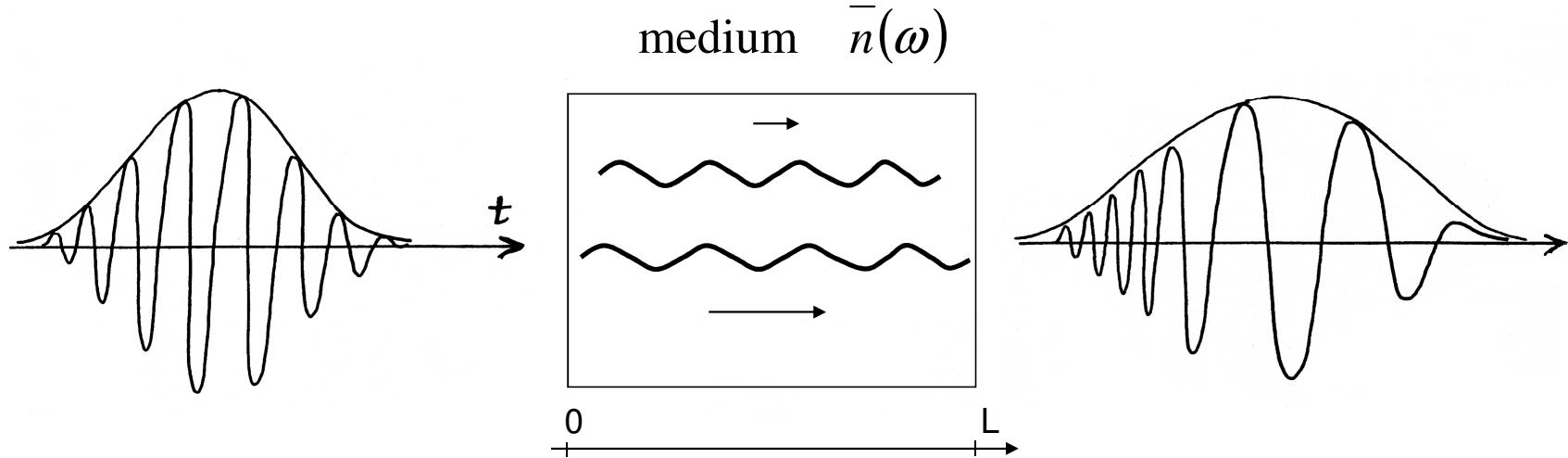
$$2F(f) = \exp\left(-\pi \frac{(f-f_0)^2}{\Delta f^2}\right) + \exp\left(-\pi \frac{(f+f_0)^2}{\Delta f^2}\right)$$



Note: Gaussian pulse with complex carrier $\exp(i\omega_0 t)$ has the spectrum

$$\exp\left(-\pi \frac{(f-f_0)^2}{\Delta f^2}\right)$$

Pulse propagation in a dispersive medium $\bar{n} = \bar{n}(\omega)$ optoelectronic devices



Superposition of sinusoidal spectral components

$$F(t, z=0) = \int_{-\infty}^{\infty} F(f) e^{i 2\pi f t} df$$

Each component reveals an individual time delay $t'(f) = L/V_{ph}(f)$

$$V_{ph}(f) = \frac{2\pi f}{\beta(f)} = \frac{c}{n(f)}$$

Time delays t' lead to phase shift of the components at the output $z = L$

$$F(t, z=L) = \int_{-\infty}^{\infty} F(f) e^{i 2\pi f (t-t'(f))} df$$

The contribution of dispersion to pulse broadening is $\Delta t_D = \frac{2\pi L}{\Delta t} \cdot \frac{d^2 \beta}{d\omega^2}$ $\frac{d\beta}{d\omega} = \frac{1}{V_{gr}(\omega)}$ $\beta(\omega) = \frac{\omega}{c} \bar{n}(\omega)$
 \rightarrow pulse broadening \uparrow with $\Delta t \downarrow$, with chromatic dispersion \uparrow ($\frac{d^2 \beta}{d\omega^2} \uparrow$).

Short pulses have broad spectra; spectral components with a large frequency spacing travel at noticeably different speeds \rightarrow noticeably different arrival times at the output \rightarrow noticeably phase shifts \rightarrow broad pulses.

Internal reflection of monochromatic plane waves

1

optoelectronic devices

Helmholtz equation :
media

$$\Delta E + \frac{\omega^2 \eta^2}{c^2} E = 0$$

here lossless

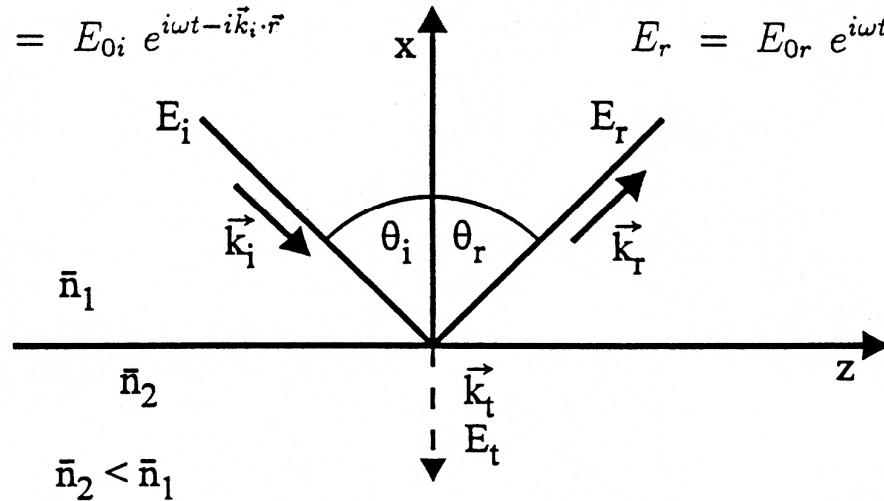
el. field $E(\underline{r}, t) = E(x, y, z, t)$

here $y = 0$

$$E_i = E_{0i} e^{i\omega t - i\vec{k}_i \cdot \vec{r}}$$

$$E_r = E_{0r} e^{i\omega t - i\vec{k}_r \cdot \vec{r}}$$

$$|E_{0r}| = |E_{0i}|$$



$$E_t = E_{0t} e^{i\omega t - ik_{tz} z + k_{tx} x}$$

Incident and reflected waves have
to fulfill the dispersion relation:
(according to Helmholtz equation)

$$k_{ix}^2 + k_{iz}^2 = \frac{\omega^2 n_1^{-2}}{c^2} = n_1^{-2} k^2$$

For medium n_2 internal reflection requires a plane wave solution propagating in z -direction but exponentially decaying in $-x$ direction (see figure above).

Therefore : x -component of \underline{k}_t is complex: $\underline{k}_t = (ik_{tx}, 0, k_{tz}) = (ik_{tx}, 0, k_{iz})$

$k_{tz} = k_{iz}$ is a consequence of the required continuity of tangential electric and magnetic field components.

According to Helmholtz equation the
dispersion relation requires :

$$k_{tz}^2 - k_{tx}^2 = \frac{\omega^2 n_2^{-2}}{c^2} = n_2^{-2} k^2$$

Interference of incident and reflected waves

optoelectronic devices

1

→ different field profiles in x – direction (this sheet)

→ different V_{ph} in z – direction

θ_{ia}

case

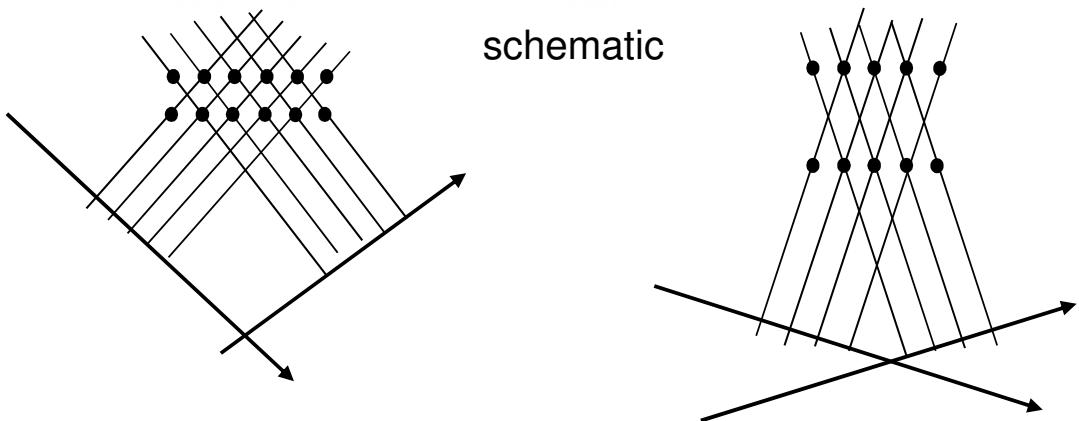
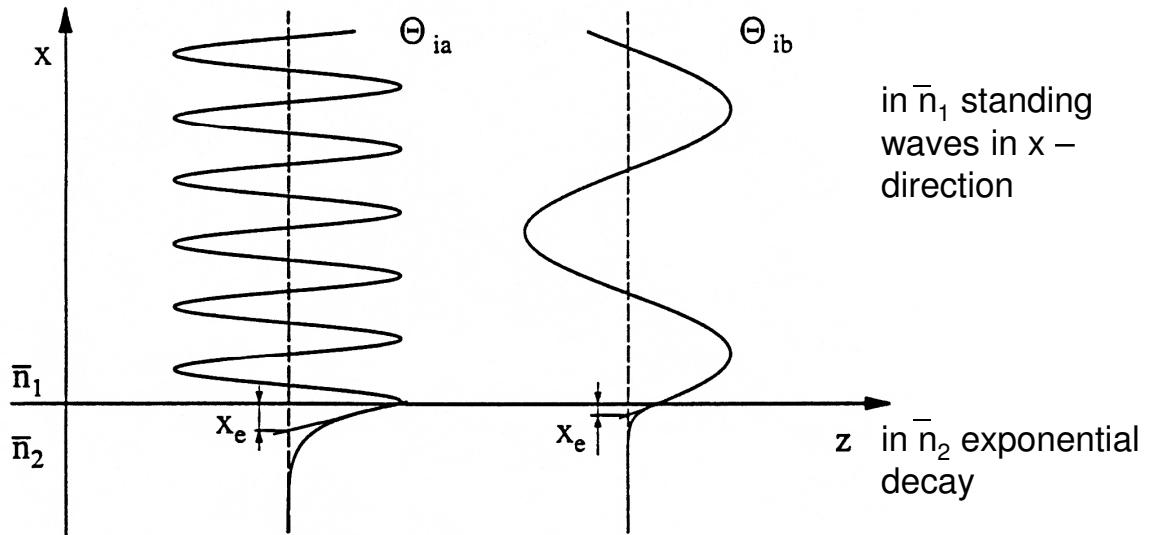
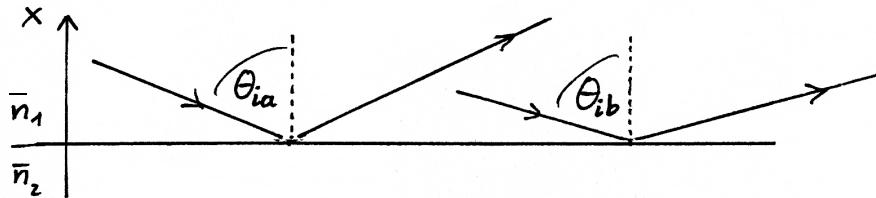
θ_{ib}

case

Illustration for 2 angles above θ_c : $\theta_c < \theta_{ia} < \theta_{ib}$

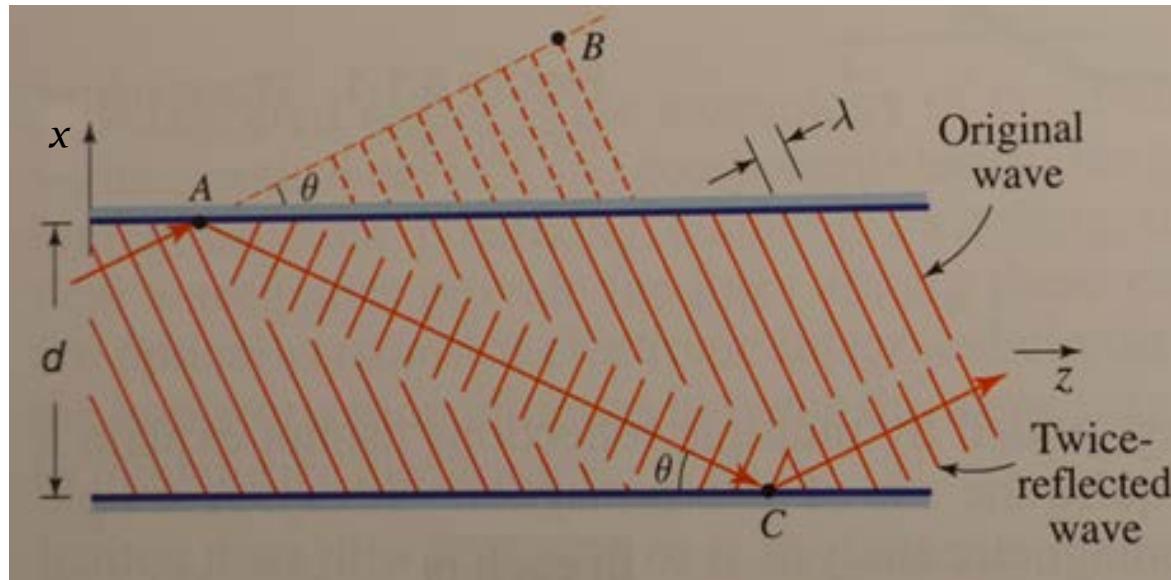
a

b



The original wave undergoes interference with the wave reflected twice at the two interfaces

1. We consider the ray model with a plane wave neglecting the penetration into the cladding



(ideally reflecting mirrors
at the interfaces).

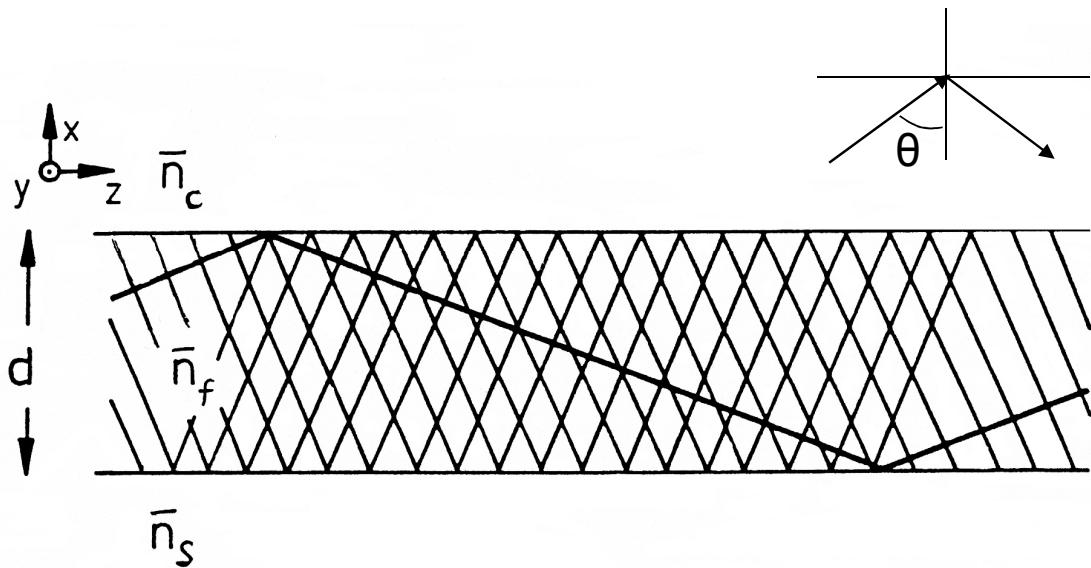
When constructive interference condition is satisfied, the phases of the two upward oriented plane waves reveal a phase shift of an integer multiples of λ .

2. Ray model with a plane wave but including the phase-shifts at the interfaces (see below).
3. Complete wave model, Solution of Helmholtz equation (see below).

Origin of modes in an optical waveguide

A simple illustration: modes correspond to an distinct angle θ .

A uniform total field in which all sub waves interfere constructively (although multiple reflections, zig-zag paths) corresponds to a mode.



→ only distinct θ provide this constructive interference and thus a uniform total field.

In reality : more complicated due to the phase – shifts (2ϕ) occurring during each internal reflection at the interfaces. Phase – shifts depend on all involved refractive indices and θ ; described by Fresnel equations.

Result :

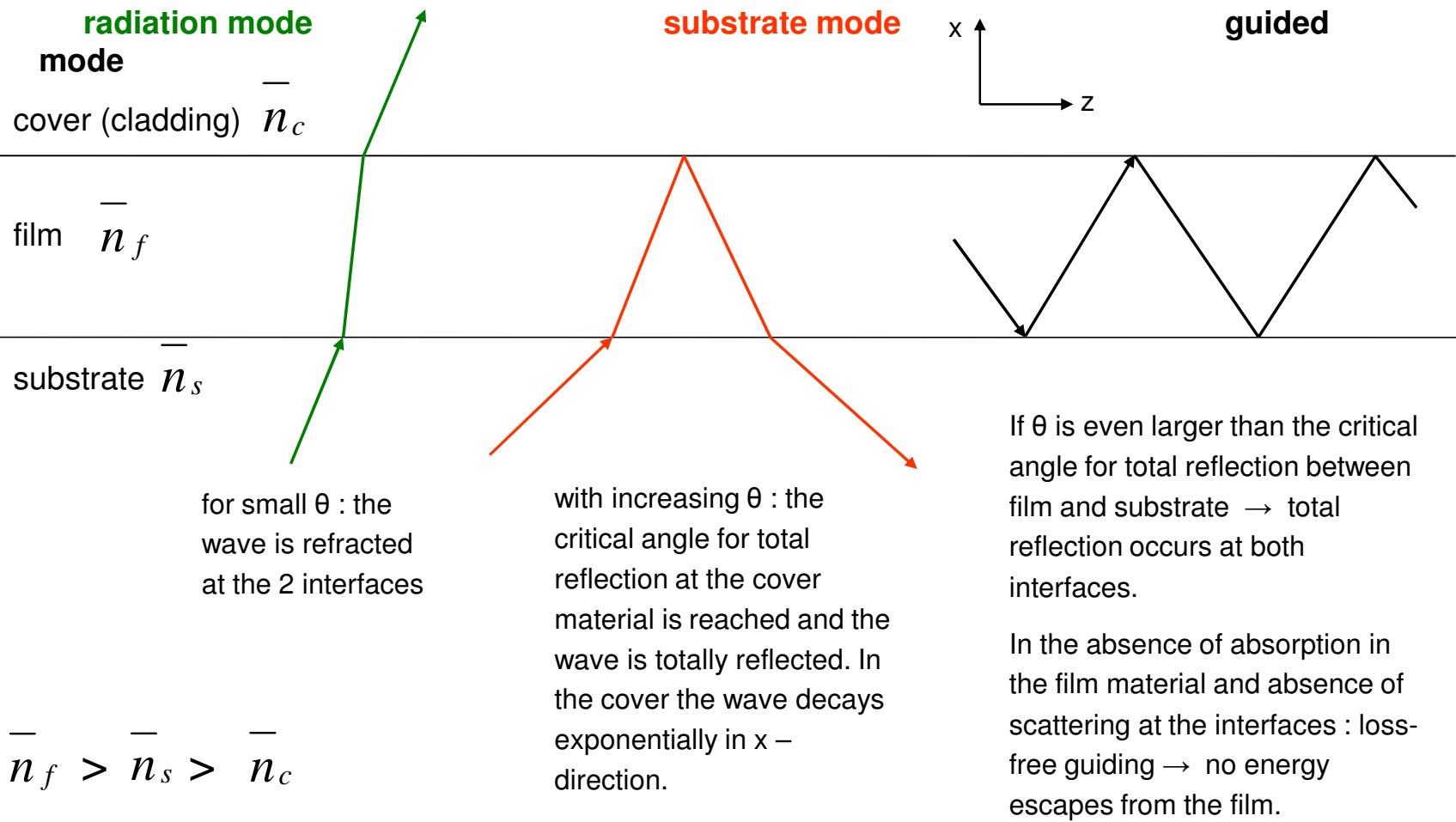
$$\tan \varphi = \frac{\sqrt{n_f^2 - \sin^2 \theta_i} - n_c}{n_f \cdot \cos \theta_i}$$

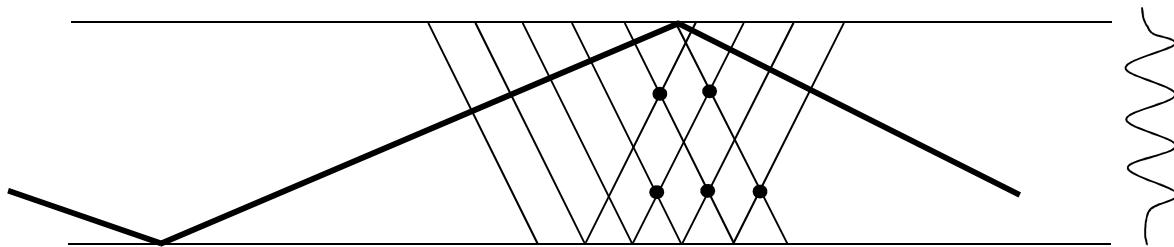
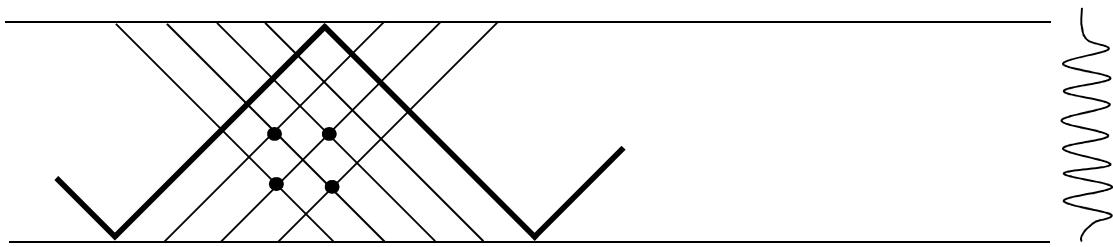
for TE fields

for the lower interface : replace n_c by n_s

Two - dimensional planparallel films

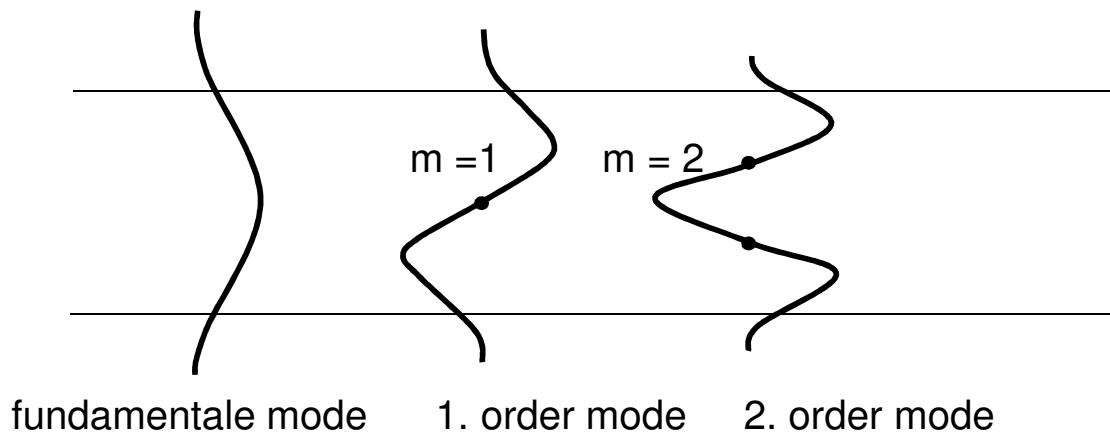
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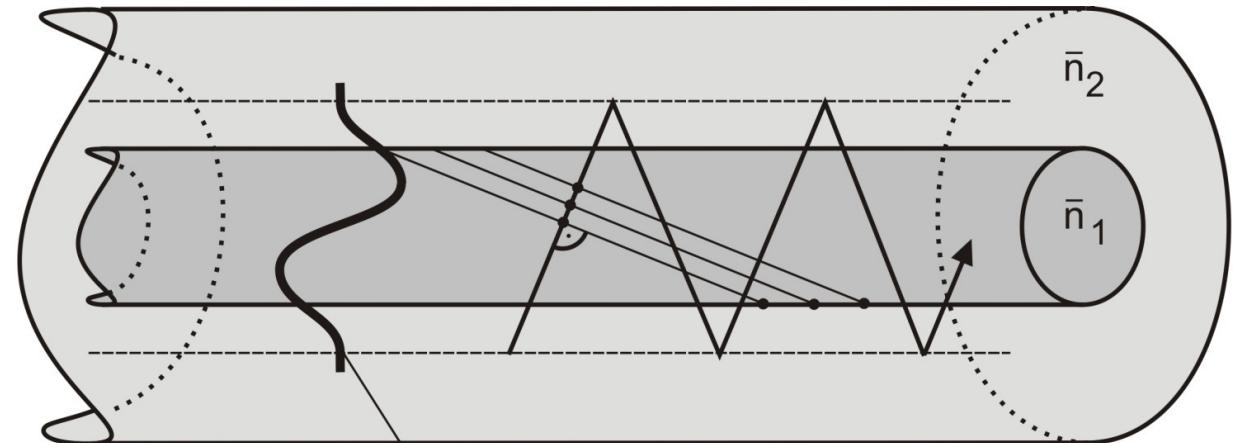


The order of the mode is given by the number of nodes (Knoten).

m is the order of the mode

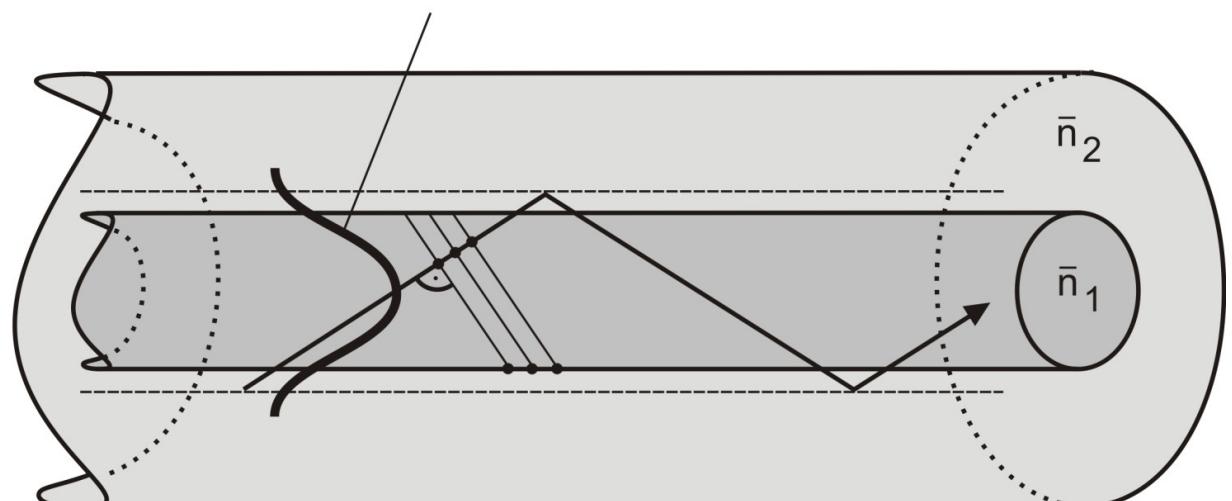


Light propagation in a multimode fibre optoelectronic devices



$m = 1$

Eigenfunction



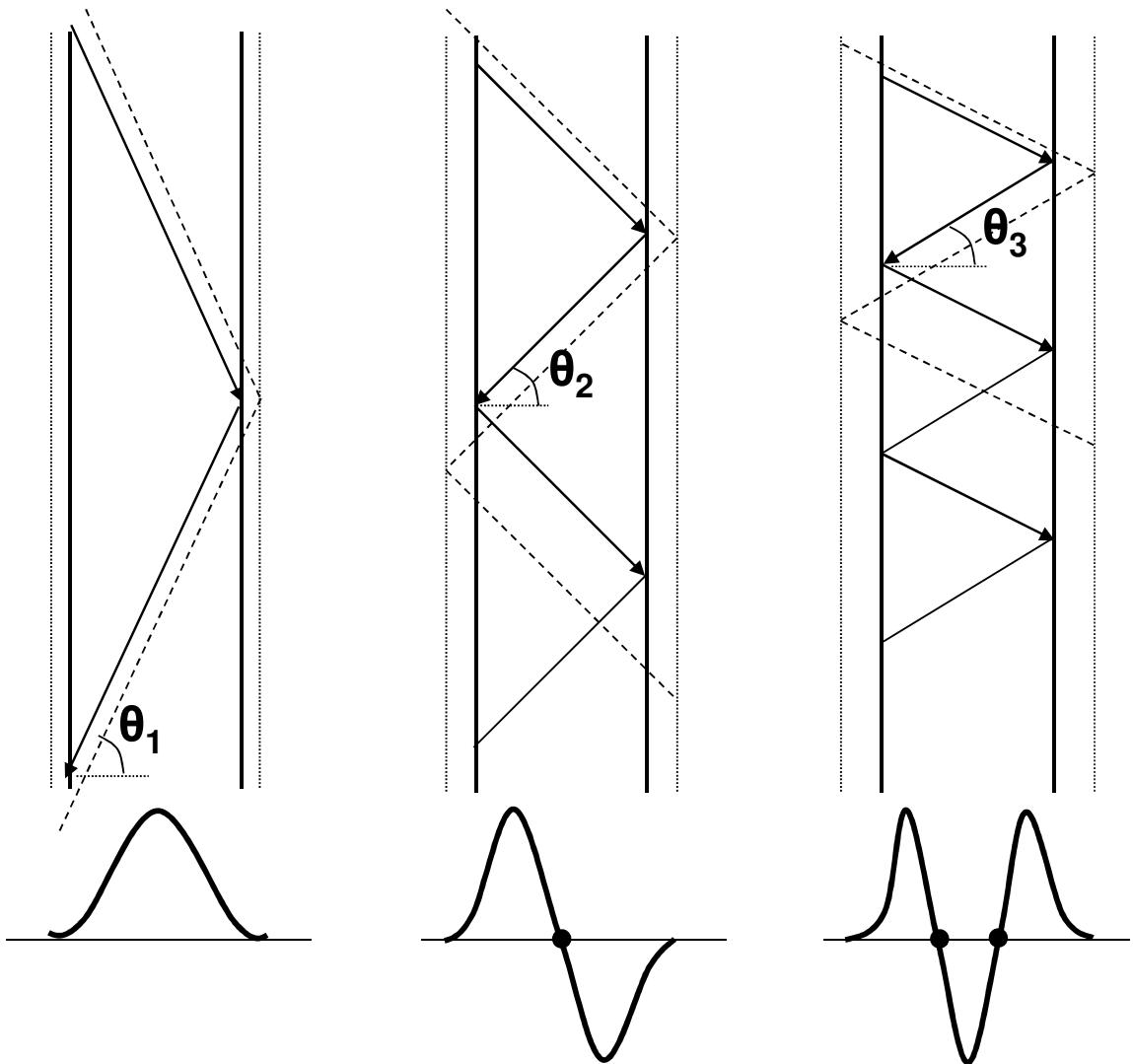
$m = 0$

Summary of essential features

optoelectronic devices

— neglecting Goos-Hänchen shift

- - - including Goos-Hänchen shift (virtual reflecting plane)



fundamental mode

$$\bar{n}_{eff\ 1} >$$

$$v_{ph1} <$$

$$\bar{n}_{eff} = n_f \cdot \sin \theta$$

1. order mode

$$\bar{n}_{eff\ 2} >$$

$$v_{ph2} <$$

$$\bar{n}_c \leq \bar{n}_s < \bar{n}_{effi} < \bar{n}_f$$

2. order mode

$$\bar{n}_{eff\ 3}$$

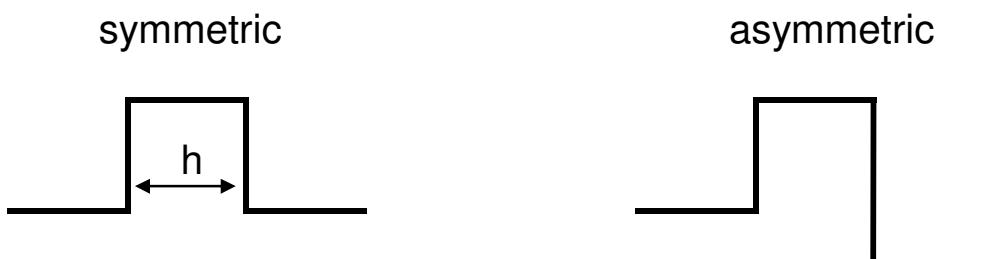
$$v_{ph3}$$

Only the fundamental mode can propagate → a single distinct θ ; all other θ do not provide a uniform constructive interference.

$$\text{normalized frequency} = kh\sqrt{n_1^2 - n_2^2} \quad \text{symmetric case}$$

3 possibilities to make a waveguide monomode :

- to choose λ large enough
- to choose waveguide thickness h small enough
- to choose the difference $n_1^2 - n_2^2$ small enough

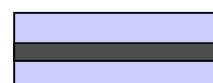


always at least one solution (fundamental mode). The wider h , the more modes exist.

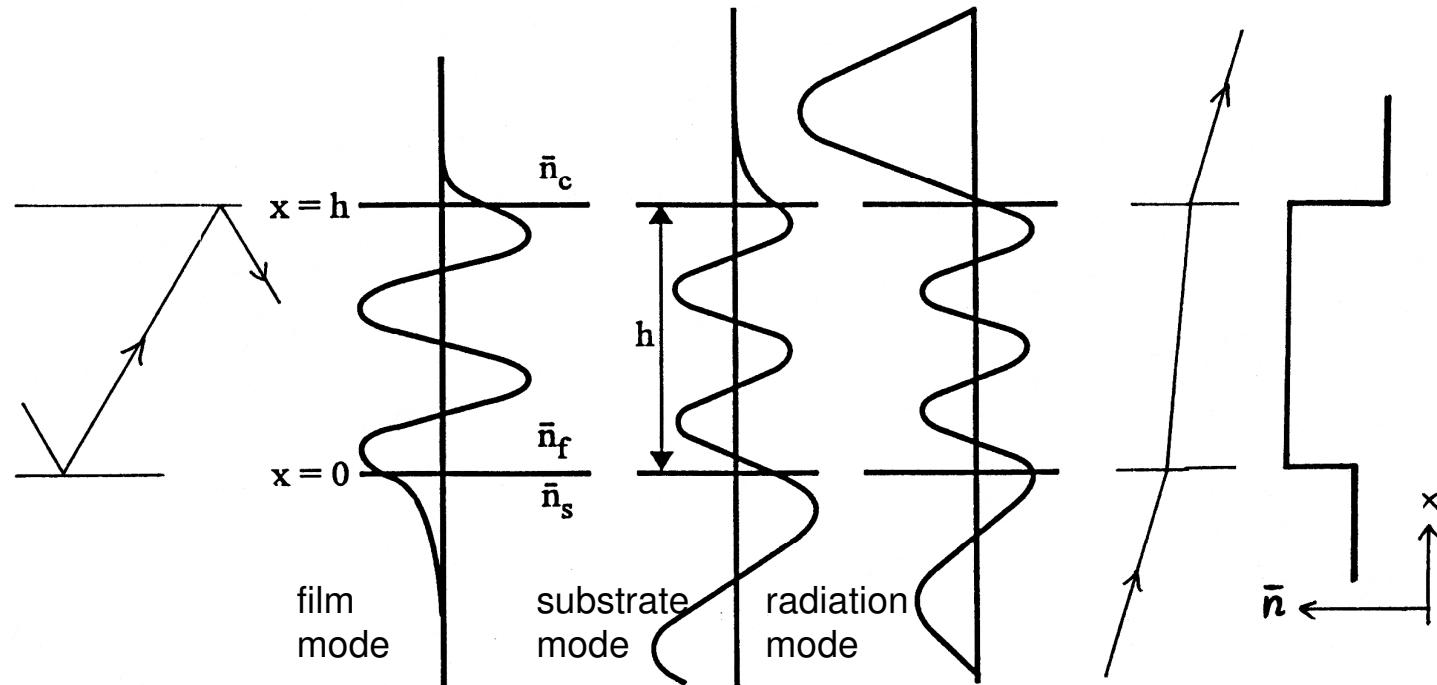
for small h it is possible that no solution exists.

reversely : for a given h , wave guiding exists only below a cut-off frequency.

Note : a planar waveguide is involves 1D problem and a fibre involves a 2D problem. Look similar in a cross-sectional view, but have totally different mode structure !



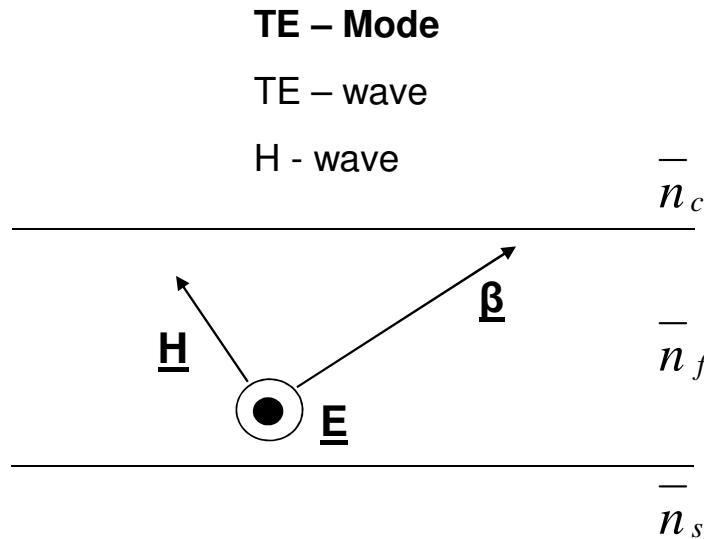
Examples for field distributions – planar waveguide optoelectronic devices



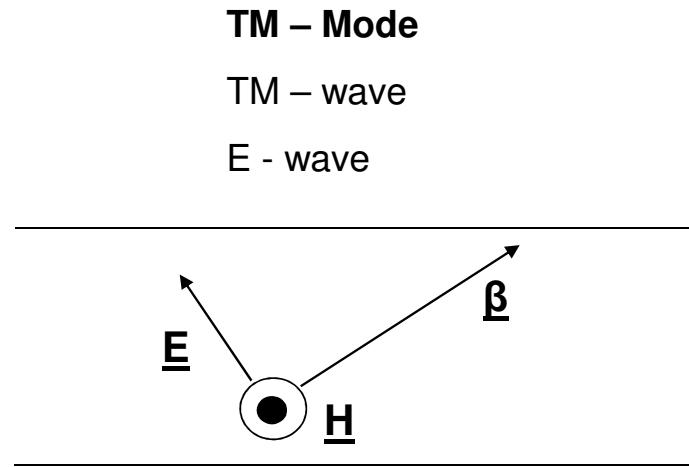
$$\bar{n}_f - \bar{n}_c > \bar{n}_f - \bar{n}_s$$

therefore, the field penetrates more into the substrate than in the cover layer for film modes.

Classification of waves and modes in optical waveguides optoelectronic devices



E no component in z - direction
In propagation direction only a
H – component → H wave



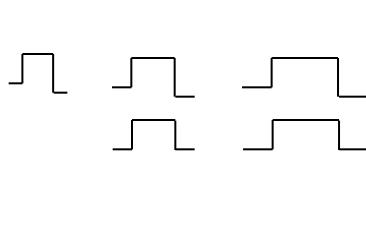
H no component in z - direction
In propagation direction only an
E – component → E wave

During a reflection at an interface : phase shifts occur, described by Fresnel's equations.
(phase shifts depend on all the involved indices and θ).
→ the TE and TM modes reveal different n_{eff} and different confinement factor.

Guided modes in planar waveguides optoelectronic devices

1. Inserting the Ansatz of propagating waves into Helmholtz equations provides a system of linear equations to be solved. The condition that a solution of this system of equations exists, provides a transcendent characteristic equation to be fulfilled.

providing $\rightarrow 0, 1$ or more eigenvalues



$$\bar{n}_s \leq \bar{n}_{\text{eff},i} \leq \bar{n}_f$$

$$\bar{n}_{\text{eff}} = \frac{\beta}{k} = \bar{n}_f \cdot \sin\theta$$

insertion of eigenvalues into the system of equations provides \rightarrow corresponding eigenfunctions (electric field profiles, modes)

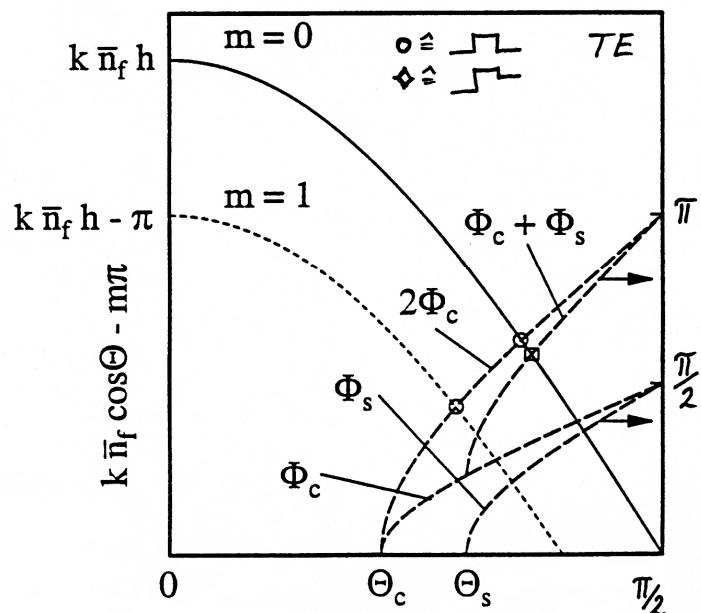
Guided modes in planar waveguides optoelectronic devices

2. Following the intuitive approach : constructive interference providing a uniform total field only occurs for distinct angles θ . The total phase shift in a cycle must amount to an integer of 2π :

$$2k \cdot n_f h \cos \theta - 2\phi_c(\theta) - 2\phi_s(\theta) = m \cdot 2\pi$$

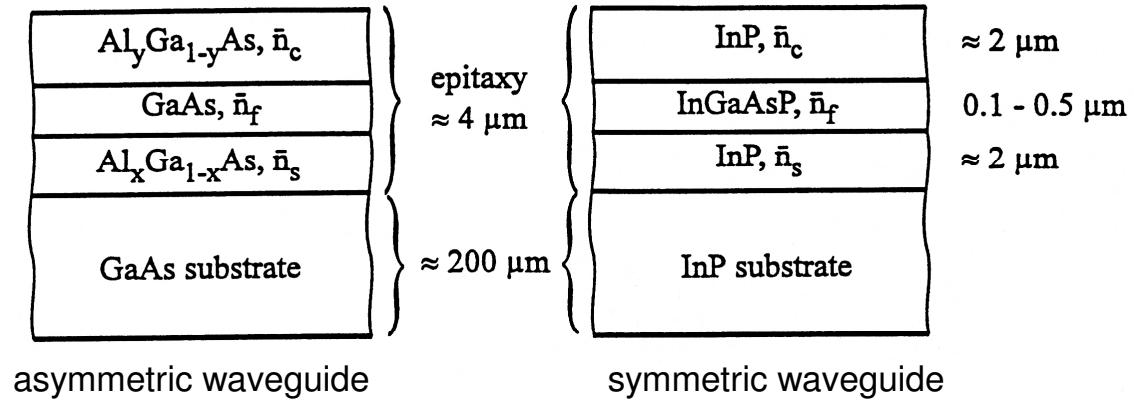
The phase shift after total internal reflection at the cover (substrate) interface is $2\Phi_c$ ($2\Phi_s$). This transcendent characteristic equation determines the permitted angles θ for constructive interference.

Solution → numerically or graphically → For TM – modes the equations are slightly modified. Intersection points (○, ◻) indicate the modes, corresponding angle θ_m .

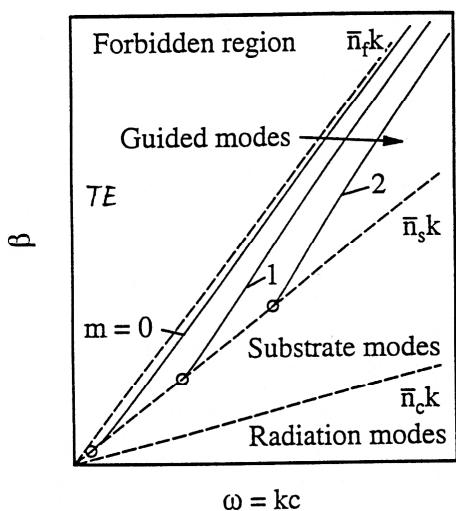


Examples:

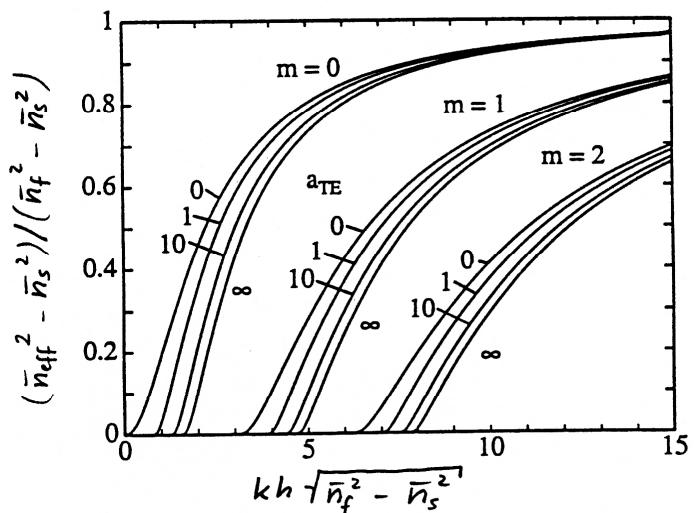
Guided modes in planar waveguides optoelectronic devices



Substrate and cover layers should be at least thick enough for the laterally decaying waves to be sufficiently attenuated before reaching further interfaces.



The dispersion relation $\beta = \beta(\omega)$ is obtained by numerically solving the characteristic equation. For TM – modes nearly identical. The lower cut-off frequency is marked by open circles.



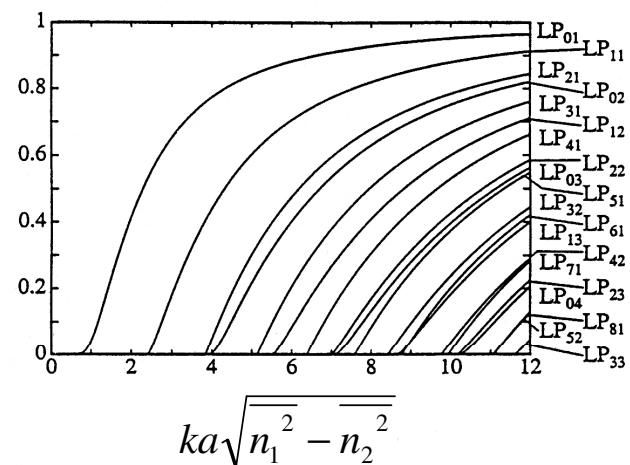
$$a_{TE} = (n_s^2 - n_c^2) / (n_f^2 - n_s^2)$$

= asymmetry parameter

The vertical axis can be approximated by $(\beta - kn_s) / (kn_f - kn_s)$ So that also in this figure a normalized dispersion relation $\beta = \beta(k)$ is shown.

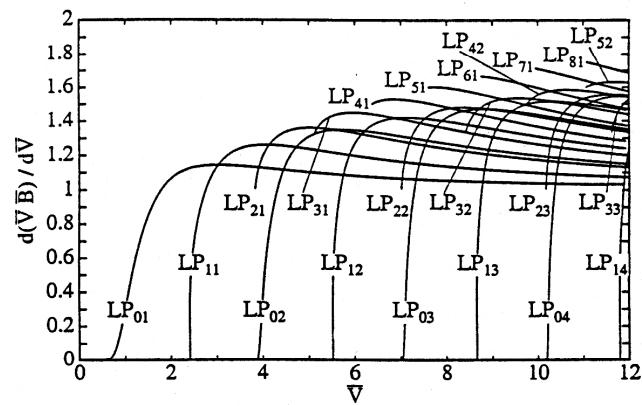
LP_{mv} = linear polarized modes
 $m \geq 0$ integers
 $v \geq 1$

$$\frac{\beta - k\bar{n}_2}{k\bar{n}_1 - k\bar{n}_2}$$

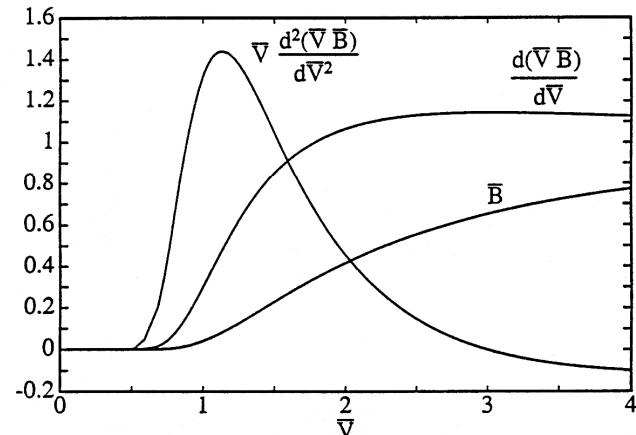


Single mode fibre; weak waveguiding $\bar{n}_1 \approx \bar{n}_2$

Group delay coefficient



normalized propagation constant B

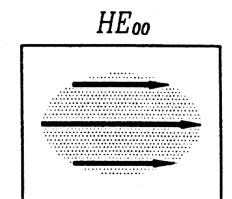


a) rectangular shaped waveguide

modes are not purely TM or TE like but mixtures: Hybrid – modes :

HE_{mn} originate from TE – modes
but $E_y \gg E_z, E_x$

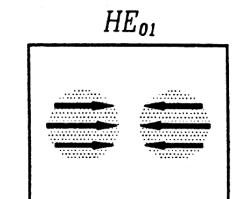
E_{00}^y



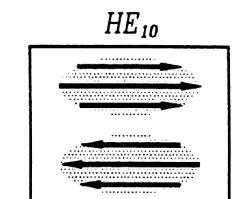
EH_{mn} originate from TM – modes
but $E_x \gg E_y, E_z$

E_{00}^x fundamental mode

E_{01}^y



E_{10}^y



E_{01}^x
0 nodes in
x - direction
1 nodes in
y - direction

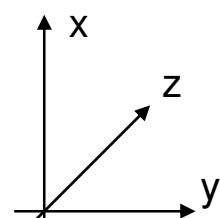
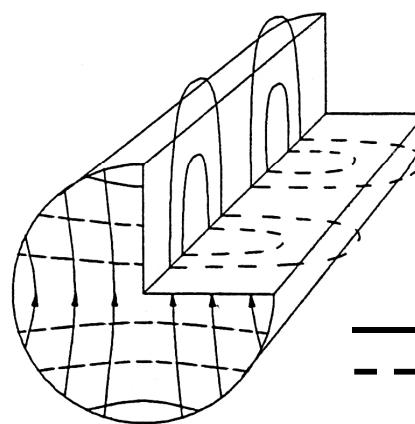
E_{10}^x

another classification
scheme

b) fibre

also here : modes are hybrid modes $HE_{v\mu}$, $EH_{v\mu}$

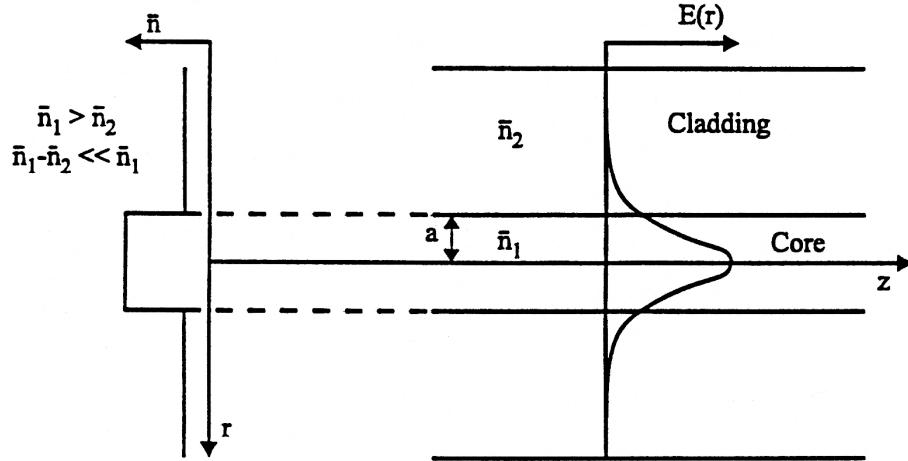
HE_{11}



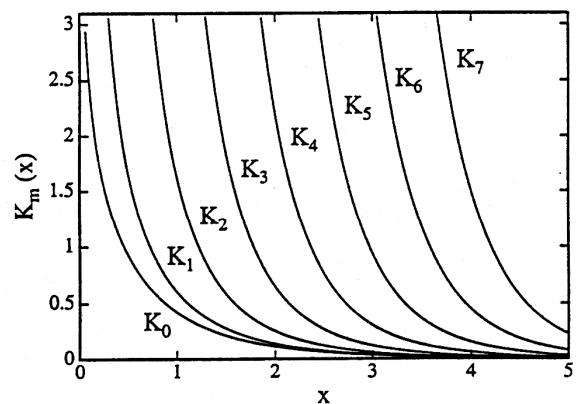
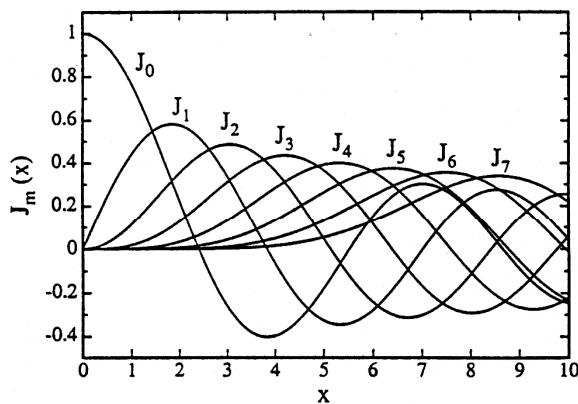
— Electric field
- - - - Magnetic field

Wave propagation in step index fibres optoelectronic devices

Cylindrical symmetry. If $\bar{n}_1 \approx \bar{n}_2 \rightarrow$ linearly polarized propagating waves is a reasonable assumption.



Solution of Helmholtz's equation in cylindrical coordinates (r, φ) involves Bessel functions I_m and modified Bessel functions K_m .



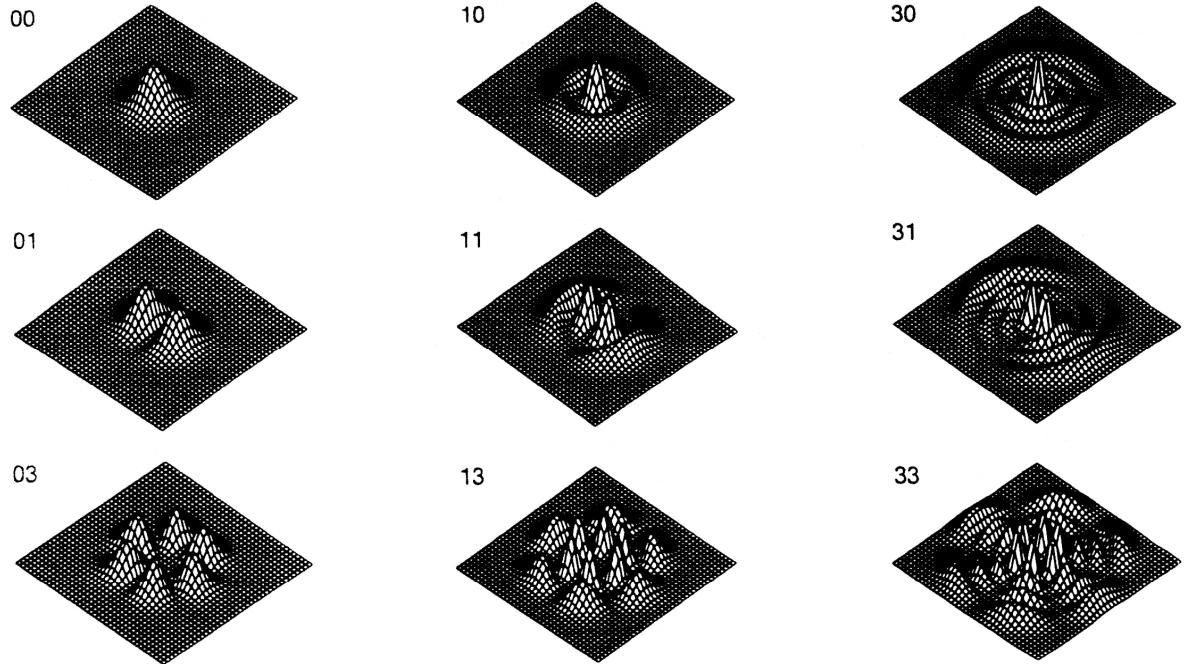
$$E(r, \varphi, z, t) = \begin{cases} C_1 I_m(ur/a) \cos(m\varphi + \varphi_0) \exp[i\omega t - i\beta z] & \text{for } r \leq a \\ C_2 K_m(ar/a) \cos(m\varphi + \varphi_0) \exp[i\omega t - i\beta z] & \text{for } r \leq a \end{cases}$$

$$U = a\sqrt{k^2 n_1^{-2} - \beta^2} \quad \text{and} \quad w = \sqrt{\beta^2 - k^2 n_2^{-2}}$$

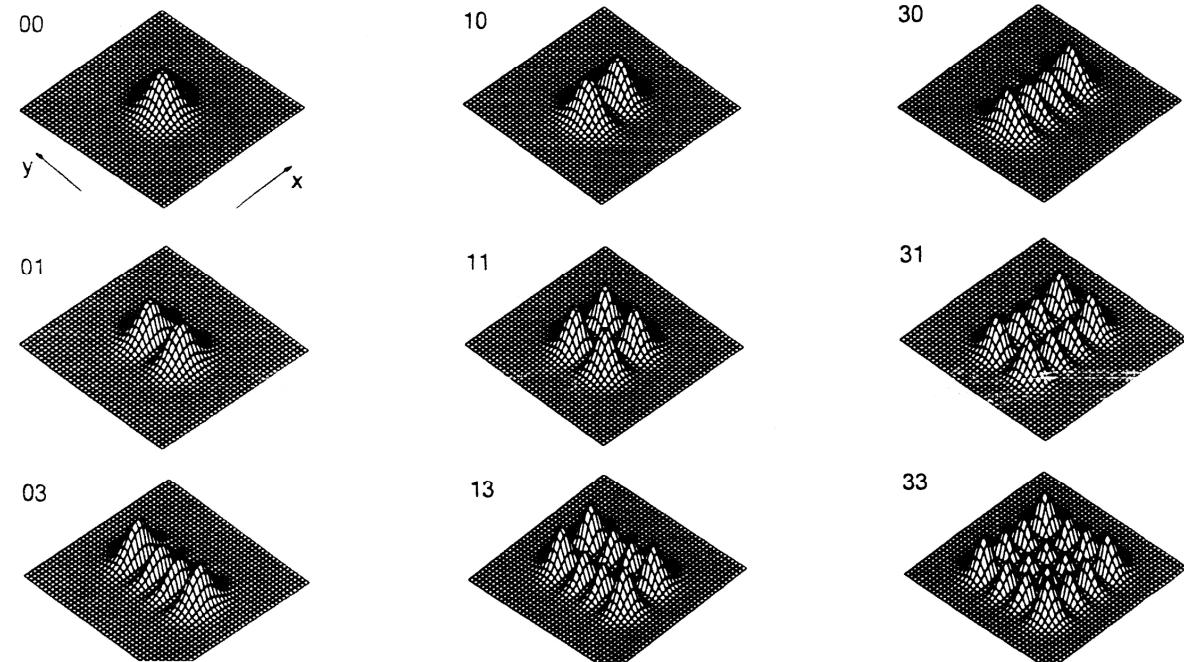
m integer, C_1, C_2 complex constants to be determined by the boundary conditions.

Circular and rectangular waveguide optoelectronic devices

circular beam



rectangular beam



- A. Modal dispersion (= intermodal dispersion) in multimode fibres Warning : the intuitive ray model does not provide all answers; Wavemodel (Helmholtz equation) → Dispersion relation → v_{gr} , n_{gr} ; v_{gr} depends on λ via (different θ) different eigenfunctions, different cladding penetration.
- B. Chromatic dispersion (= spectral dispersion) of the group velocity
 - Material dispersion $\bar{n}_i = \bar{n}_i(\lambda)$
 v_{gr} depends via the refractive index on λ .
 - Waveguide dispersion v_{gr} depends via the waveguide geometry on λ .
- C. Polarization mode dispersion due to fibre bending, not axial inhomogeneities
- D. Profile dispersion

Conclusion

optoelectronic devices

Transmission in different spectral ranges

Optical transmission characteristics of optical fibres is determined by attenuation and bandwidth (dispersion)

Attenuation is affected by:

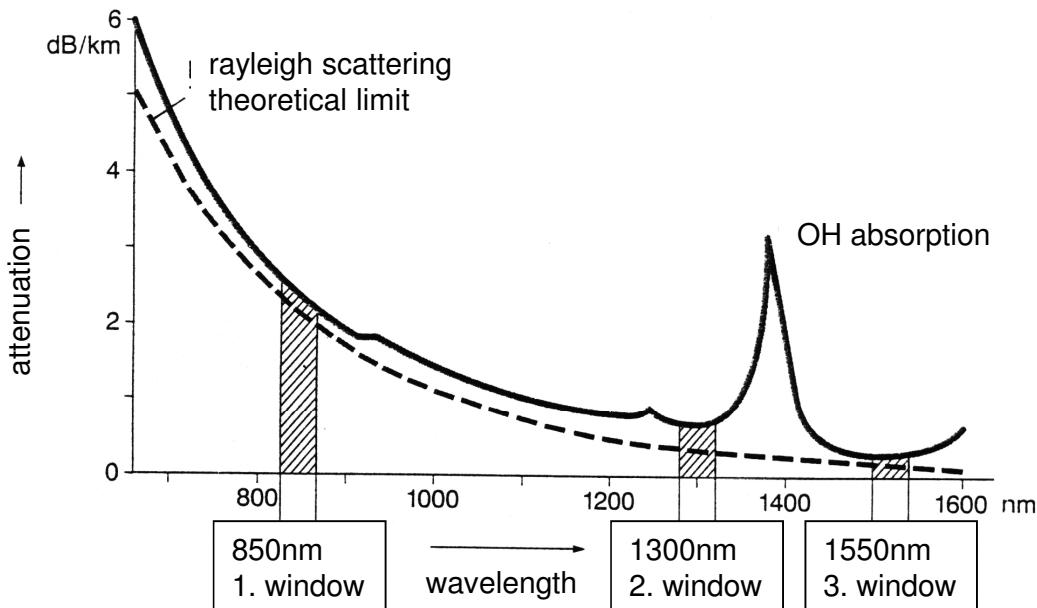
- rayleigh scattering
- absorption
- radiation losses

Bandwidth is limited by:

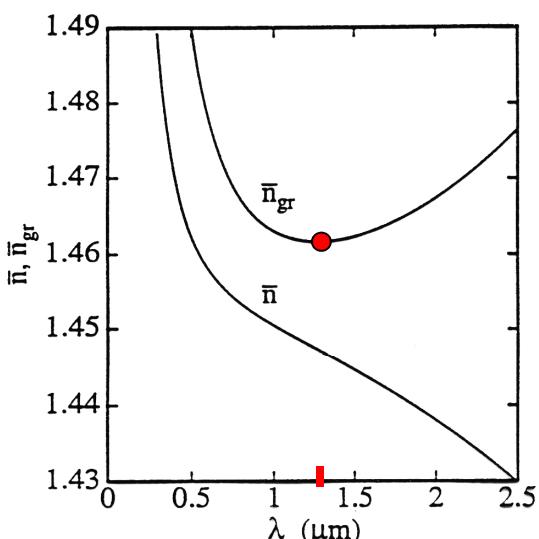
- modal dispersion
- material dispersion
- waveguide dispersion

Silica glass optical fibre (SiO_2) show three different „transmission windows“ which show optimum attenuation and bandwidth.

- 1. window at $\lambda = 850\text{nm}$ (cost-effective laser)
- 2. window at $\lambda = 1300\text{nm}$ (minimal dispersion)
- 3. window at $\lambda = 1550\text{nm}$ (minimal absorption)



Group index and group dispersion optoelectronic devices



minimum at $\lambda_0 = 1.273 \mu m$

$$\bar{n} = \frac{c}{v_{ph}}$$

analogous:

$$\bar{n}_{gr} = \frac{c}{v_{gr}} = \frac{c}{d\omega/d\beta} = c \frac{d\beta}{d\omega} = c \frac{d}{d\omega} \left(\frac{\omega \bar{n}}{c} \right)$$

$$= \bar{n} + \omega \frac{d\bar{n}}{d\omega} = \bar{n} - \lambda \frac{d\bar{n}}{d\lambda}$$

↑ exercise

determined by

v_{ph} : propagation velocity of a monochromatic wave

v_{gr} : propagation velocity of an optical pulse

\bar{n}

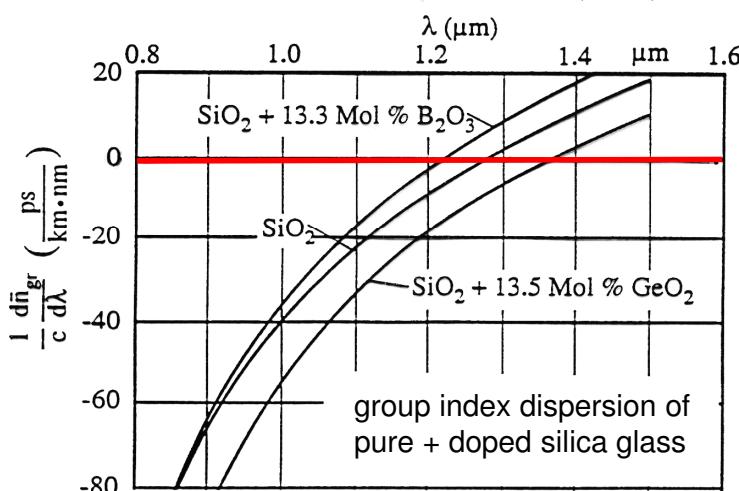
n_{gr}

Propagation of single elementary pulses of different carrier wavelength λ along L :

time delay $t = \frac{L}{v_{gr}} = \frac{L}{c} \bar{n}_{gr}$ of a single pulse

delay difference between 2 pulses with shifted carrier wavelength $\Delta\lambda$ $\Delta t \approx \frac{dt}{d\lambda} \Delta\lambda = \frac{L}{c} \frac{d\bar{n}_{gr}}{d\lambda} \Delta\lambda$

Delay difference per L : $\frac{\Delta t}{L} \approx \frac{\Delta\lambda}{c} \cdot \left(\frac{d\bar{n}_{gr}}{d\lambda} \right) = \frac{\Delta\lambda}{c} \cdot \left(\cancel{\frac{d\bar{n}}{d\lambda}} - \cancel{\frac{d\bar{n}}{d\lambda}} - \lambda \cdot \frac{d^2\bar{n}}{d\lambda^2} \right)$



remember:

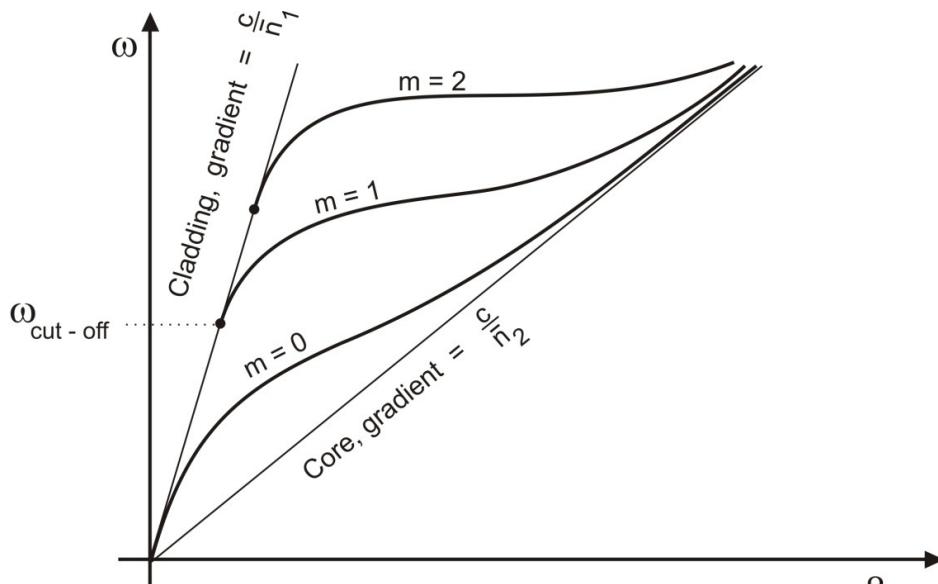
time delay difference Δt in ps of 2 gaussian pulses with carrier frequency difference $\Delta\lambda = 1 \text{ nm}$ apart after travelling $L = 1 \text{ km}$

Dispersion relations $\Omega = \Omega (k)$ Phonon waves in crystals,

Polariton waves in crystals

$E = E (k)$ Electrons and holes in crystals

$\omega = \omega (\beta_m)$ Photons in layered media
(waveguides, fibres)



$$\beta_m = k_1 \cdot \sin \theta_m = \frac{\bar{n}_m^* \omega}{c}$$

\bar{n}_m^* - Eigenvalues

k - wave vektor

β_m - propagation constant in z - direction

Note that: $\bar{n}_i = \bar{n}_i (\lambda)$ is not yet included. This material dispersion would modify the straight lines into slightly bent lines.

v_{gr} changes from mode to mode (intermodal dispersion) and within a mode with λ (intramodal dispersion).

Modal dispersion

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First, only modal dispersion considered:

Mode number : $m = 0, 1, 2, \dots$



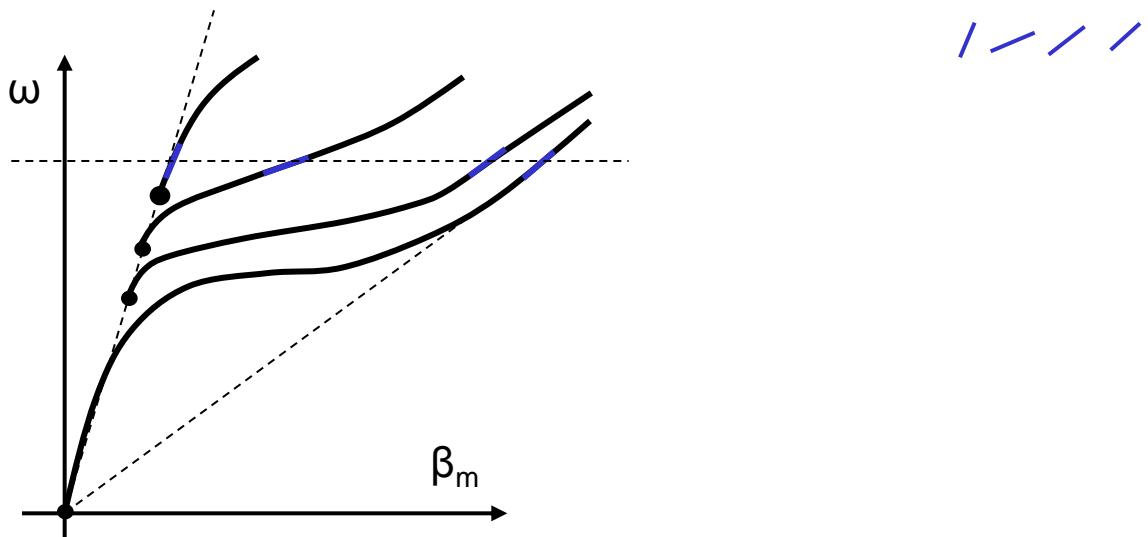
Light travels using different modes, propagating at different V_{gr} , respectively.

$$\Delta\tau = \frac{L}{V_{g,\min}} - \frac{L}{V_{g,\max}}$$

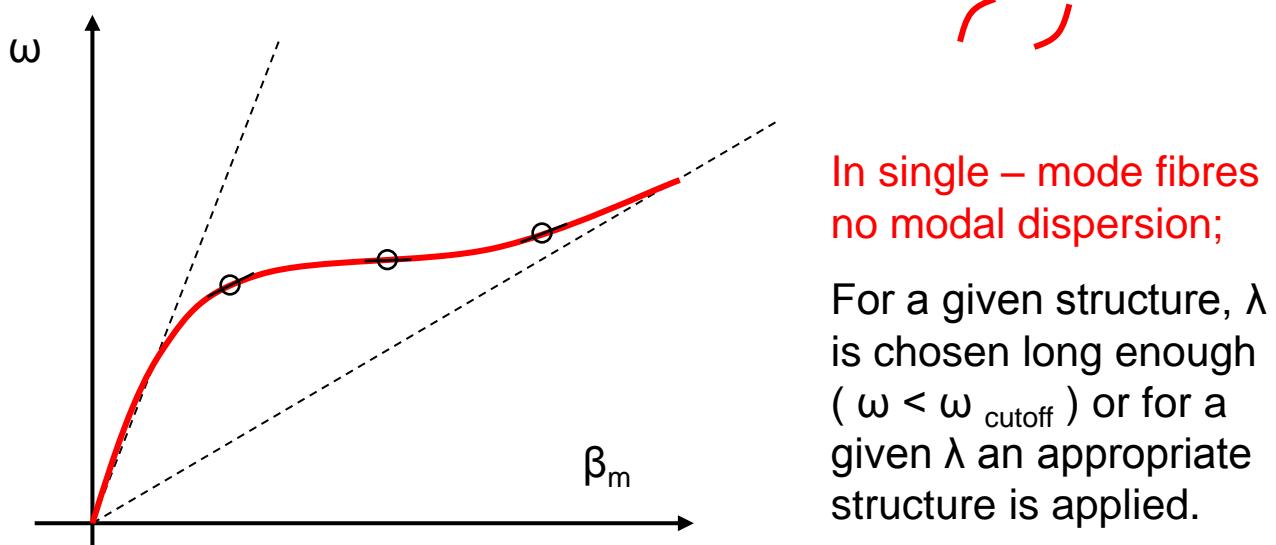
$$V_{g,\min} = \frac{c}{n_1} \quad V_{g,\max} = \frac{c}{n_2}$$

Neglecting that in between there may exist smaller slopes !
 Intermodal dispersion related to the different slopes (waveguide dispersion as a part of intramodal dispersion is related to the evivatures).

- a) Modal dispersion in a Multimode fibre; $\omega = \text{const}$ in this example. Intermodal dispersion related to the different slopes



- b) Waveguide dispersion in a single mode fibre; small variation of ω (e.g. within the spectral laser line). Waveguide dispersion as a part of intramodal dispersion is related to the curvatures.

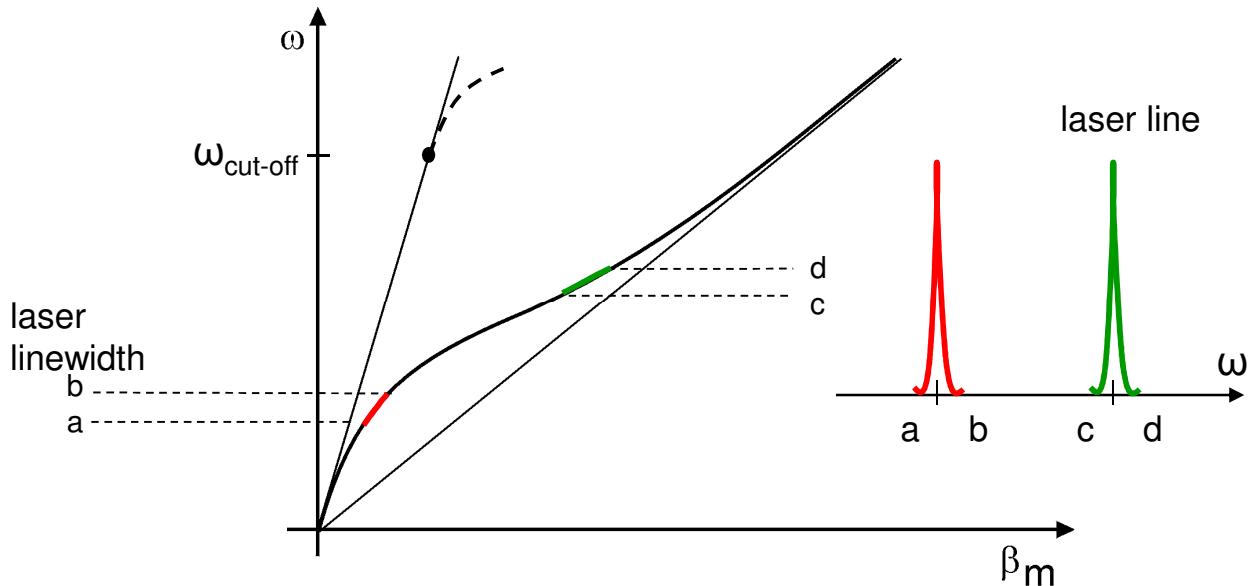


- c) Waveguide dispersion also occurs in multimode fibres, e.g. in the lowest branch of the dispersion relation (a) and, thus, is similar to dispersion relation branch shown in red under b.

Waveguide dispersion

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Now single-mode fibres considered (no modal dispersion) $\omega < \omega_{\text{cut-off}}$



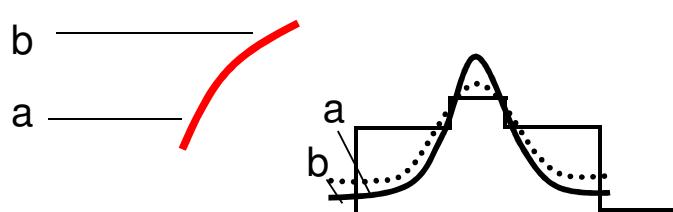
v_{gr} depends on λ

Since : - mode profiles and eigenvalues depend on λ .
 - in the ray model: for a constructive interference, slightly different λ require slightly different paths (angles).

case 1: if $\omega_a < \omega_b < \omega_{\text{cut-off}}$

$$\lambda_a > \lambda_b > \lambda_{\text{cut-off}}$$

$$v_{\text{gr},a} > v_{\text{gr},b}$$



case 2: if $\omega_c < \omega_d < \omega_{\text{cut-off}}$

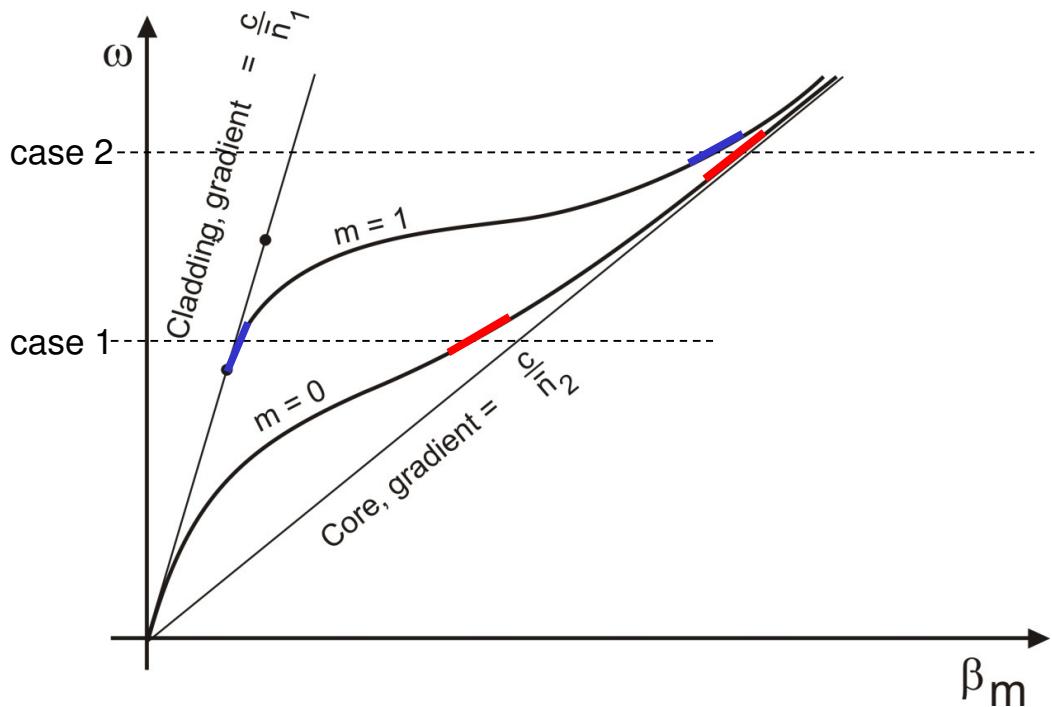
$$\lambda_c < \lambda_d < \lambda_{\text{cut-off}}$$

$$v_{\text{gr},c} < v_{\text{gr},d}$$



However :

- a) in special situations the relation of the group velocities may be reversed according to the dispersion relation.
- b) The cases $v_{ph} \leq$ and $\geq v_{gr}$ additionally exist.



Modal dispersion

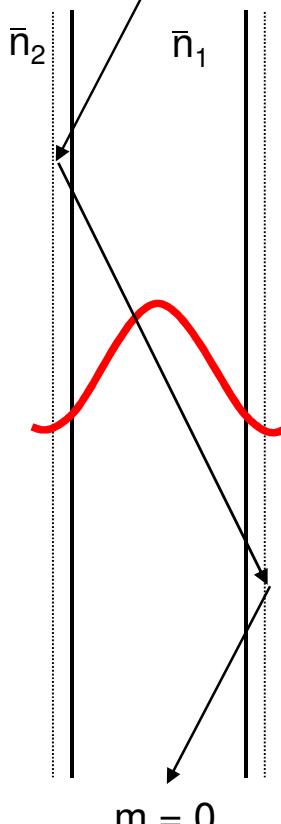
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Warning: the simple view (ray model) : light traveling along the path of the fundamental mode arrives more quickly than a higher „mode ray“ is wrong due to two reasons :

- v_g in z – direction is important
- Higher order modes penetrate more into the cladding where refractive index is low.

Only the dispersion relation gives correct answers !

However here also the ray model



$m = 0$



$m = 1$

$$v_{ph} = \frac{c}{n_{eff}}$$

in z - direction
but important
is v_{gr}

\bar{n}_{eff} highest
more in the core

v_{ph} smaller

v_{gr} smaller

Eigenvalue

← always →

← in many cases →

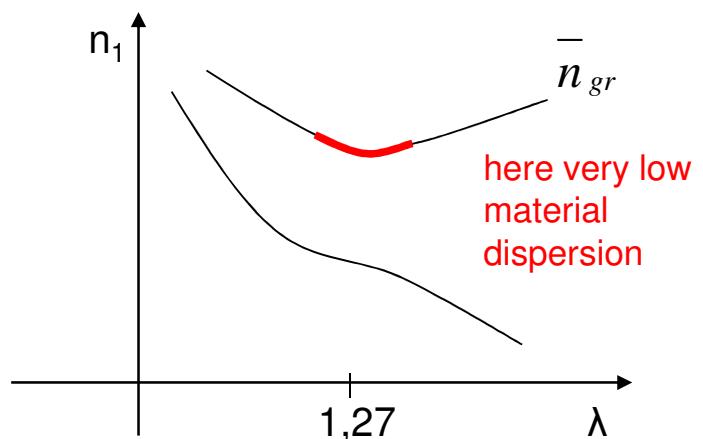
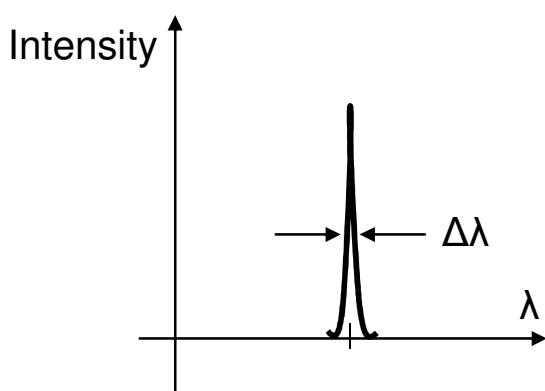
\bar{n}_{eff} lower
more in the cladding

v_{ph} larger

v_{gr} larger

Material Dispersion

optoelectronic devices



$$\bar{n}_1 = \bar{n}_1(\lambda) \rightarrow \bar{n}_{gr} = \bar{n}_{gr}(\lambda) \quad v_{gr} = \frac{d\omega}{dk} = \frac{c}{n_{gr}}$$

$$v_{gr} = \frac{L}{t} = \frac{c}{\bar{n}_{gr}} \quad dt = \frac{L}{c} d\bar{n}_{gr} \quad \text{Differentiation of the path - time law.}$$

$$\Delta\tau = \frac{L}{t} \cdot \frac{d\bar{n}_{gr}}{d\lambda} \Delta\lambda \quad \bar{n}_{gr} = \bar{n} - \lambda \frac{d\bar{n}}{d\lambda} \quad (\text{is a consequence of : } \bar{n}_{gr} = c \frac{d\beta}{d\omega} = c \frac{d}{d\omega} \left(\frac{\omega \bar{n}}{c} \right))$$

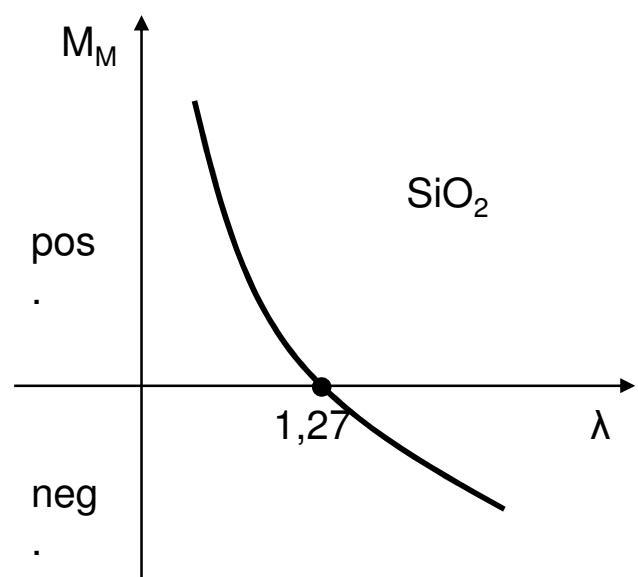
$$\rightarrow \frac{\Delta\tau}{L} = \frac{\Delta\lambda}{c} \left(\frac{d\bar{n}}{d\lambda} - \frac{d\bar{n}}{d\lambda} - \lambda \frac{d^2\bar{n}}{d\lambda^2} \right) \quad \frac{\Delta\tau}{L} = |M_M| \Delta\lambda$$

$$M_M = -\frac{\lambda}{c} \cdot \frac{d^2\bar{n}}{d\lambda^2}$$

$v_{gr} = v_{ph}$ no dispersion

$v_{gr} < v_{ph}$ normal dispersion

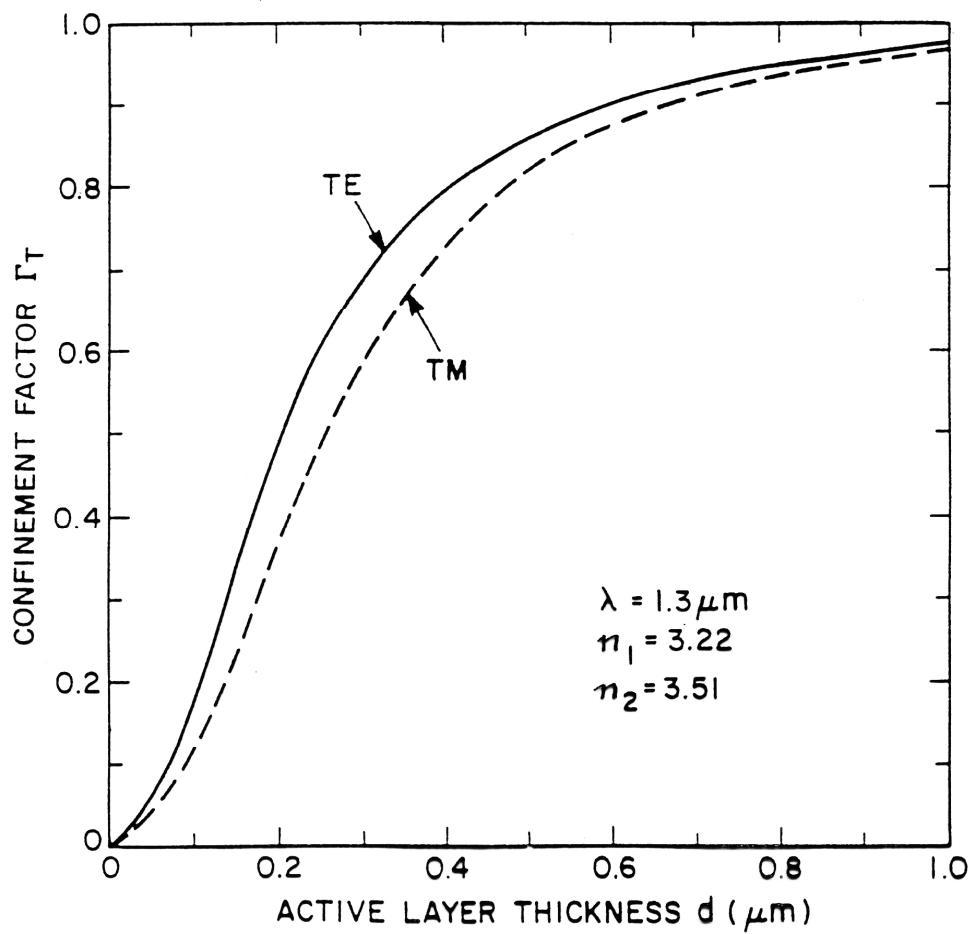
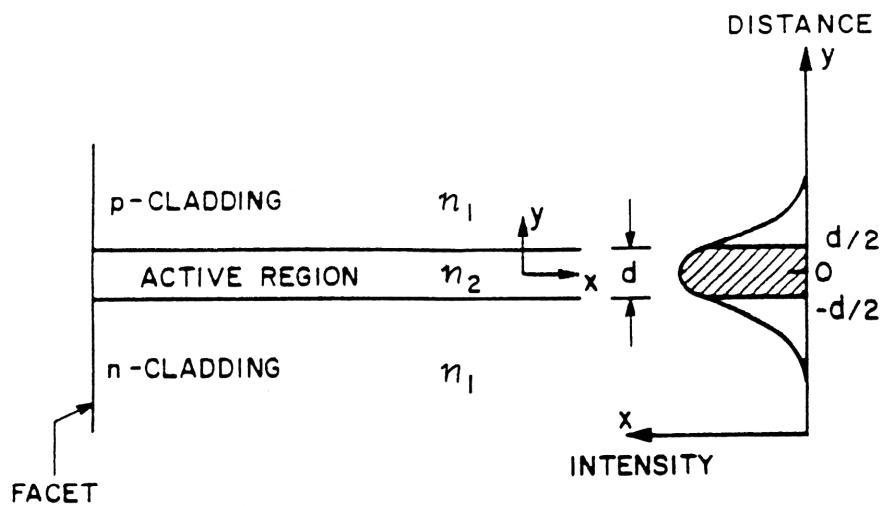
$v_{gr} > v_{ph}$ abnormal dispersion



Confinement of the guided light field in the central layer

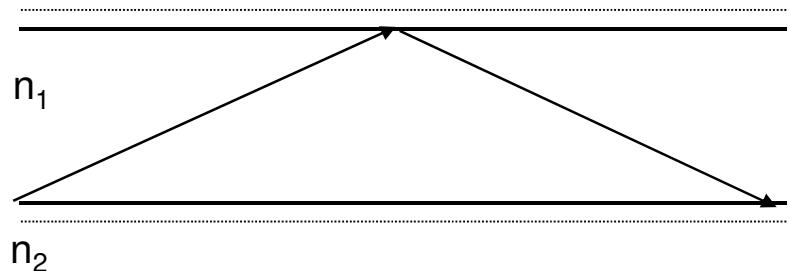
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1



1. Mode dispersion

n_2

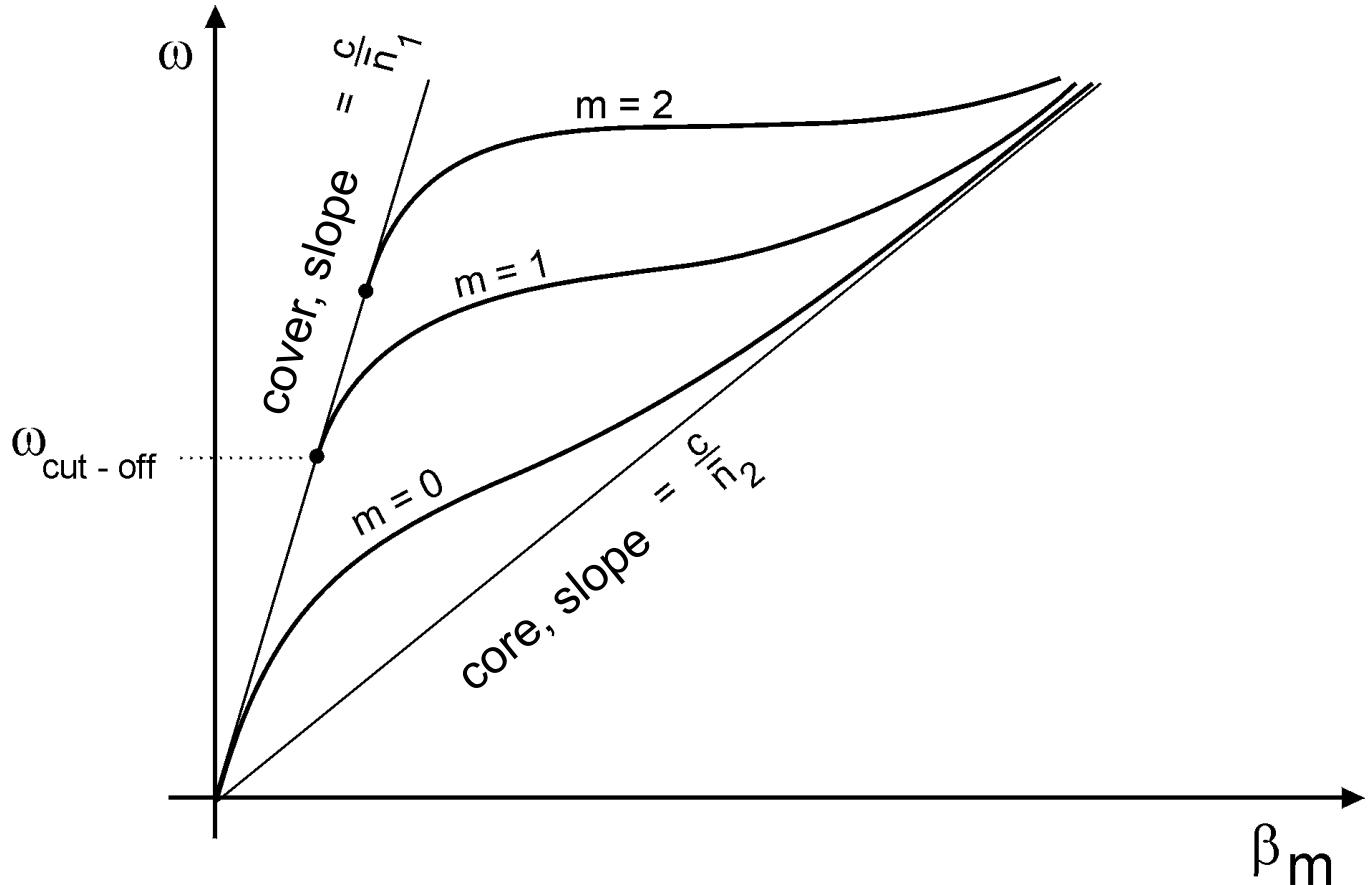


2. Chromatic dispersion = material dispersion + waveguide dispersion

a) material dispersion $\bar{n}(\lambda)$

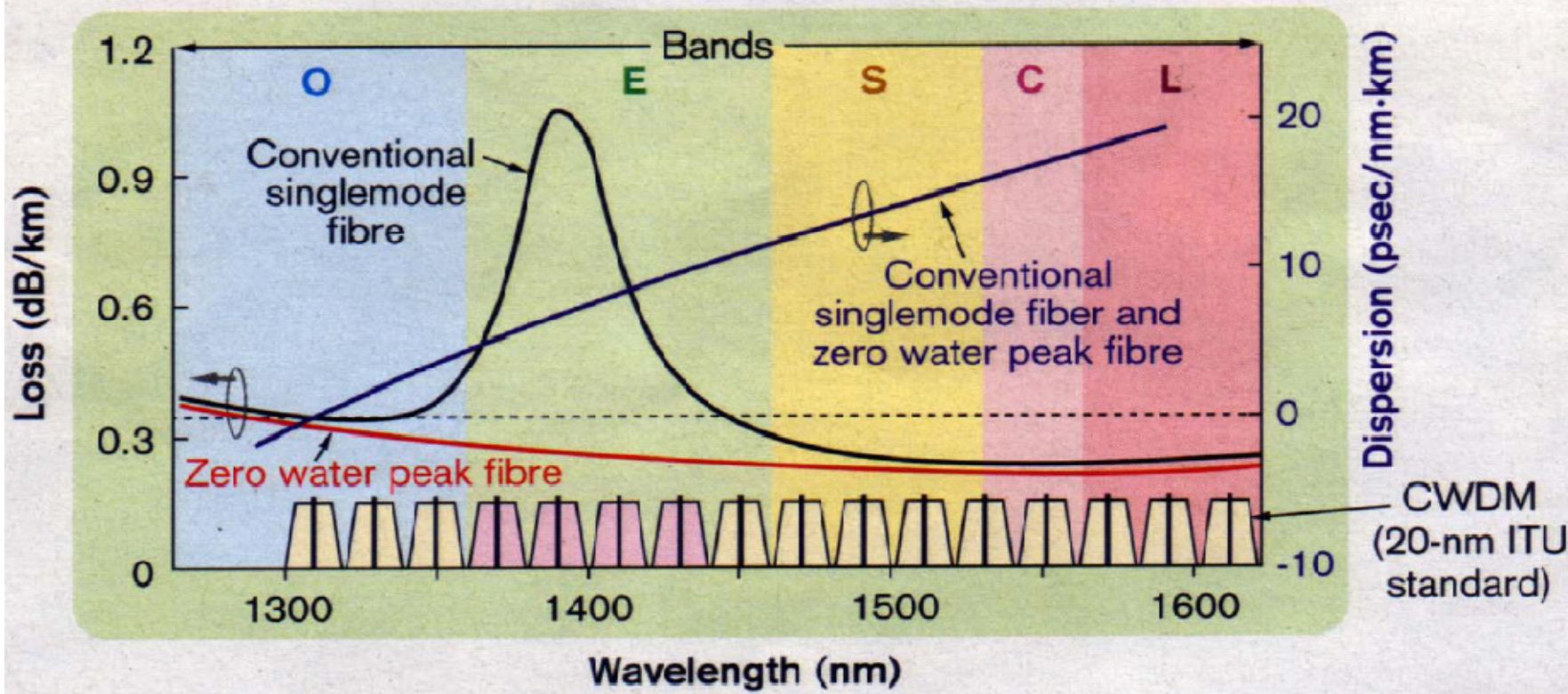
$$\frac{\Delta t}{l} = |M| \cdot \Delta \lambda = -\frac{\lambda}{c} \frac{d^2 n}{d \lambda^2}$$

b) waveguide dispersion $\bar{n}(x)$



schematic view of the dispersion relation of a quartz glass fibre,
fundamental mode $m=0$, mode of first order $m=1$, mode of
second order $m=2$

Spectral attenuation and dispersion comparison



Multiple cladding profile fibre

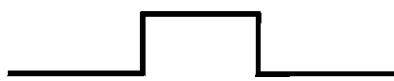
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Interplay of material and waveguide dispersion in different single – mode fibres

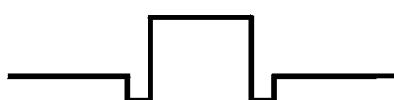
- the waveguide dispersion coefficient M_w (ps / (km*nm)) depends in a complicated way on geometry and refractive index profile of the fibre
- the material dispersion coefficient M_m (ps / (km*nm)) describes the wavelength dependence of the refractive index in a homogeneous bulk (3D) material.

$$M_m = \frac{1}{c} \cdot \frac{d\bar{n}_{gr}}{d\lambda} = -\frac{\lambda}{c} \cdot \frac{d^2\bar{n}_i}{d\lambda^2}$$

single - clad



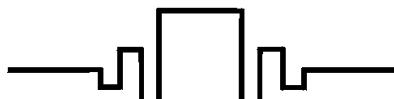
double - clad



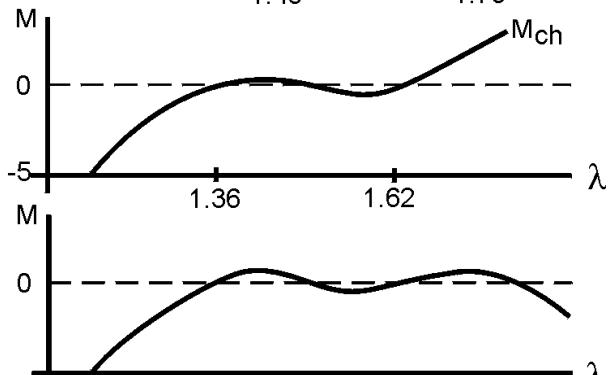
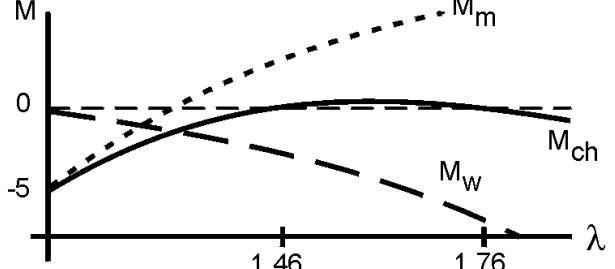
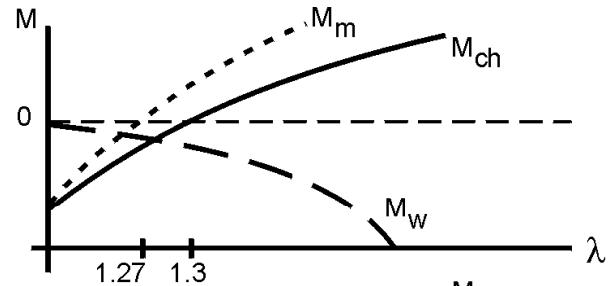
triple - clad



quadruple - clad



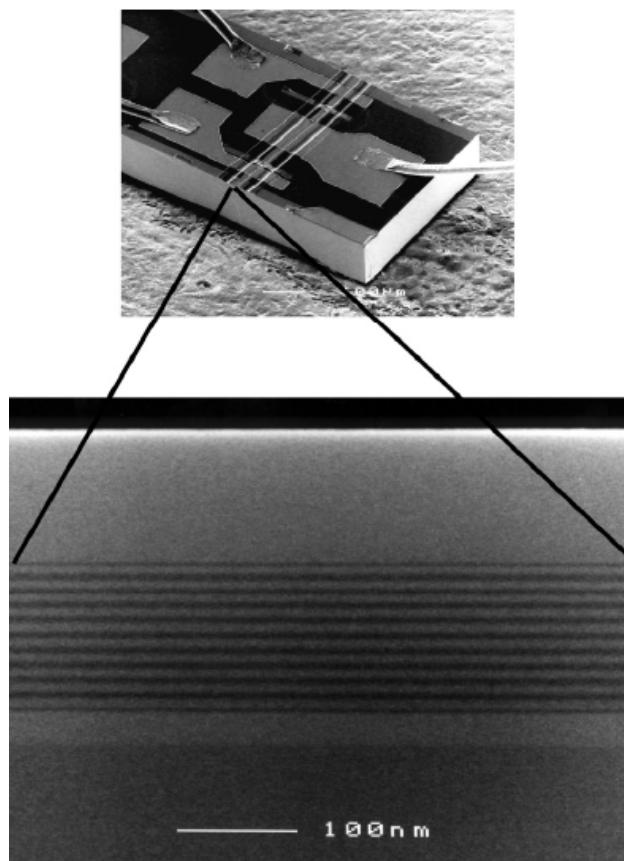
$$M_{ch} = M_m + M_w$$



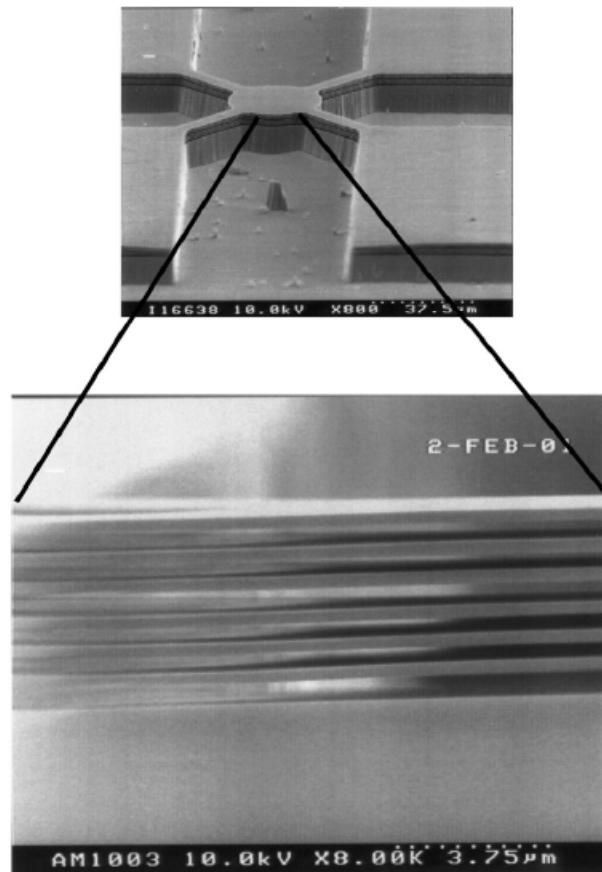
Micro optoelectronic devices

optoelectronic devices

Tunable DFB laser

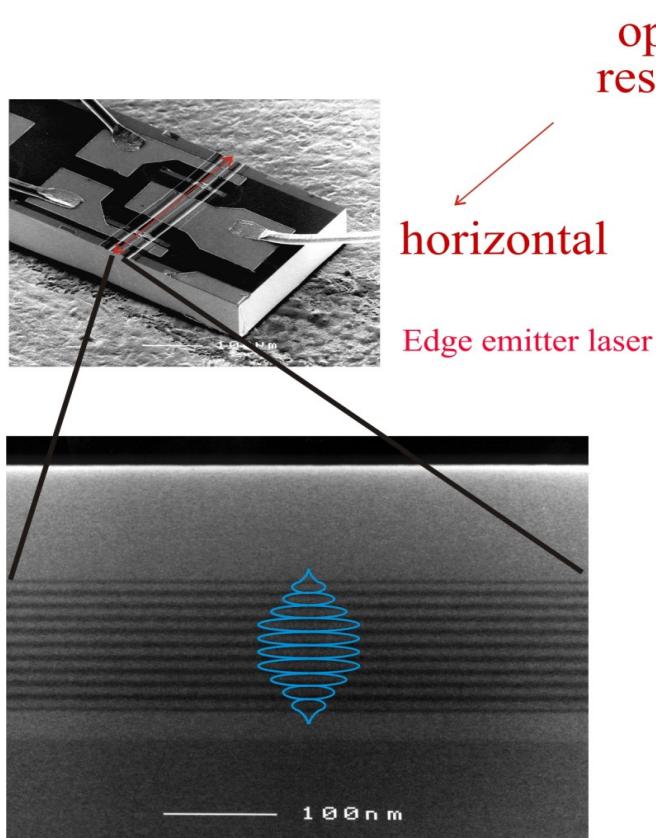


Semiconductor multiple air-gap filter structure

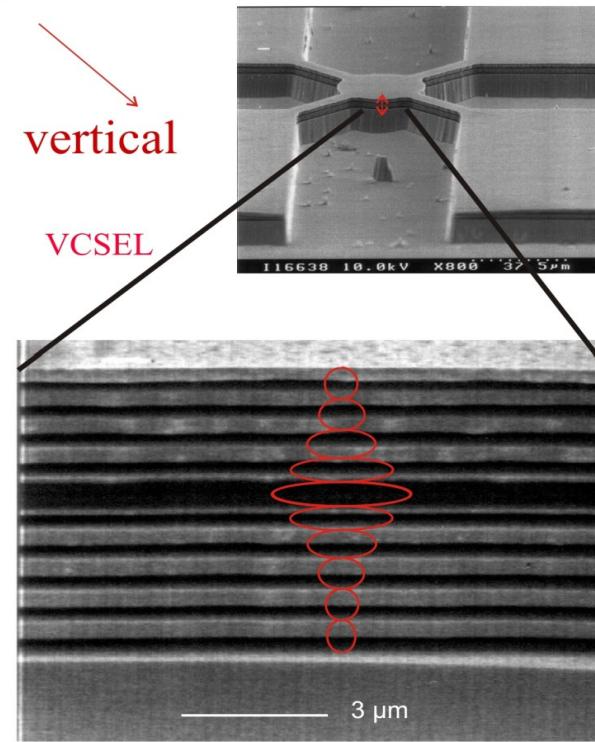


Micro optoelectronic lasers

optoelectronic devices



AlGaInAs/AlGaInAs MQWs
electron wave resonator
Schrödinger-equation

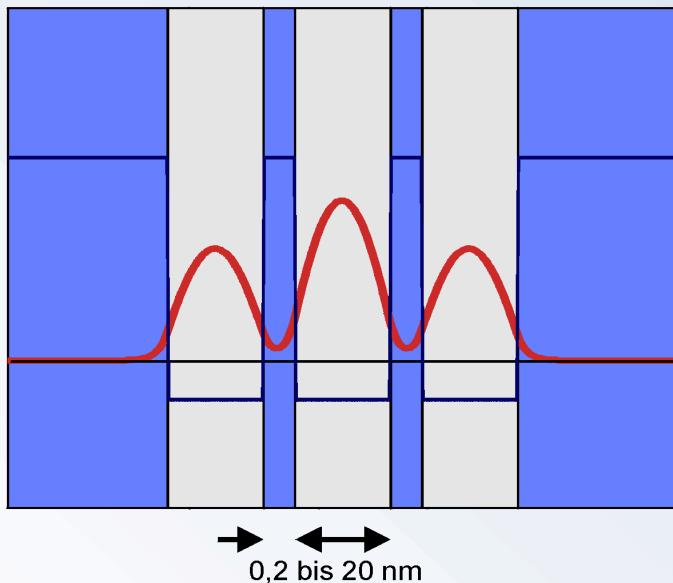


GaInAsP/air-gap DBR
photon wave resonator
Helmholtz-equation

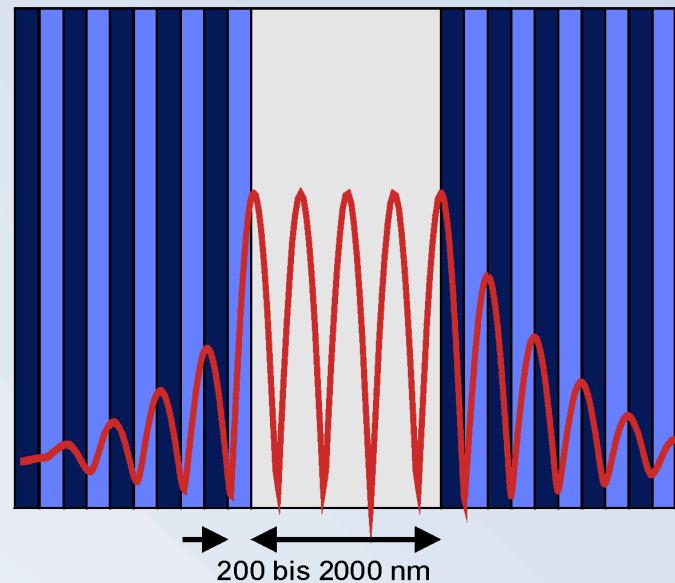
Multilayer structures

optoelectronic devices

Electron wave in a multiple quantum well



Photon wave in an optical resonator



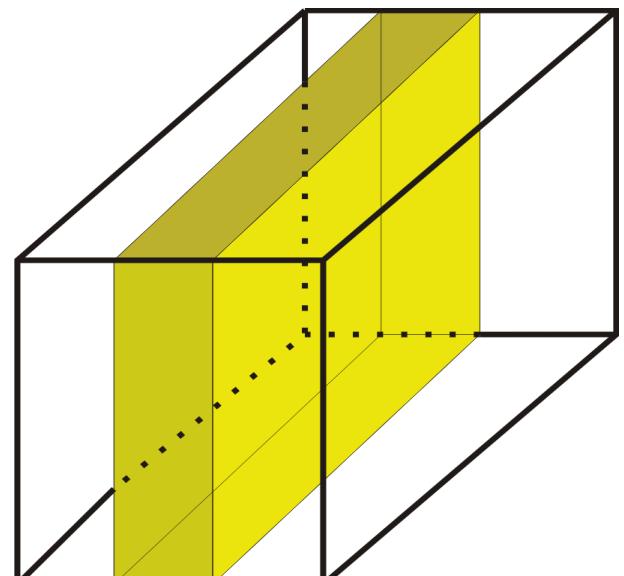
In the order of magnitude of the electron wave length CB Energy potential varies from layer to layer (due to the thin barriers, the wells are coupled)

In the order of magnitude of the light wavelength Refractive index varies from layer to layer

Photon wave in an optical resonator

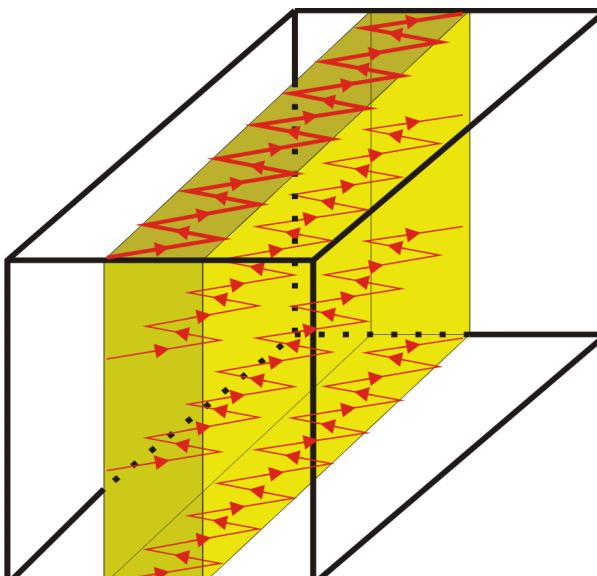
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Solution of Helmholtz Equation



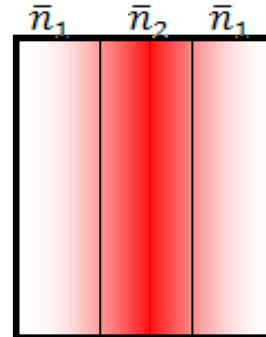
material 1
material 1

material 2
high refraction
index



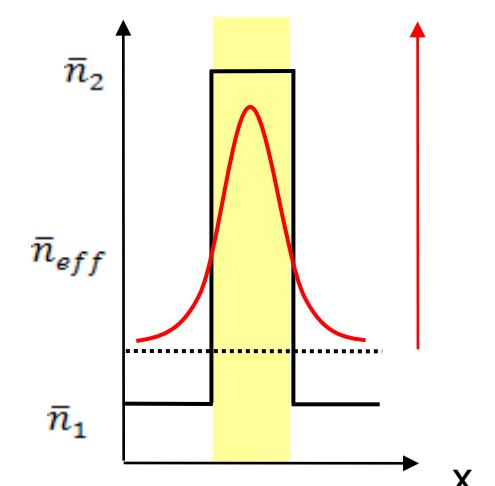
ray model

in x-direction
a light cage



wave model

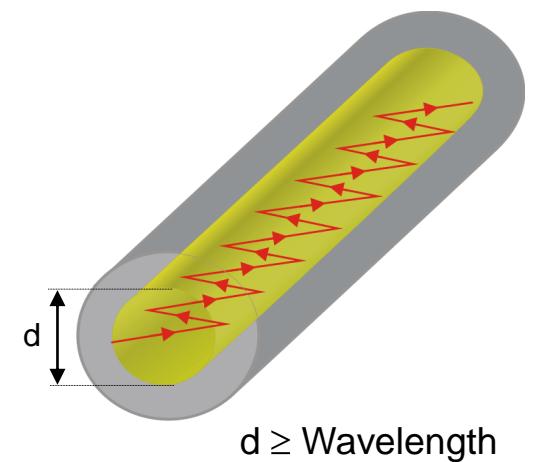
Refraction
index



x

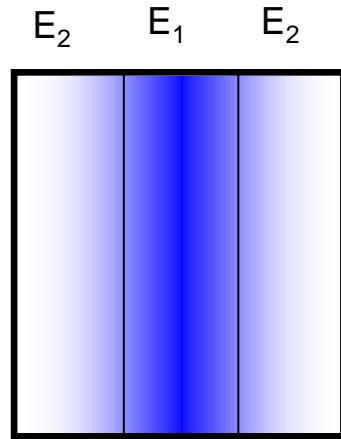
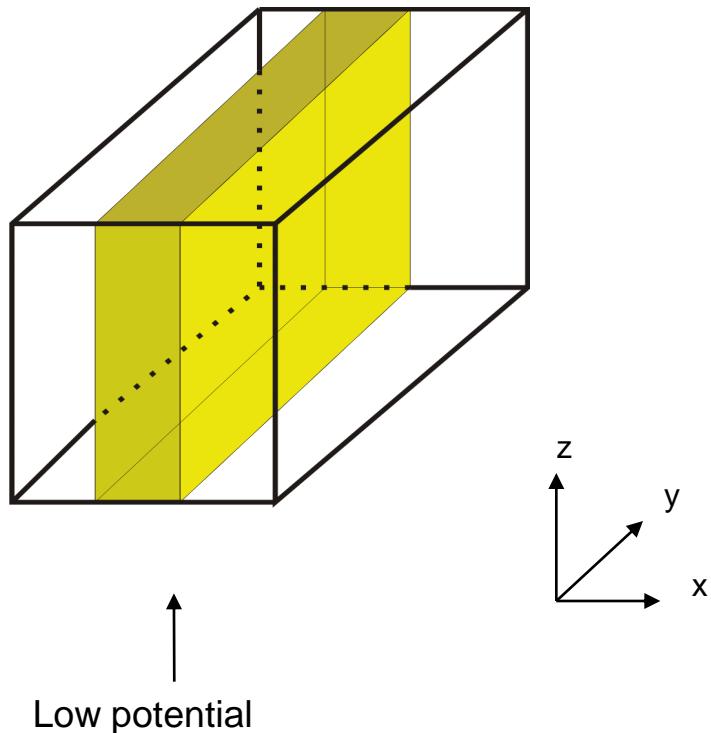
Applications :

- fibres
- semiconductor laser resonator

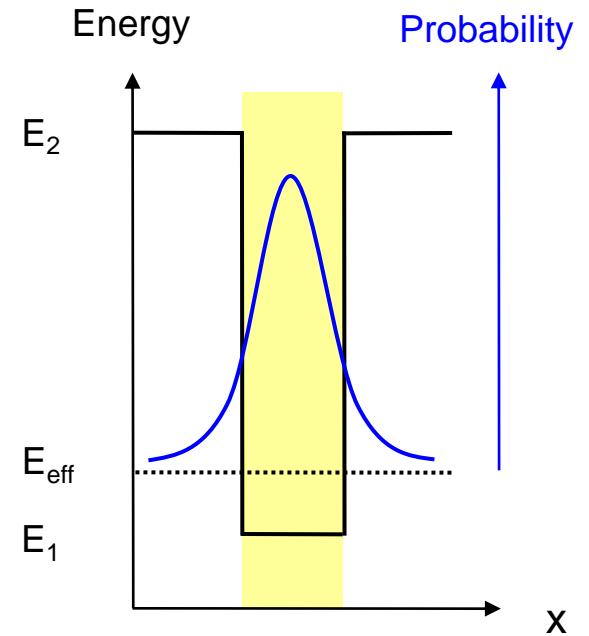


$d \geq \text{Wavelength}$

Solution of Schrödinger Equation



Quantum mechanical model



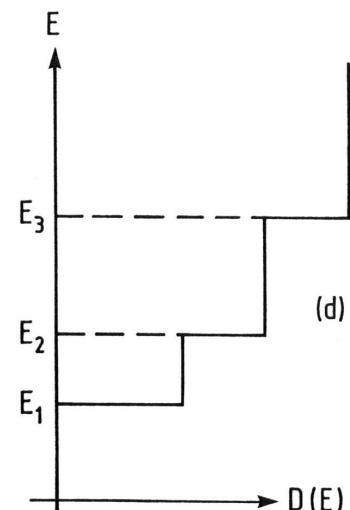
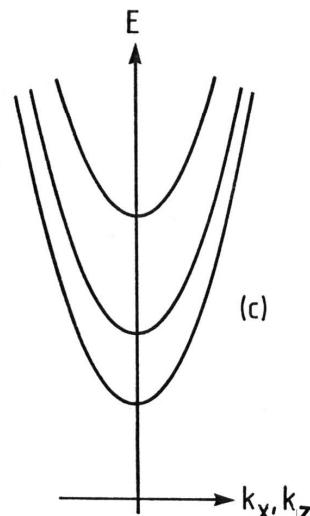
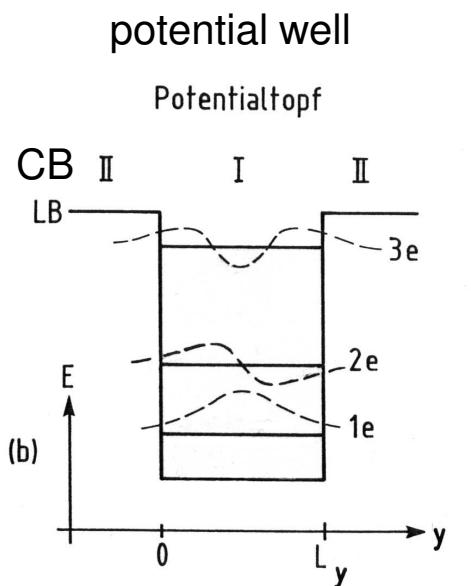
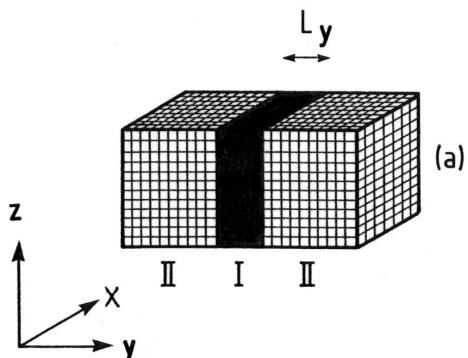
in x-direction a electron cage

- Applications :**
- fast Transistors (HEMT, MODFET)
 - modern opto electronic devices

Quantum wells

optoelectronic devices

Quasi 2D



schematic view in space

band structure in real space

band structure in k -space

density of states

Comparison of different wave types

optoelectronic devices

	Classical waves		Quantum mechanical waves
	acoustic	Electr. - magnetic	Material
Example	Sound in air	light	Atoms, molecules
Wave equation	$\nabla(\rho \cdot c_s^2 \nabla p) - \rho \cdot \frac{\partial^2 p}{\partial t^2} = 0$	$\Delta E + \frac{\omega^2 \cdot n^2}{c^2} E - \frac{\epsilon(r)}{c_0^2} \frac{\partial^2 E}{\partial t^2} = 0$	$\frac{-\hbar^2}{2m^*} \Delta \Psi + V(r)\Psi - i \cdot \hbar \frac{\partial \Psi}{\partial t} = 0$
Property	Air pressure p	Electrical field E	Probability $ \psi ^2$
Dispersion relation of free waves	$\omega = C_s \cdot k$	$\omega = C_0 / \sqrt{(\epsilon k)}$	$\omega = \hbar k^2 / 2m^*$ $E = \hbar \omega, p = \hbar k$
Wavelength range	2 cm – 20 m	0.4 – 0.8 μm	$\lambda = h / p$ e (eV) : $\leq nm$ C 60 : ≈ pm